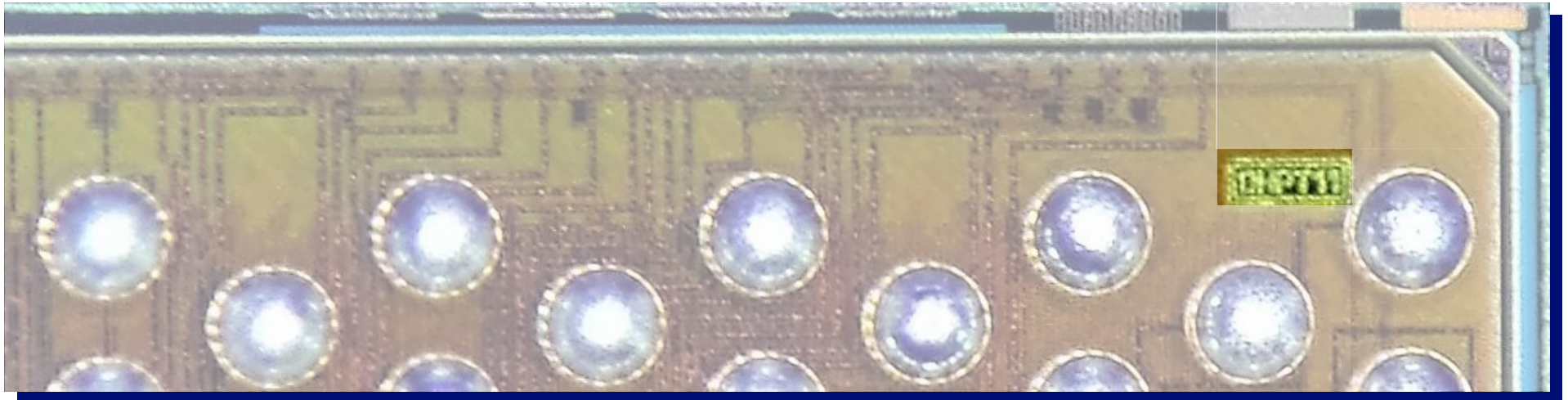


# DHPT1.0 Comparison

9th VXD Belle II Workshop  
13-15 Jan. 2016, Valencia Spain

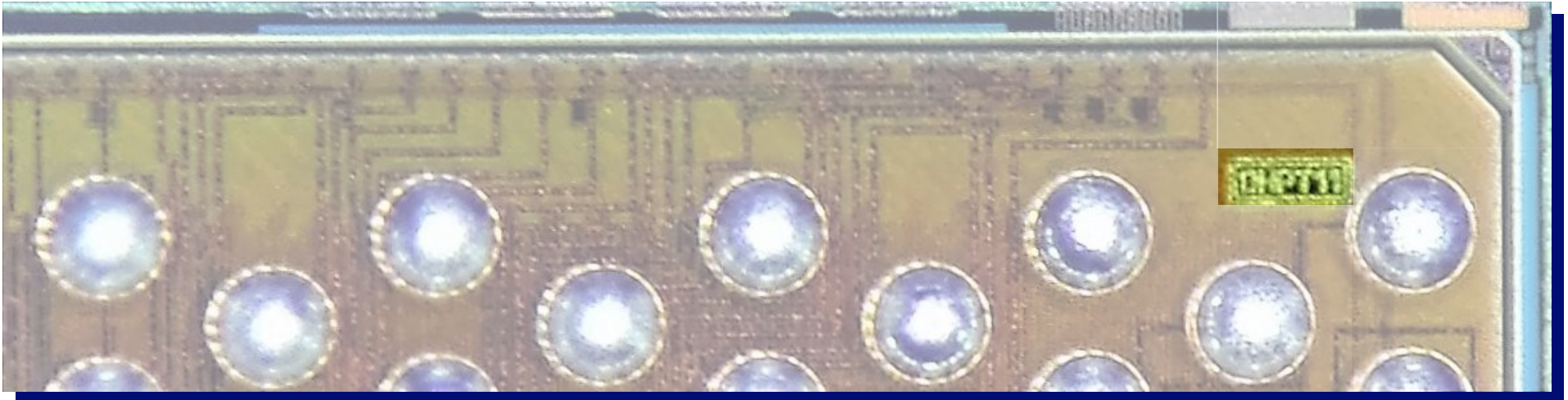


## Changes from DHPT1.0 to DHPT1.1



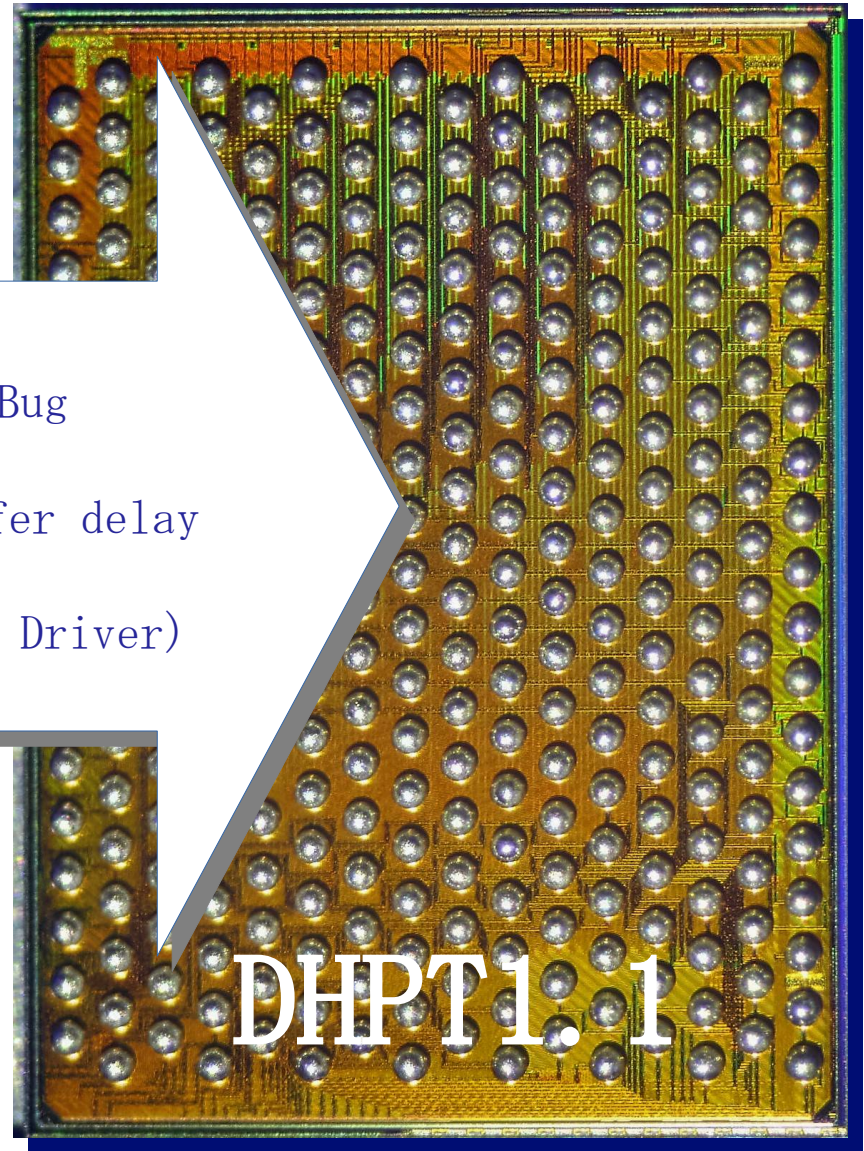
## Results

## Changes from DHPT1.0 to DHPT1.1



Results

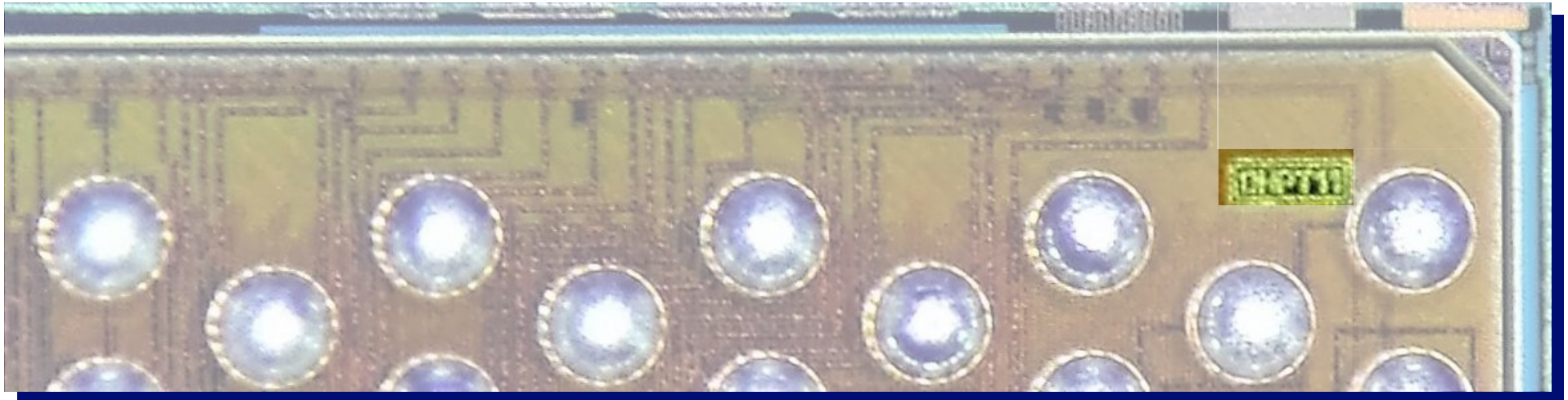




Serializer Bug  
LVDS RX / IO buffer delay  
Serial Link (CML Driver)

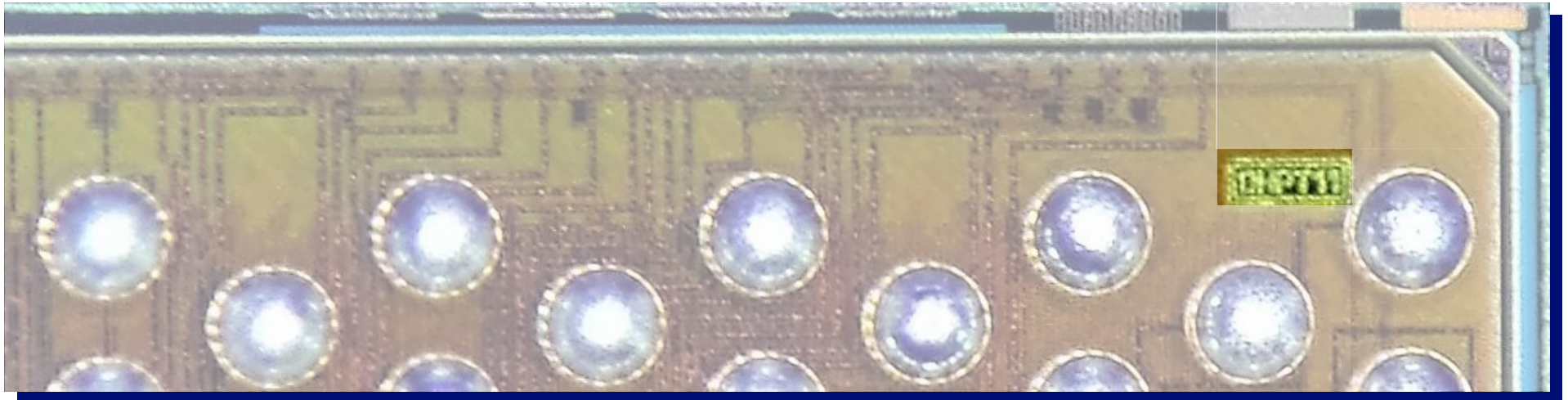


## Changes from DHPT1.0 to DHPT1.1



## Results

## Changes from DHPT1.0 to DHPT1.1



Results

Serializer Bug

- Mistake made during extracting and simulating the layout with all process corners
- Serializer works, but VCC and/or GCK have to be adjusted:
  - GCK= 80 MHz → VCC = 1.6V (works but should not be applied for a long time)
  - GCK= 60 MHz → VCC = 1.4V (ok)
- Manufacturer test data → wafer batch has „slow NMOS“ (too high threshold)

PARAMETER	BY LOT:	SPEC LO	SPEC HI	MIN	MAX	MEAN	STD DEV
VT1_N4	(N/.3/.06/1)	0.300	0.490	0.368	0.490	0.423	0.029
Isof_N4	(N/.3/.06/1)	-1.400E-07	0.000	-8.958E-10	-3.833E-11	-2.339E-10	2.063E-10
Isat_N4	(N/.3/.06/1)	0.491	0.735	0.547	0.673	0.593	0.031

Digital checks for DHPT 1.1:

Jtag communication DHE & DHPT



Memory tests



All digital tests passed

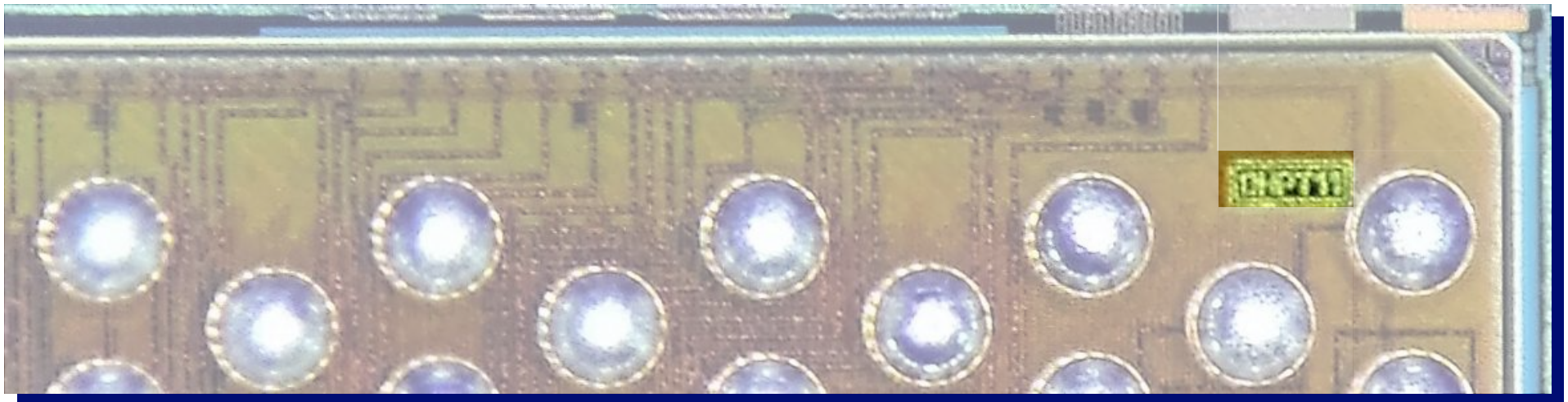


Link established  
(*down to VDD 1.25V !unsensed!*)



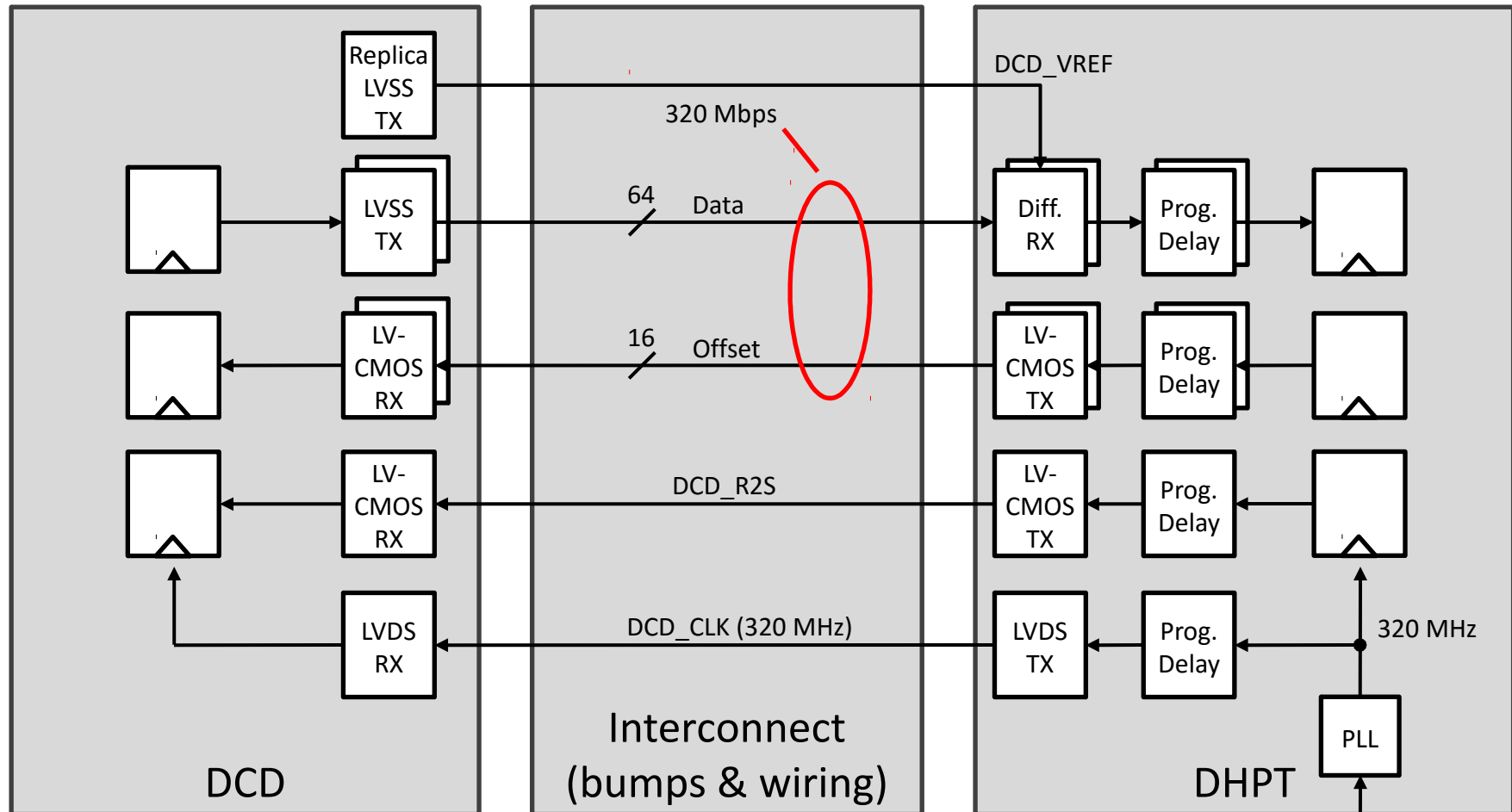


## Changes from DHPT1.0 to DHPT1.1



Results LVDS RX / IO buffer delay

# DCD – DHPT Interface Block Diagram

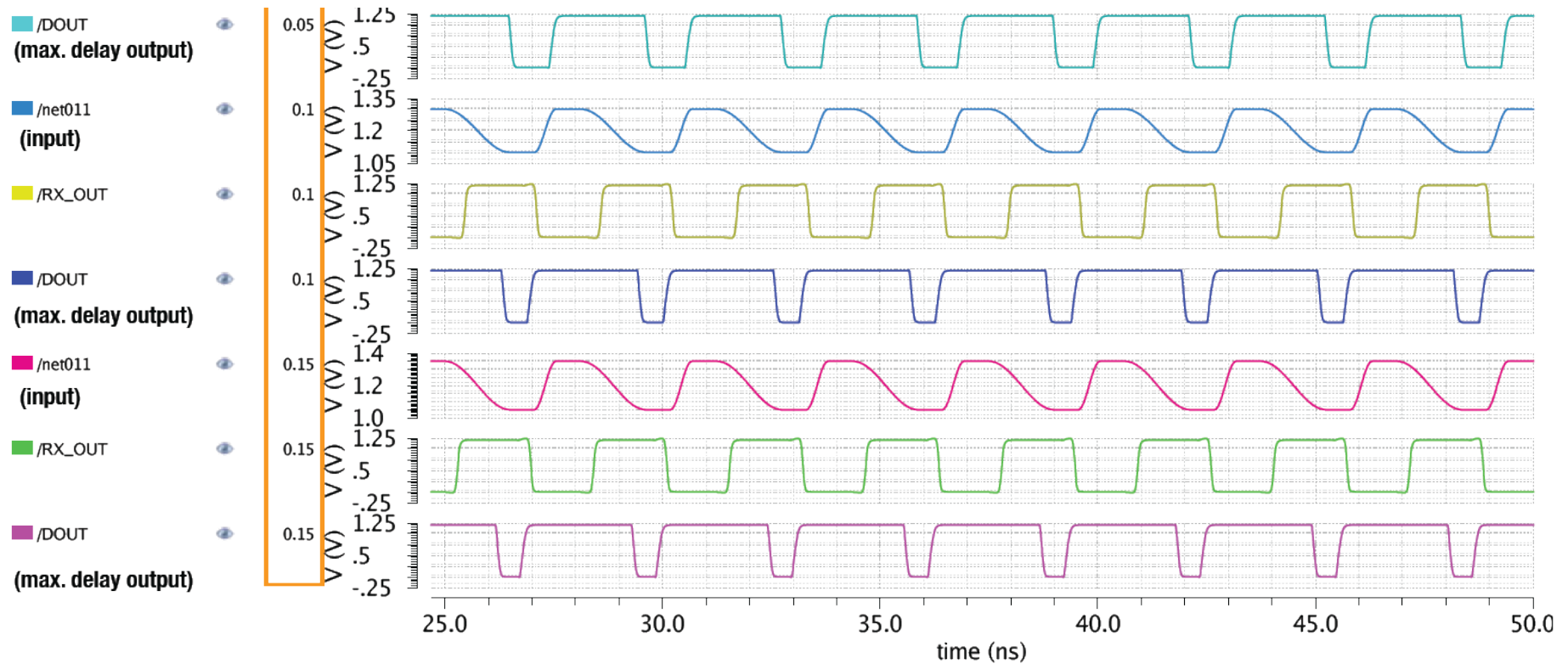


8 links with 8 data + 2 offsets bits each  
ADC sample rate = 10MHz  
32 ADCs per link → 320 Mbps

GCK  
(80 MHz)

# Duty cycle distortion

- Duty cycle distortion was overlooked during DHPT 1.0 sign-off





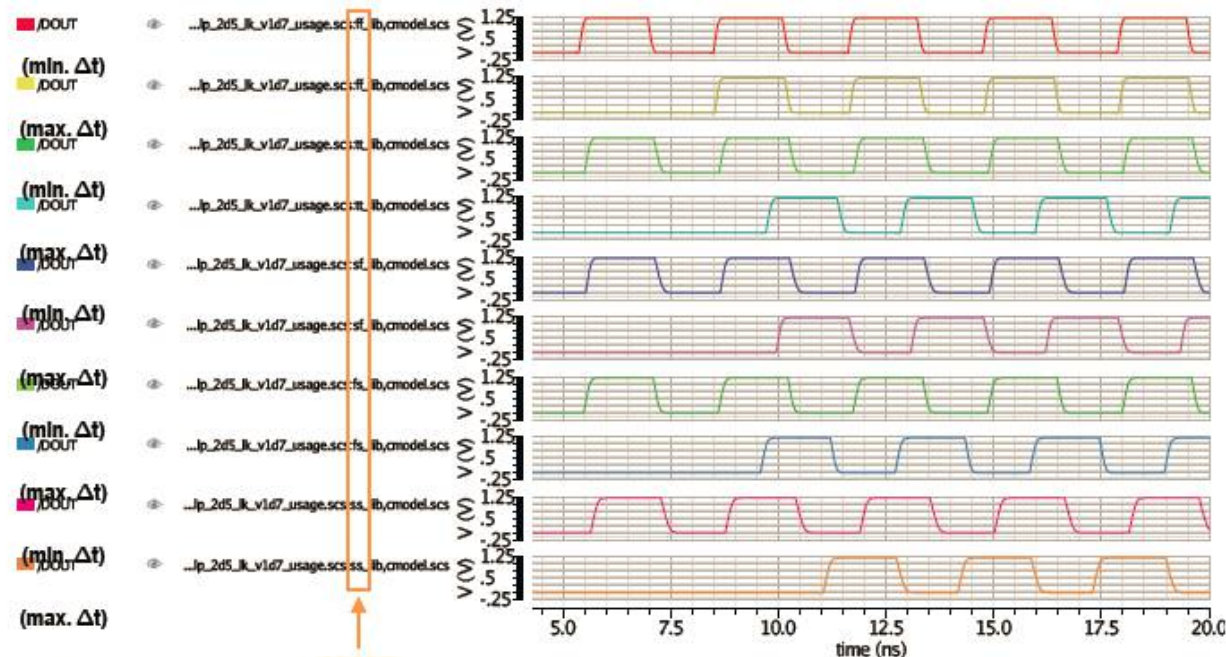
# Delay Element Modification

- Custom delay elements made out of identical inverters

All corners covers 3.125 ns ( $\leftarrow$  320 MHz).

Max. delay time with extracted model

	$\Delta t$	duty cycle (min. $\Delta t$ )	duty cycle (max. $\Delta t$ )
tt	4.20 ns	52.0%	53.3%
ff	3.15 ns	51.4%	52.2%
fs	4.10 ns	51.6%	51.8%
sf	4.43 ns	52.2%	54.9%
ss	5.42 ns	52.8%	54.9%

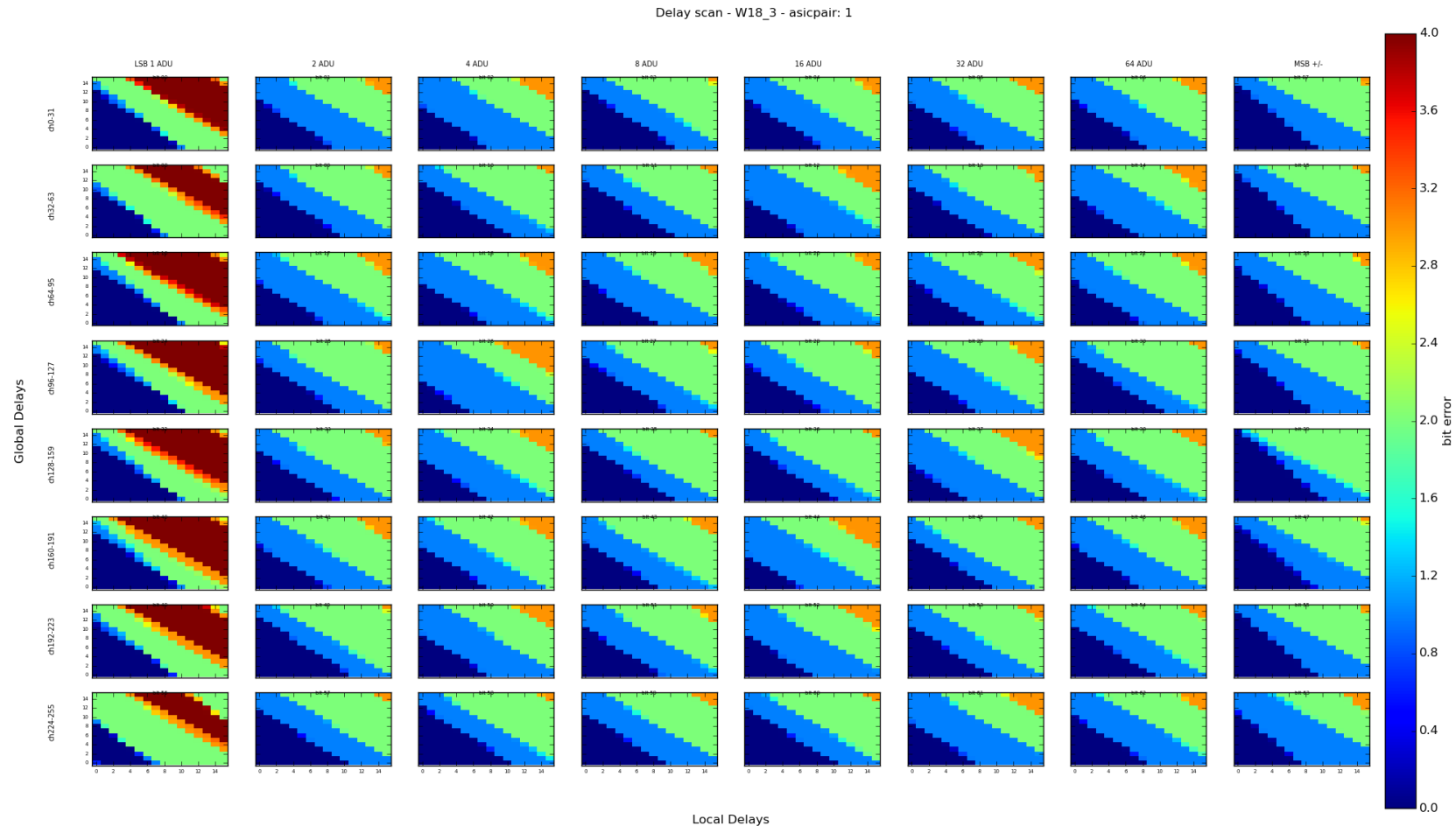


07.04.2015, T.Kishishita

Duty cycle degrades at most a few percent after max. delay.

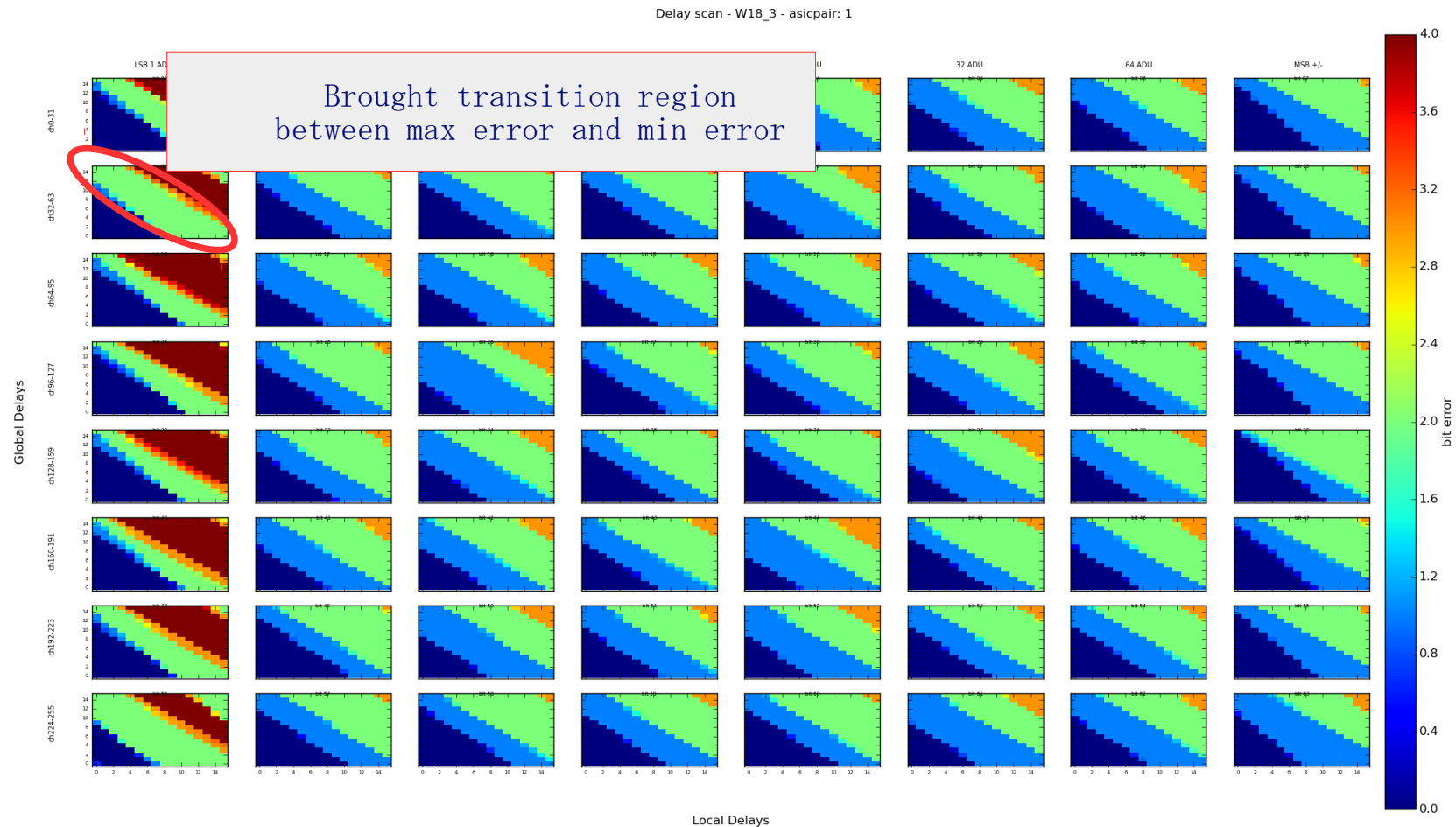
## DHPT 1.0: Duty cycle distortion of signal present

- Each inverter pairs introduces a duty cycle distortion



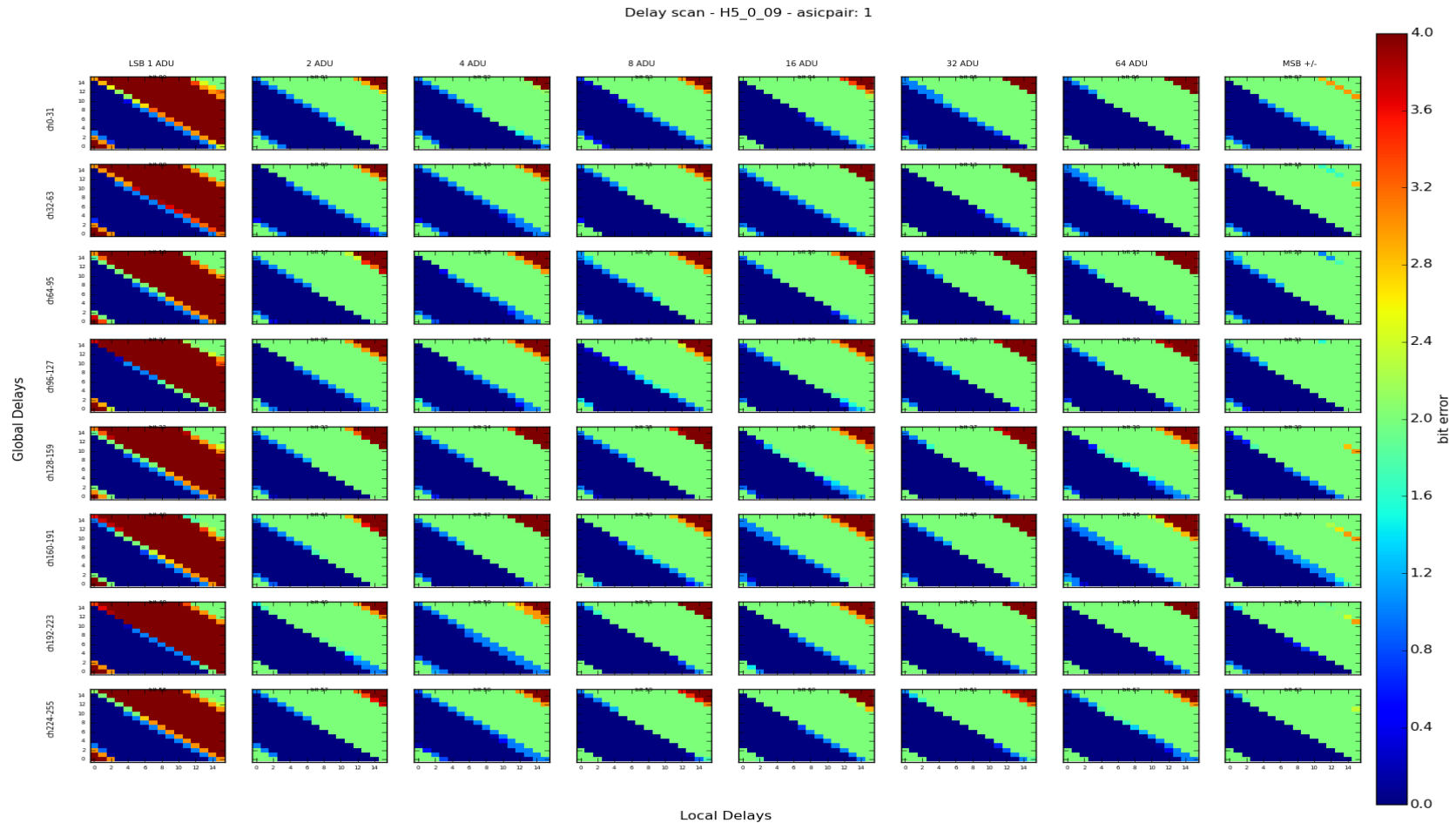
## DHPT 1.0: Duty cycle distortion of signal present

- Each inverter pairs introduces a duty cycle distortion

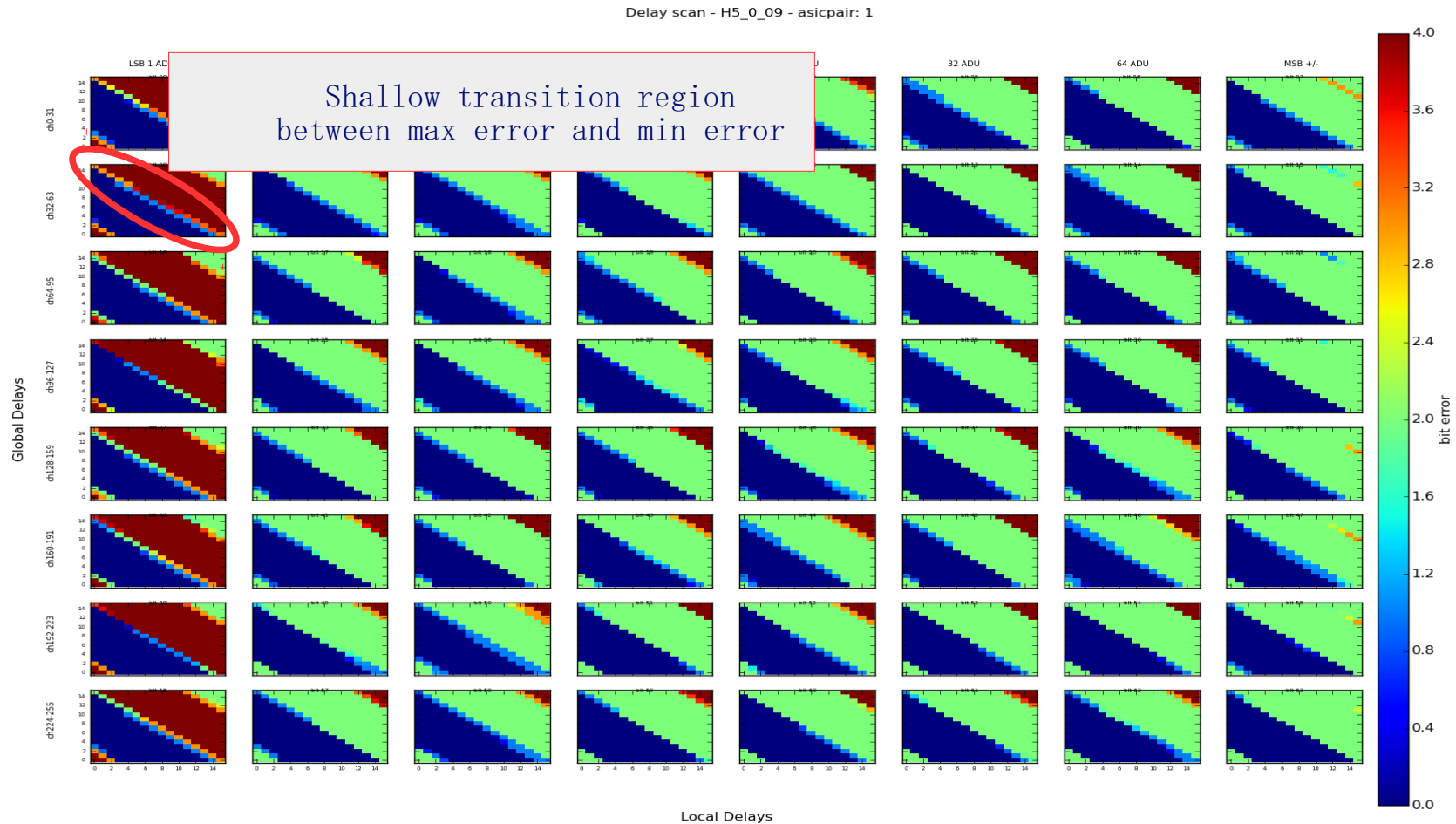




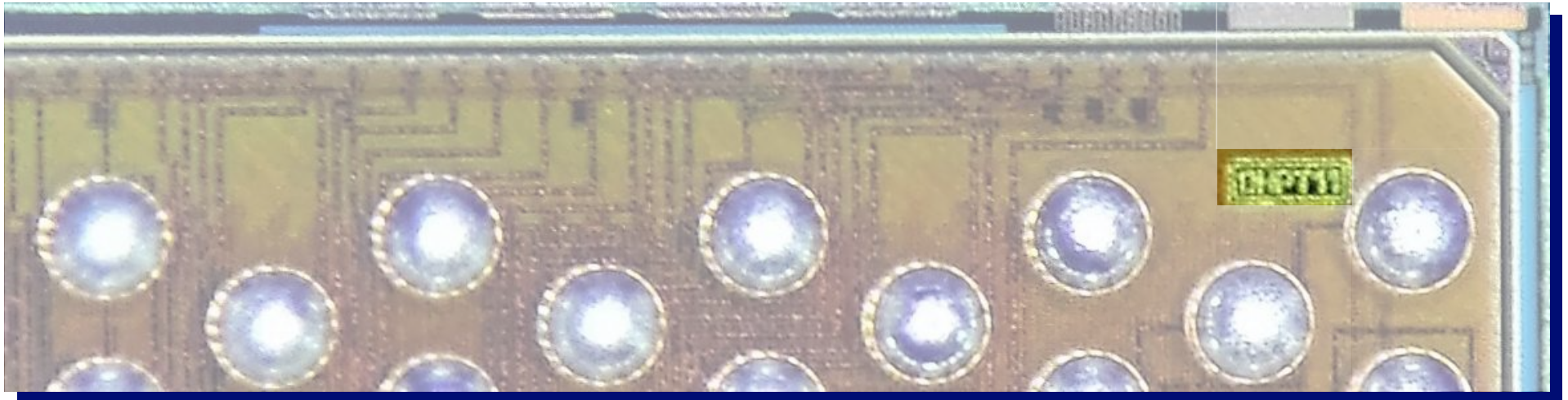
# DHPT 1.1: No duty cycle distortion of signal present



# DHPT 1.1: No duty cycle distortion of signal present

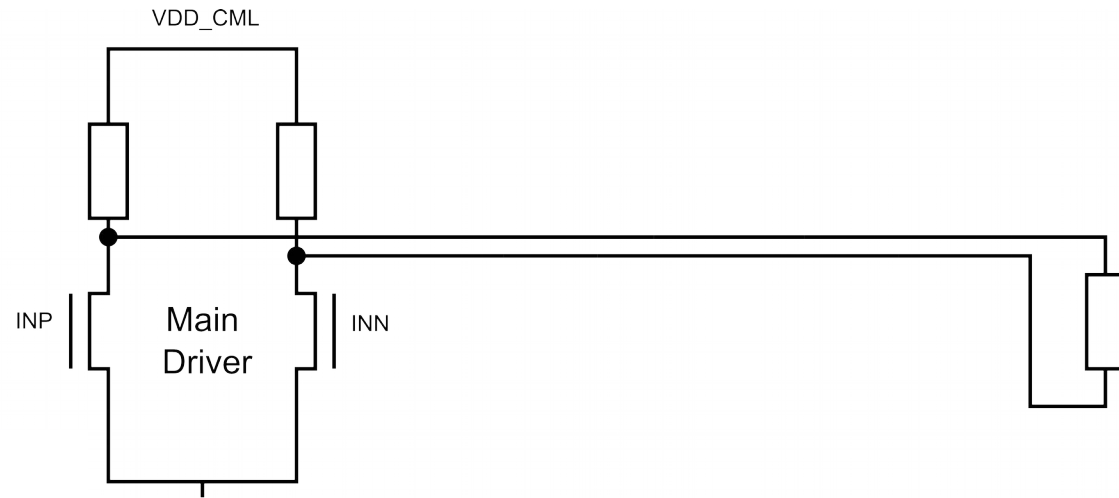


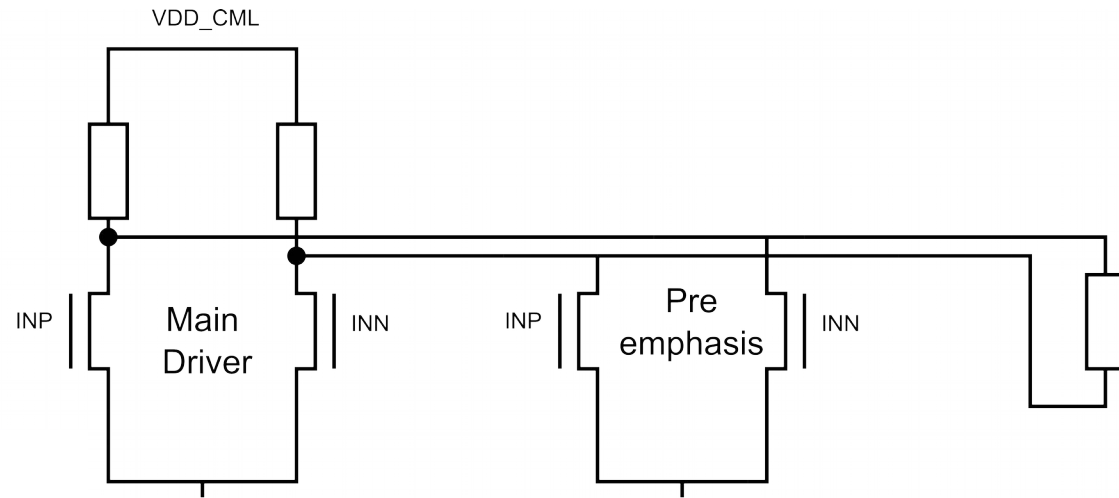
## Changes from DHPT1.0 to DHPT1.1

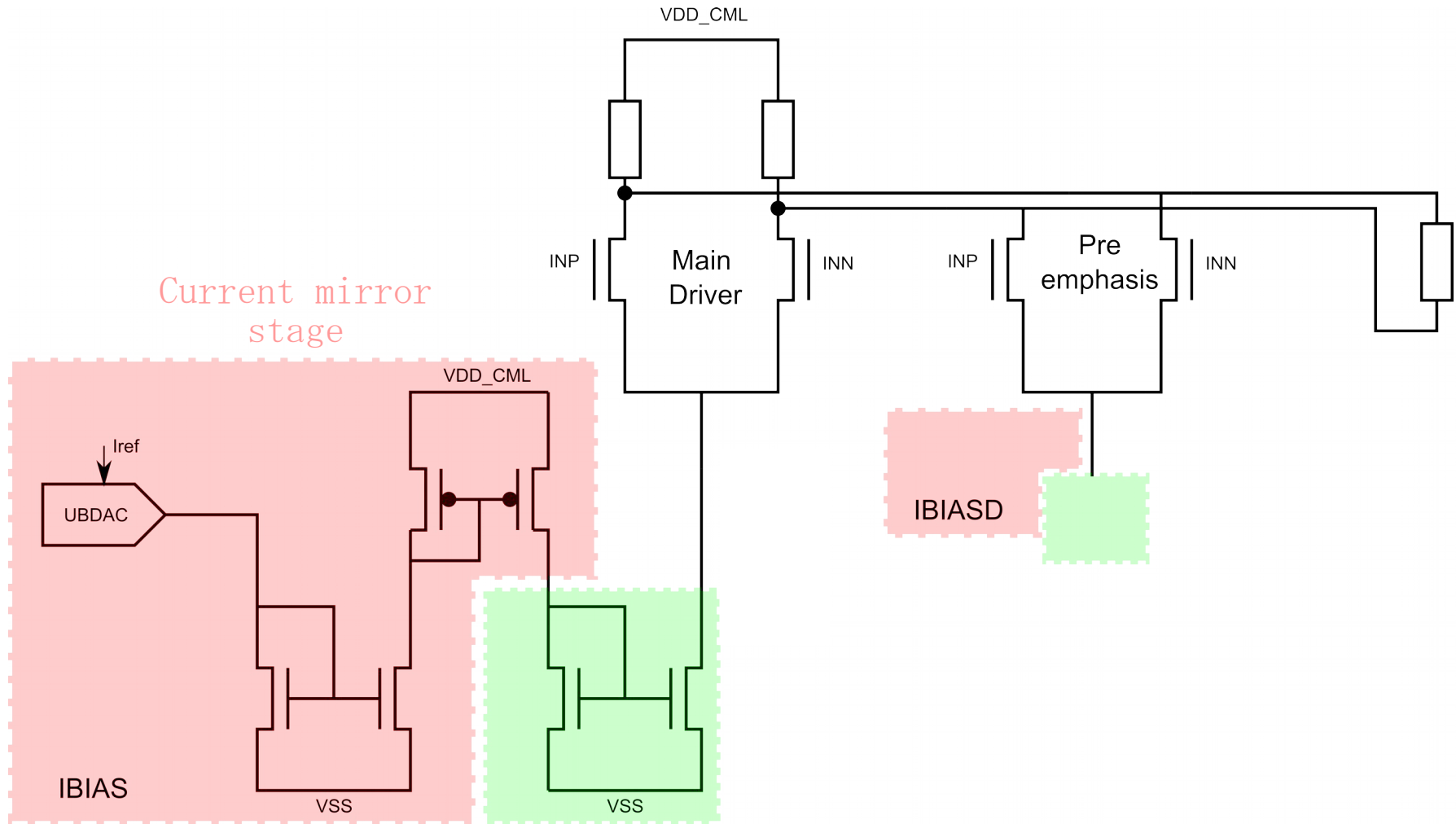


Results    Serial Link (CML Driver)

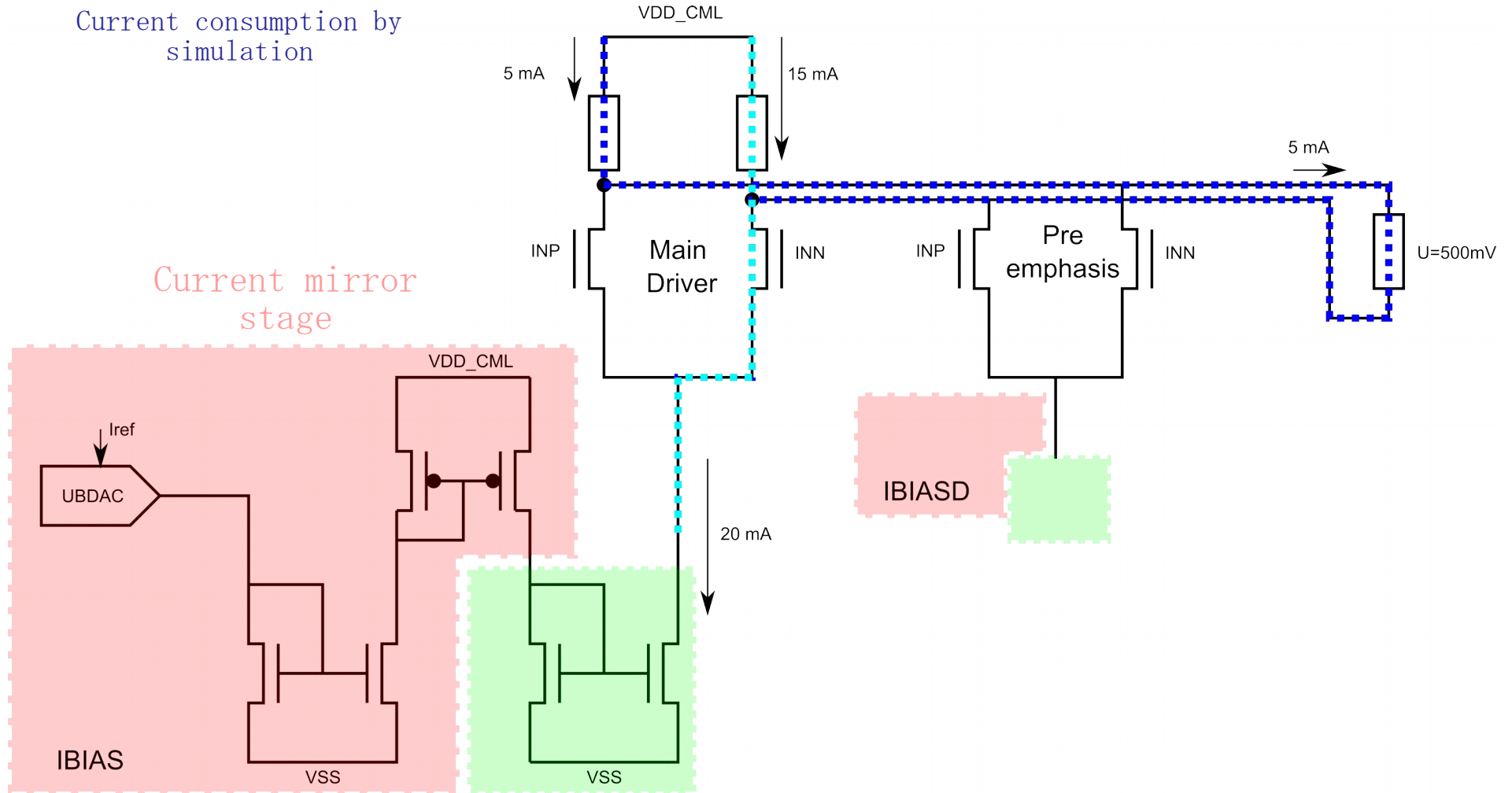






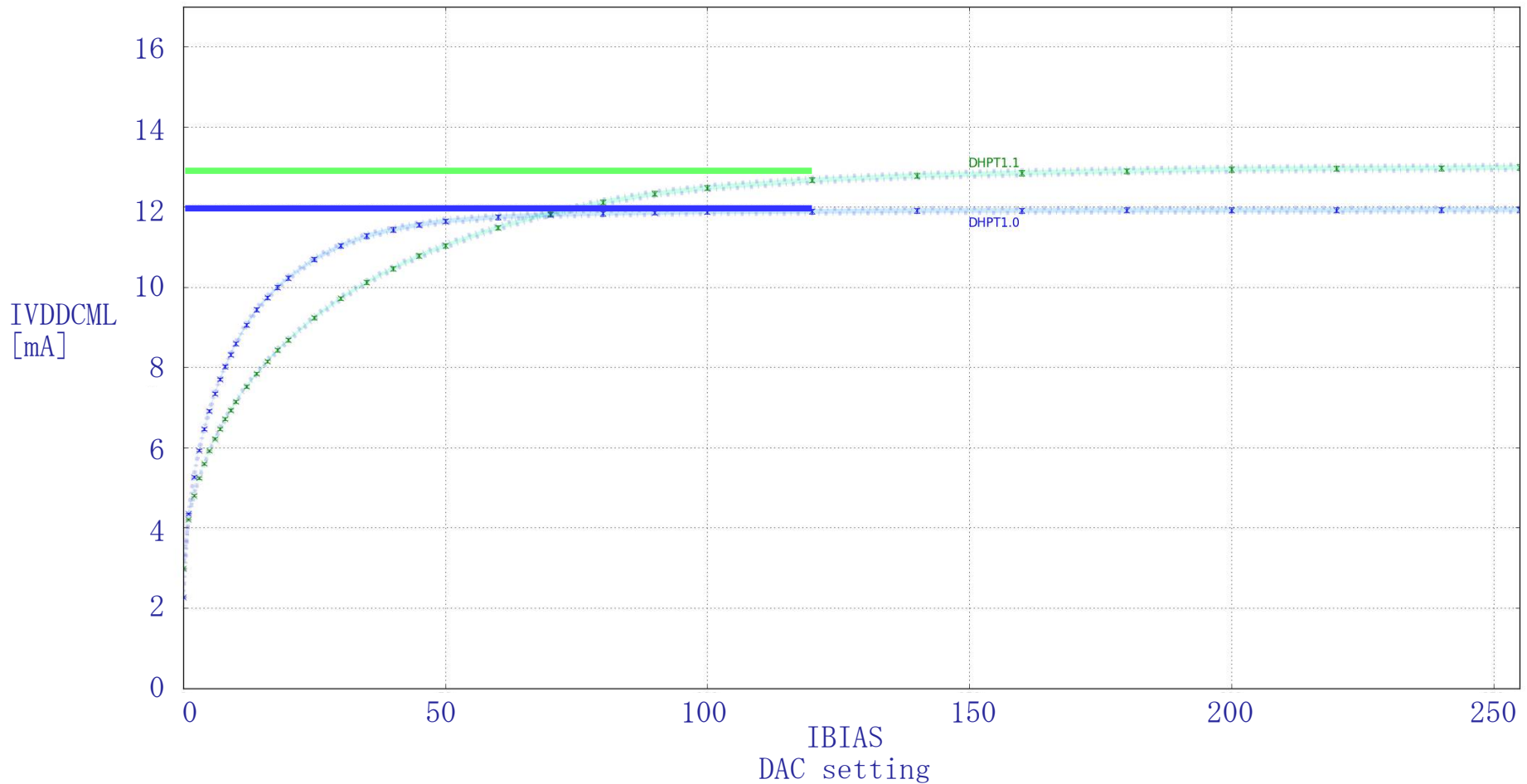


Current consumption by simulation

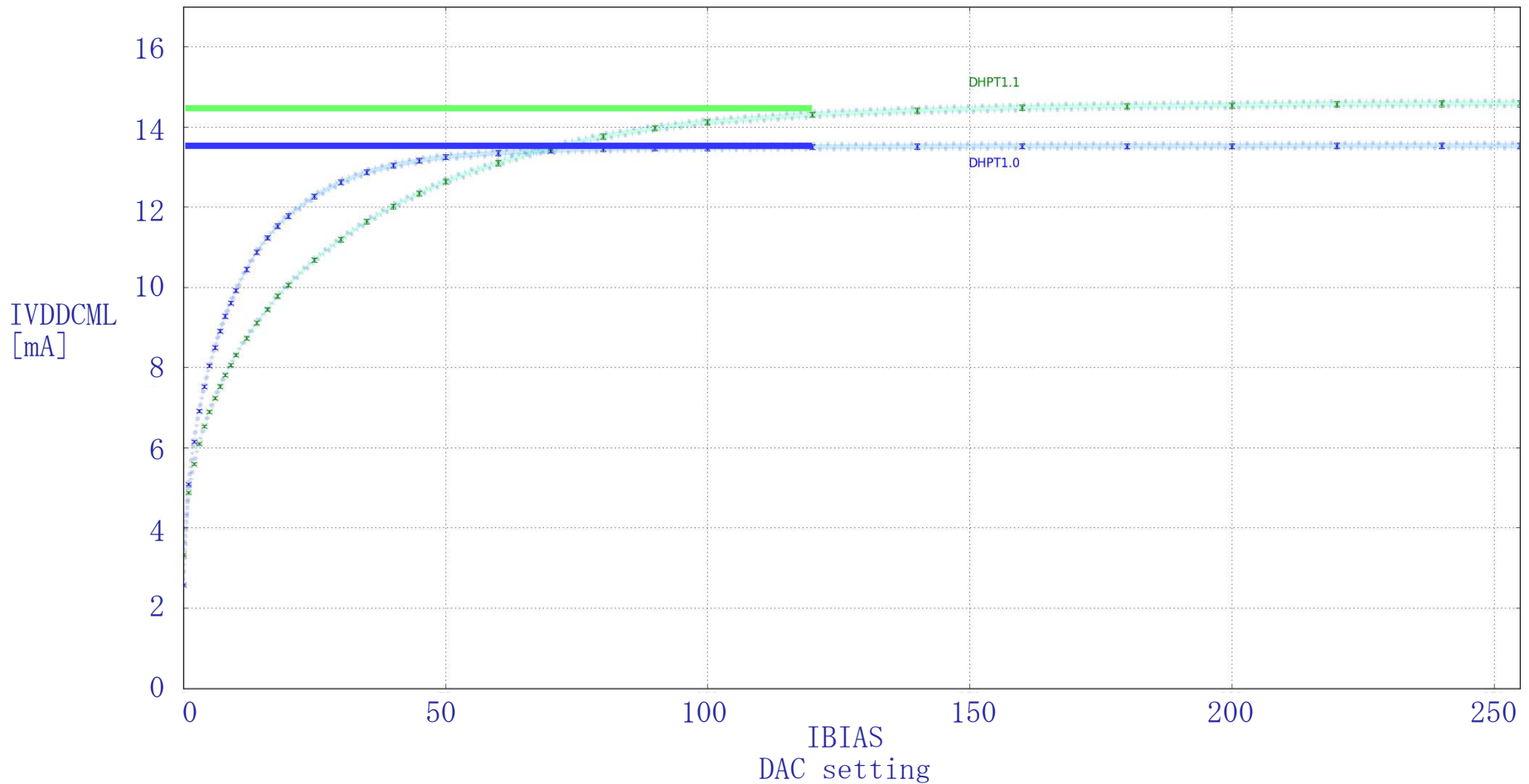




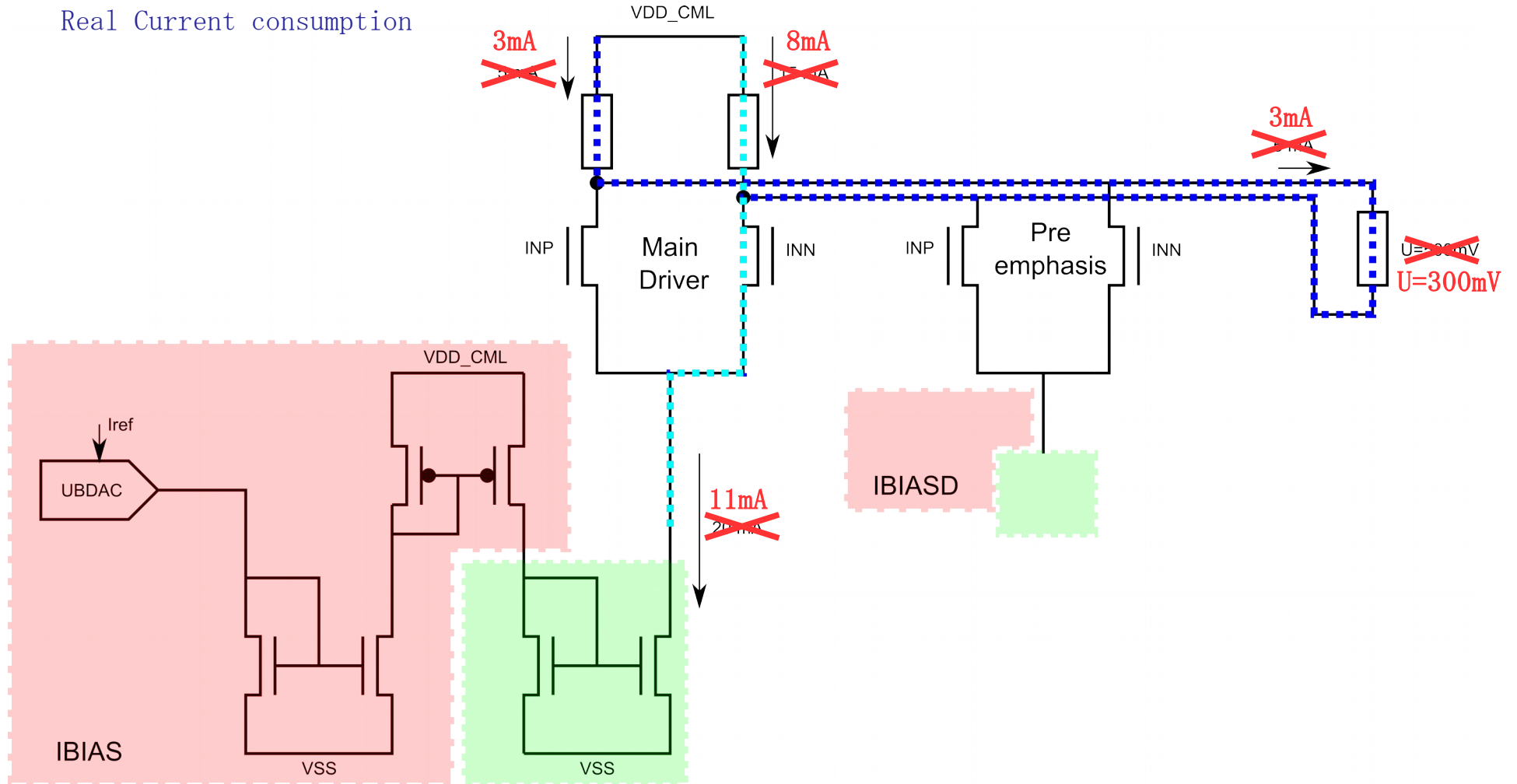
Current consumption  
VDD = VDDCML = 1.2V, DVDD = 1.8V



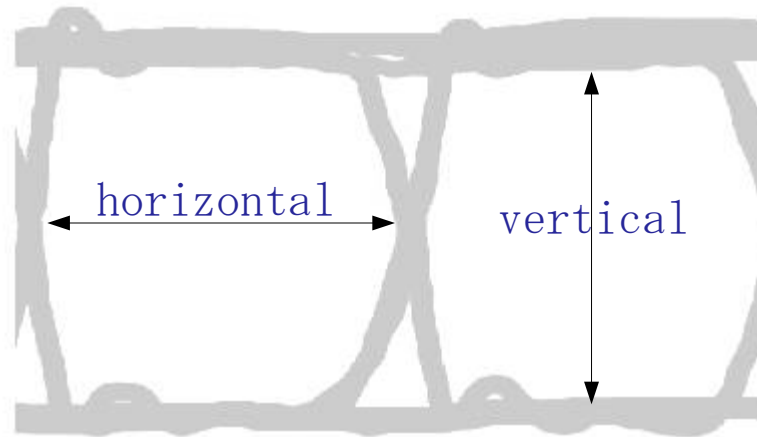
Current consumption  
 $VDD = VDDCML = 1.3V, DVDD = 1.8V$



Real Current consumption

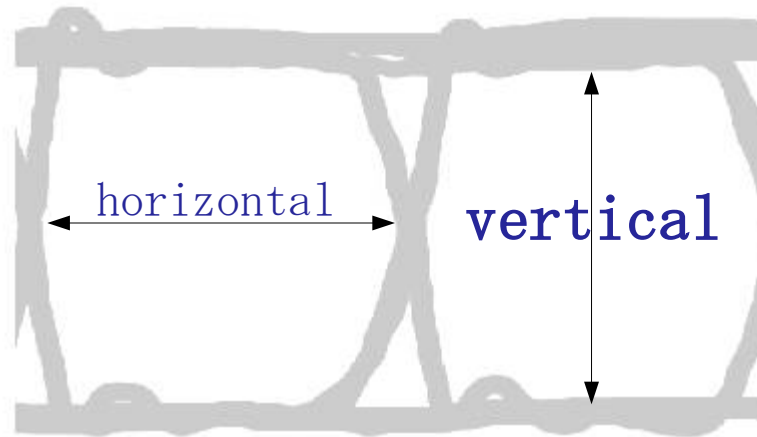


CML driver  
Eye diagram measurements





CML driver  
Eye diagram measurements



## DHE specification

*From Virtex-6 User Guide*

**Table 4-26: RX Margin Analysis Ports**

Port	Dir	Clock Domain	Description
RXDATA[31:0]	Out	RXUSRCLK2	The user needs to detect data errors on RXDATA in order to monitor the bit error rate of the link.
DFEYEDACMON[4:0]	Out	RXUSRCLK2	Average vertical eye height (voltage domain) used by the DFE as an optimization criterion. 11111: Indicates approximately 200 mV <sub>PPD</sub> of internal eye opening.

5bit value (0-31) for the vertical opening

*From Virtex-6 FPGA Data Sheet: DC and Switching Characteristics*

**Table 17: GTX Transceiver DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
DV <sub>PPIN</sub>	Differential peak-to-peak input voltage	External AC coupled ≤ 4.25 Gb/s	125	–	2000	mV
		External AC coupled > 4.25 Gb/s	175	–	2000	mV

Min 125mV vertical opening

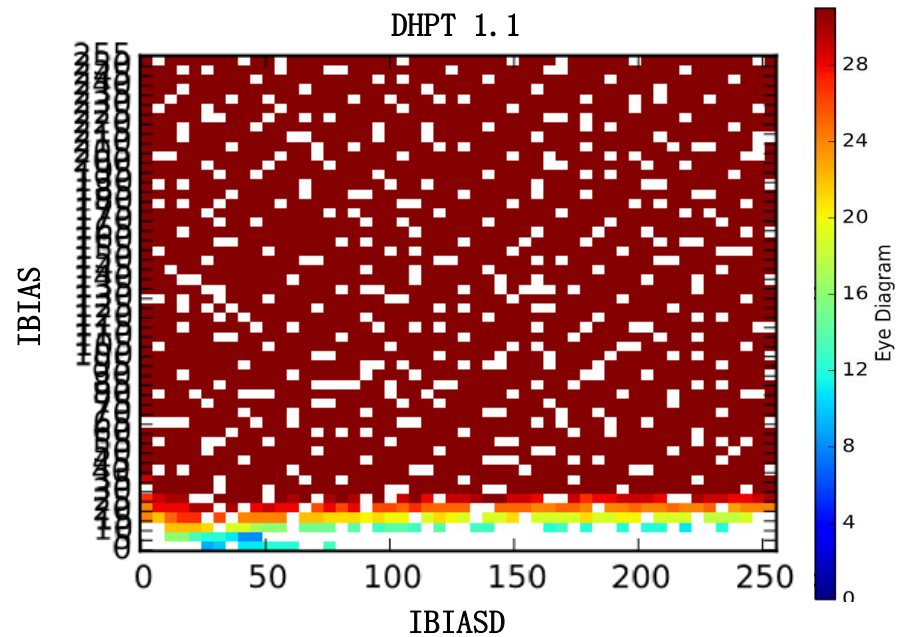
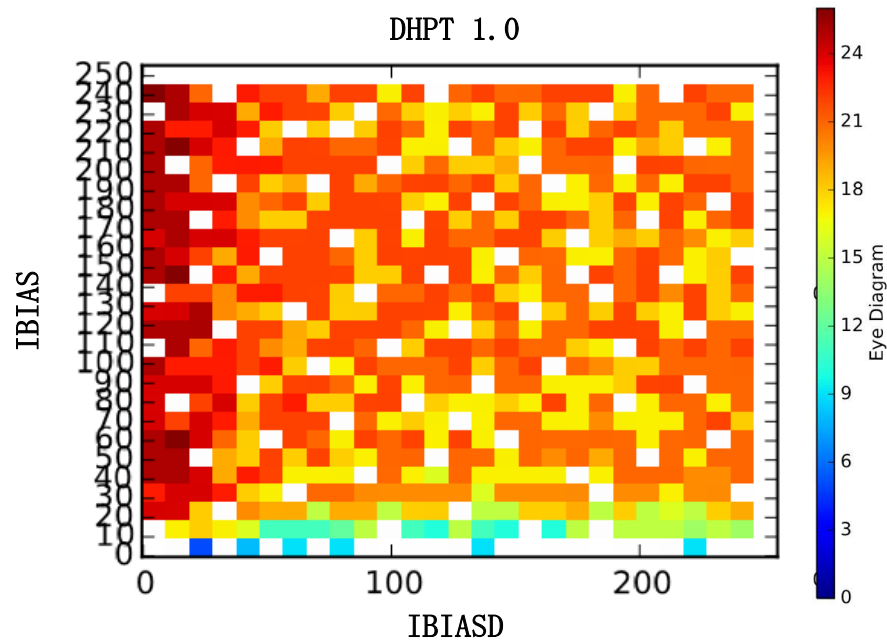
CML driver

Scan over parameter space

*IBIAS*, *IBIASD* and *pll\_cml\_dly*

no receiver equalizing

Examples for *pll\_cml\_dly* = 0 and GCK = 62.50 MHz



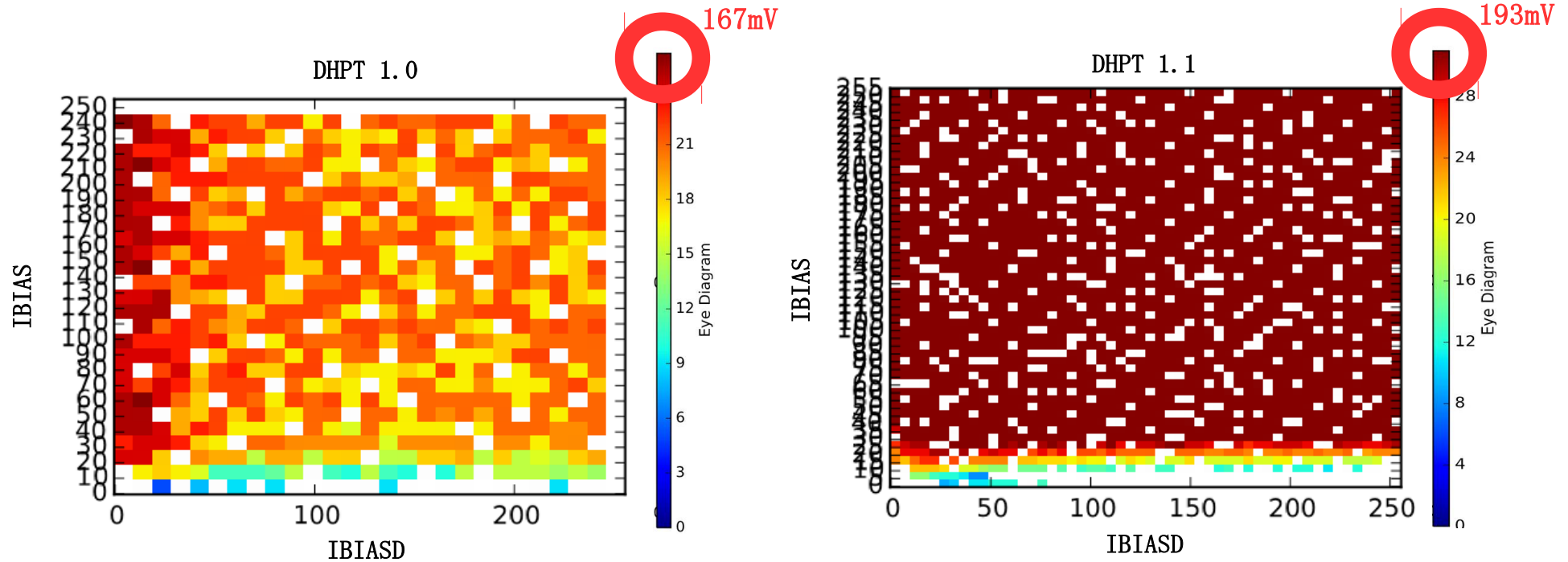
CML driver

Scan over parameter space

*IBIAS*, *IBIASD* and *pll\_cml\_dly*

no receiver equalizing

Examples for *pll\_cml\_dly* = 0 and GCK = 62.50 MHz





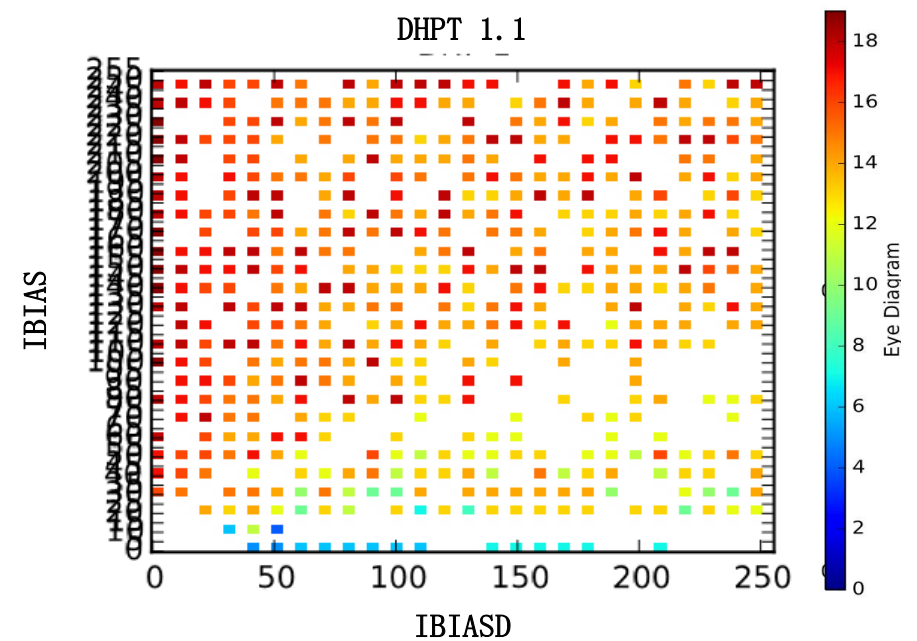
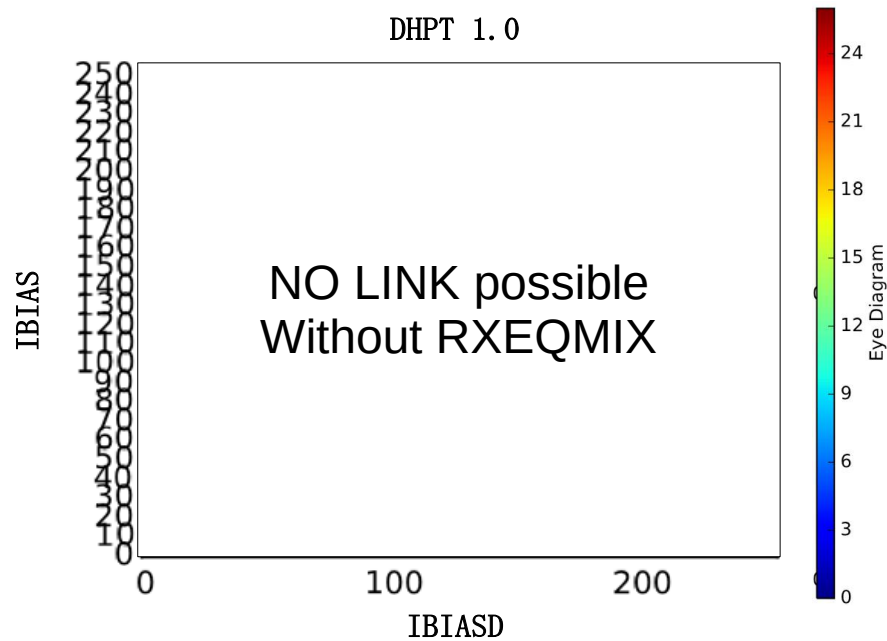
CML driver

Scan over parameter space

*IBIAS*, *IBIASD* and *pll\_cml\_dly*

no receiver equalizing

Examples for *pll\_cml\_dly* = 0 and GCK = 76.23 MHz



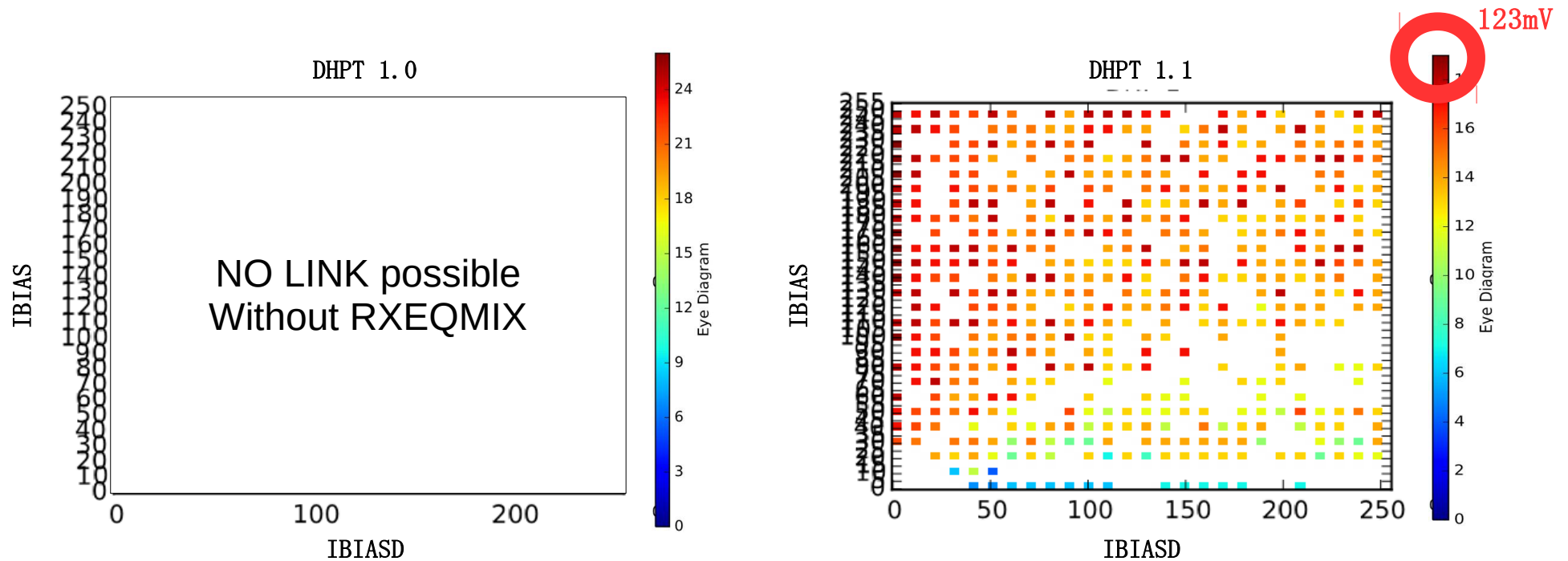
CML driver

Scan over parameter space

*IBIAS*, *IBIASD* and *pll\_cml\_dly*

no receiver equalizing

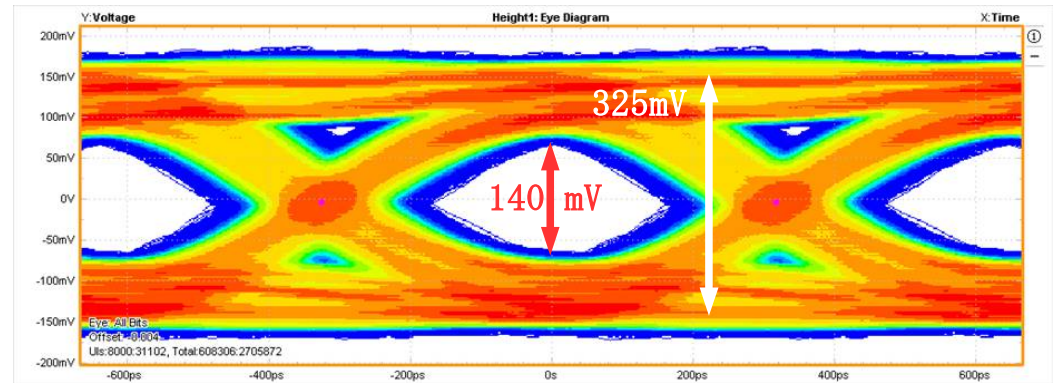
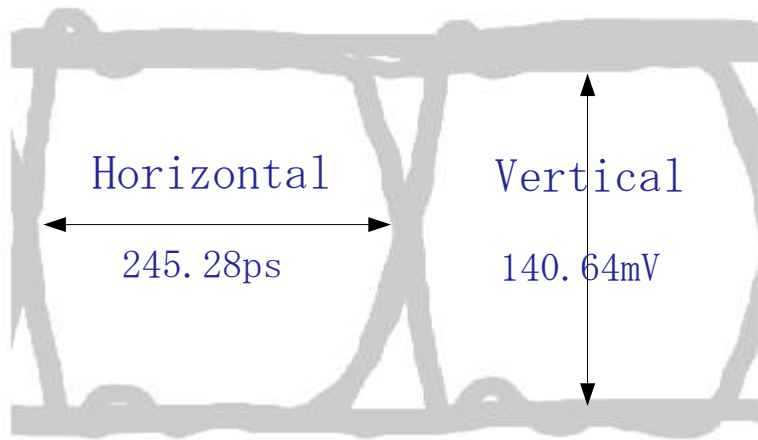
Examples for *pll\_cml\_dly* = 0 and GCK = 76.23 MHz



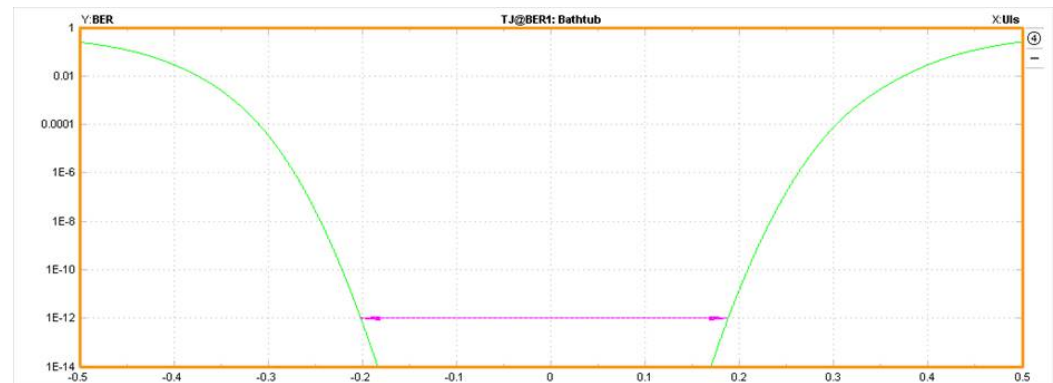
CML driver

Best eye diagram  
 With adjusted PLL settings  
 (jitter improvement)  
 for **15m** TWP cable

Virtex5/6 specs: min 125mV  
 for < 4.95Gbps

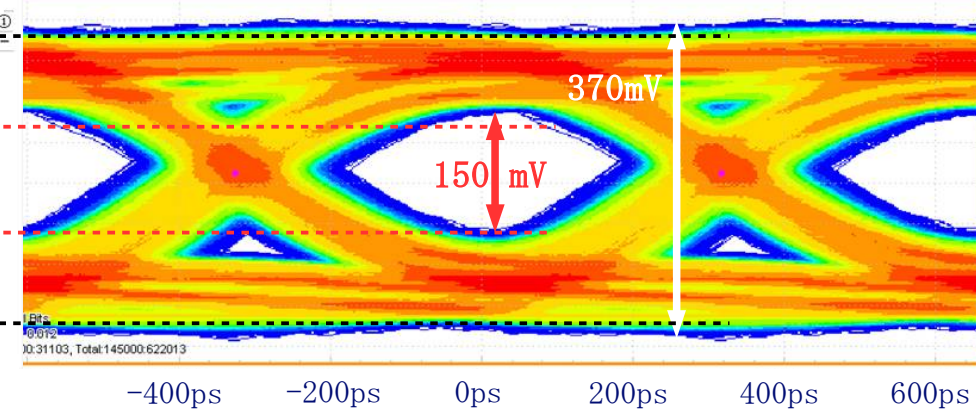
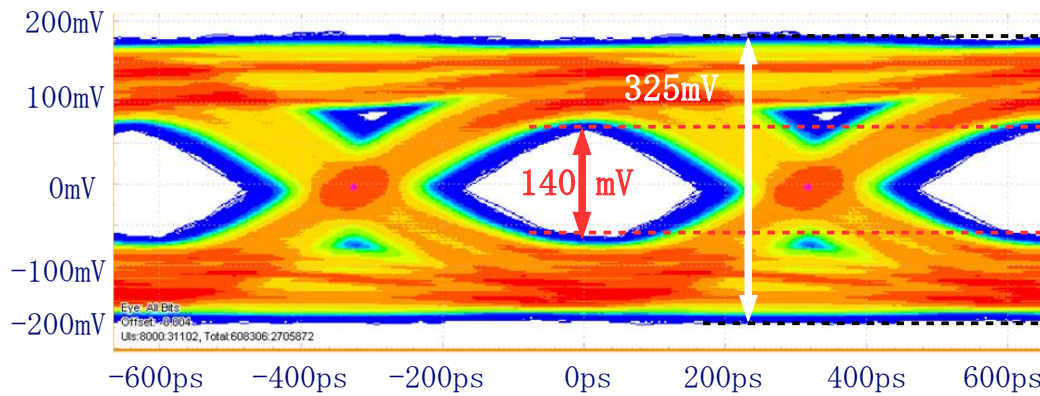


IBIAS =255 IBIASD =20 pll\_cml\_dly\_sel =1  
 PLL\_ICP =255(10) PLL\_VCO =255(96) IREF =15(8)



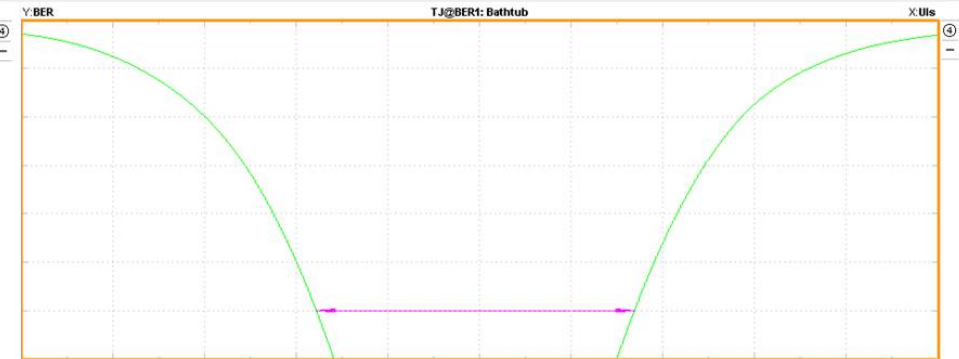
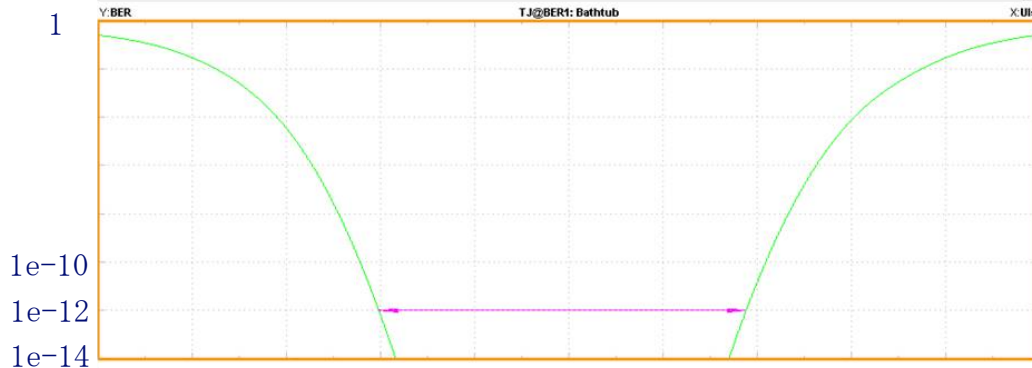
VDD=VDD\_CML=1.2V

VDD=VDD\_CML=1.3V



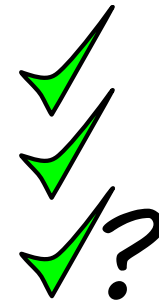
IBIAS =255    IBIAS =20    pll\_cml\_dly\_sel =1  
 PLL\_ICP =255(10)    PLL\_VC0 =255(96)    IREF =15(8)

IBIAS =255    IBIAS =20    pll\_cml\_dly\_sel =1  
 PLL\_ICP =255(10)    PLL\_VC0 =255(96)    IREF =15(8)



Improvement of the design achieved:

- a) Resolvment of the Serializer Bug
- b) IO Buffer delay do not suffer from duty cycle distortion
- c) Slight improvement of the CML driver



The diviation of the CML driver performance with respect to simulation vs real measurement needs to be investigated in more detail

Tests and Measurements prove that the DHPT 1.1 is in a very good shape for the final experiment.

## Production

- Tape-out: September 9, 2015
- Delivery (100 bumped samples): November 14, 2015

## Changes from DHPT 1.0 to DHPT 1.1

- DCD – DHPT Interface
  - Improved data receiver pads (no hysteresis, reduced input capacitance)
  - New delay elements (improved duty cycle balance)
- Serial Data Link
  - New Serializer (fix of the timing bug)
  - Improvement of the CML driver (reduction of parasitic resistances)

➔ Digital part did not change (data processing, configuration etc.)



- Decision for DHPT 1.1 as the production candidate by February (?)
  - Then: Order of 9 additional wafers (1000 chips in total)
  - Two new needle cards for probe station testing currently being produced (HTT)
- ➔ Estimated testing throughput: ~50 chips per week

If a further DHPT re-design should be unavoidable (for example: Gated-mode operation not yet tested) a DHPT 1.2 with changes in the digital part will be designed and submitted.

- One month re-design (digital synthesis)
  - Two months production
- ➔ ~3 months delay in the delivery of chips for PXD production



**Thank you**

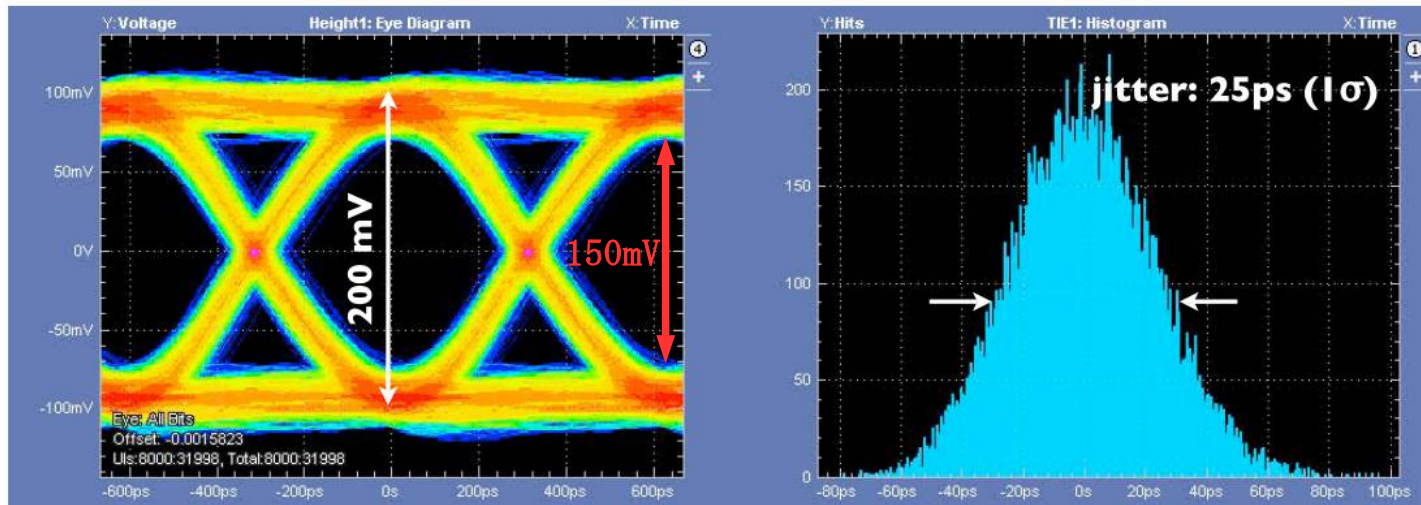


# Back up



# Signal Integrity Analysis

- ◆ 1.6 Gbps, 8bit LFSR sequence **38 cm flex** (I.V.) + **10m** Infiniband cable (LEONI, AWG 26)
- ◆ Max. pre-emphasis settings

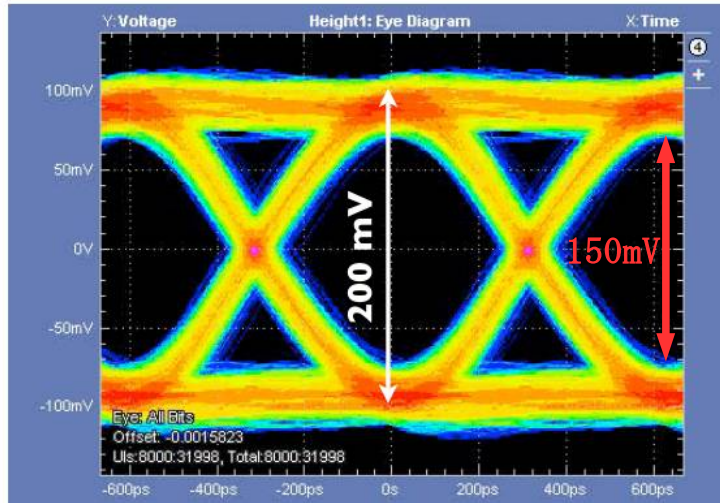


10m + 0.38m Kapton

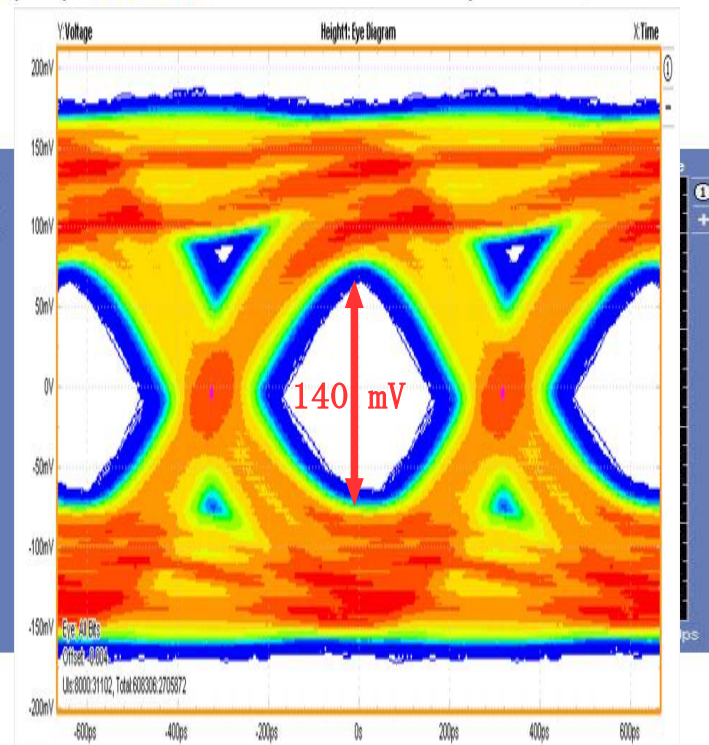
15m TWP  
DHPT1.1 (fullscale) -18/20-

# Signal Integrity Analysis

- ◆ 1.6 Gbps, 8bit LFSR sequence **38 cm flex** (I.V.) + **10m** Infiniband cable (LEONI, AWG 26)
- ◆ Max. pre-emphasis settings



10m TWP + 0.38m Kapton  
DHPT0.1 (test)

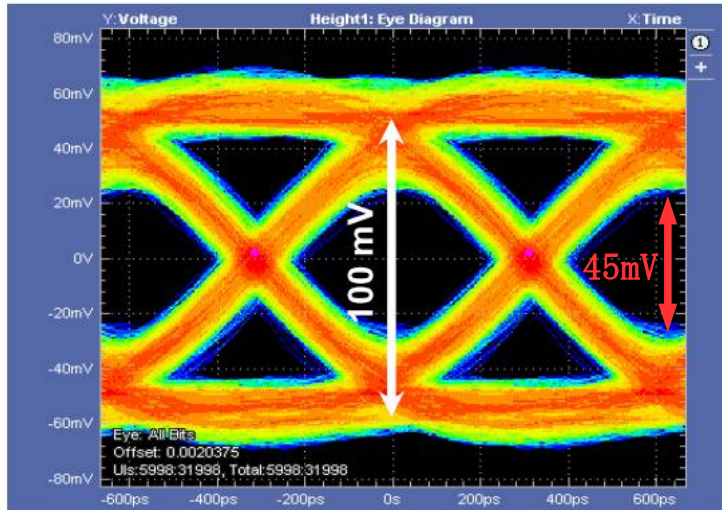


15m TWP  
DHPT1.1 (fullscale)

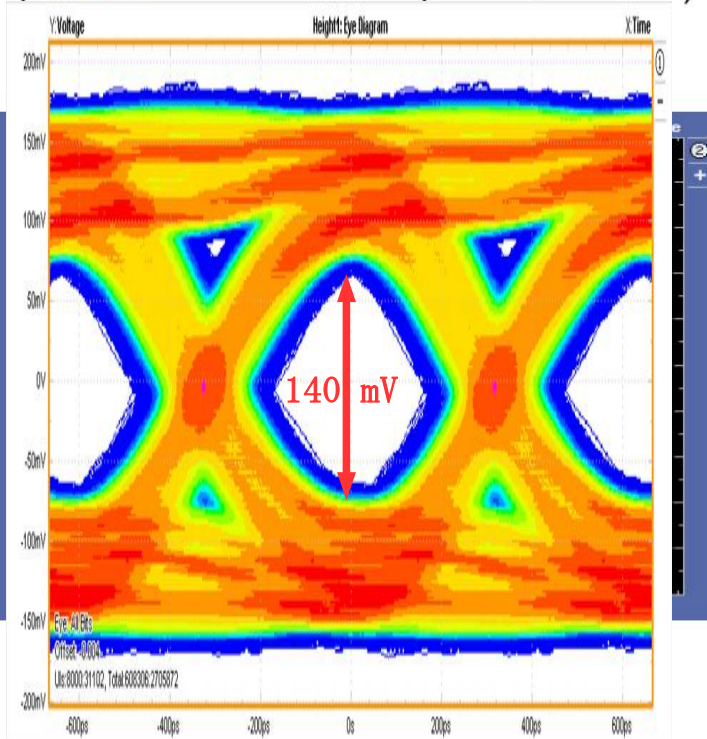


# Signal Integrity Analysis

1.6 Gbps, 8bit LFSR sequence **38 cm flex** (I.V.) + **20m** Infiniband cable (LEONI, AWG 26)  
 Max. pre-emphasis settings

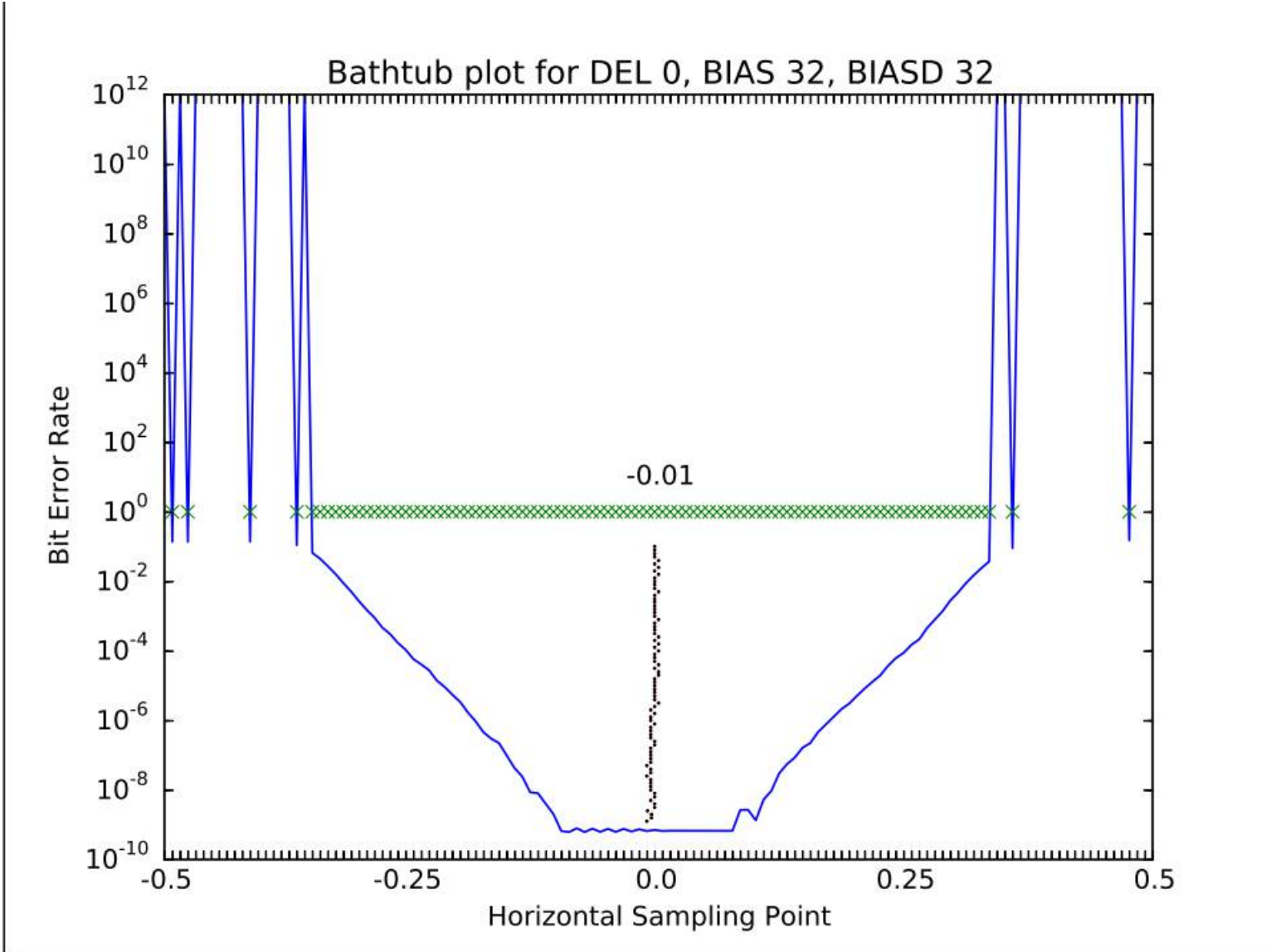


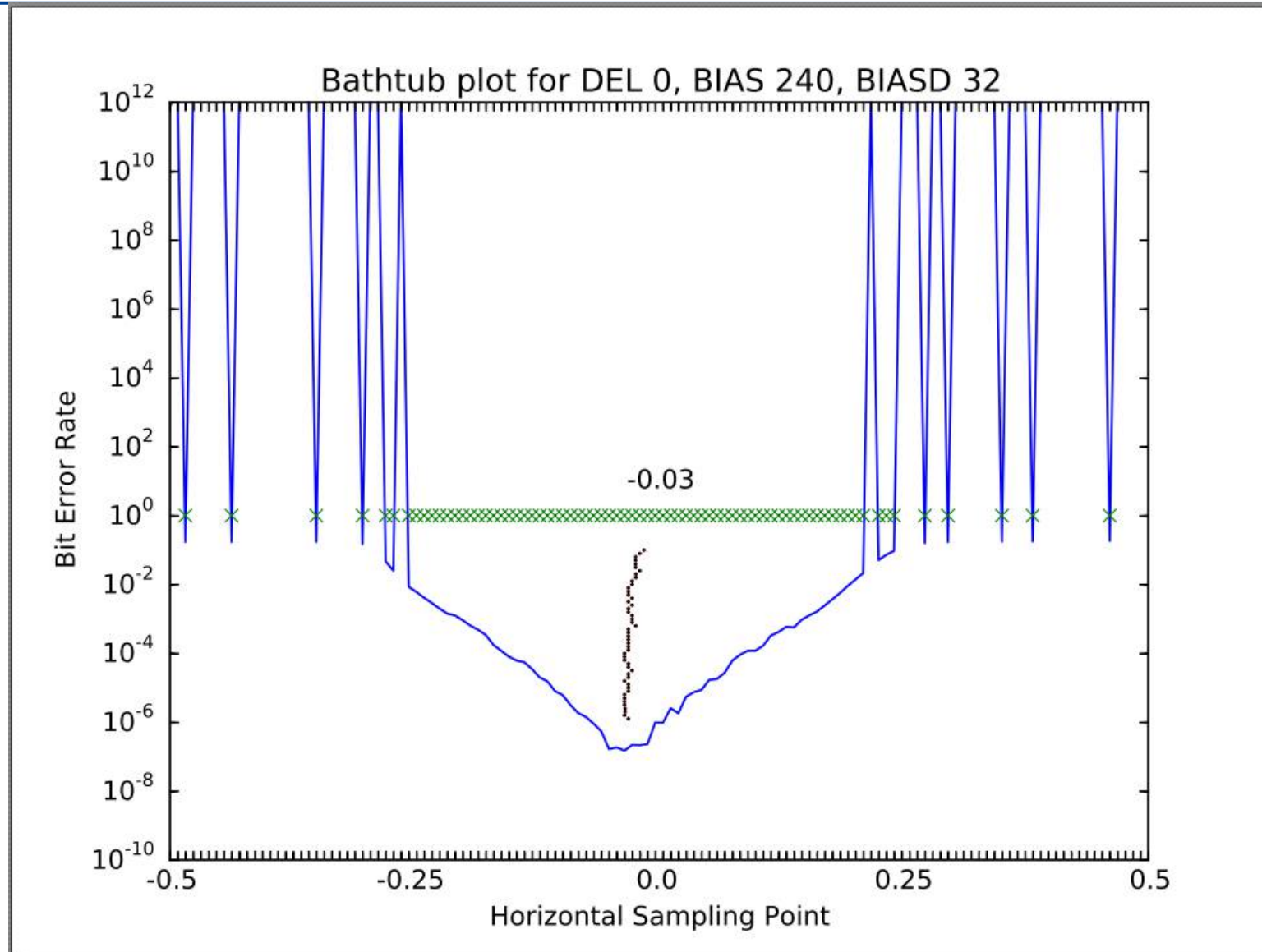
20m TWP + 0.38m Kapton  
 DHPT0.1 (test)



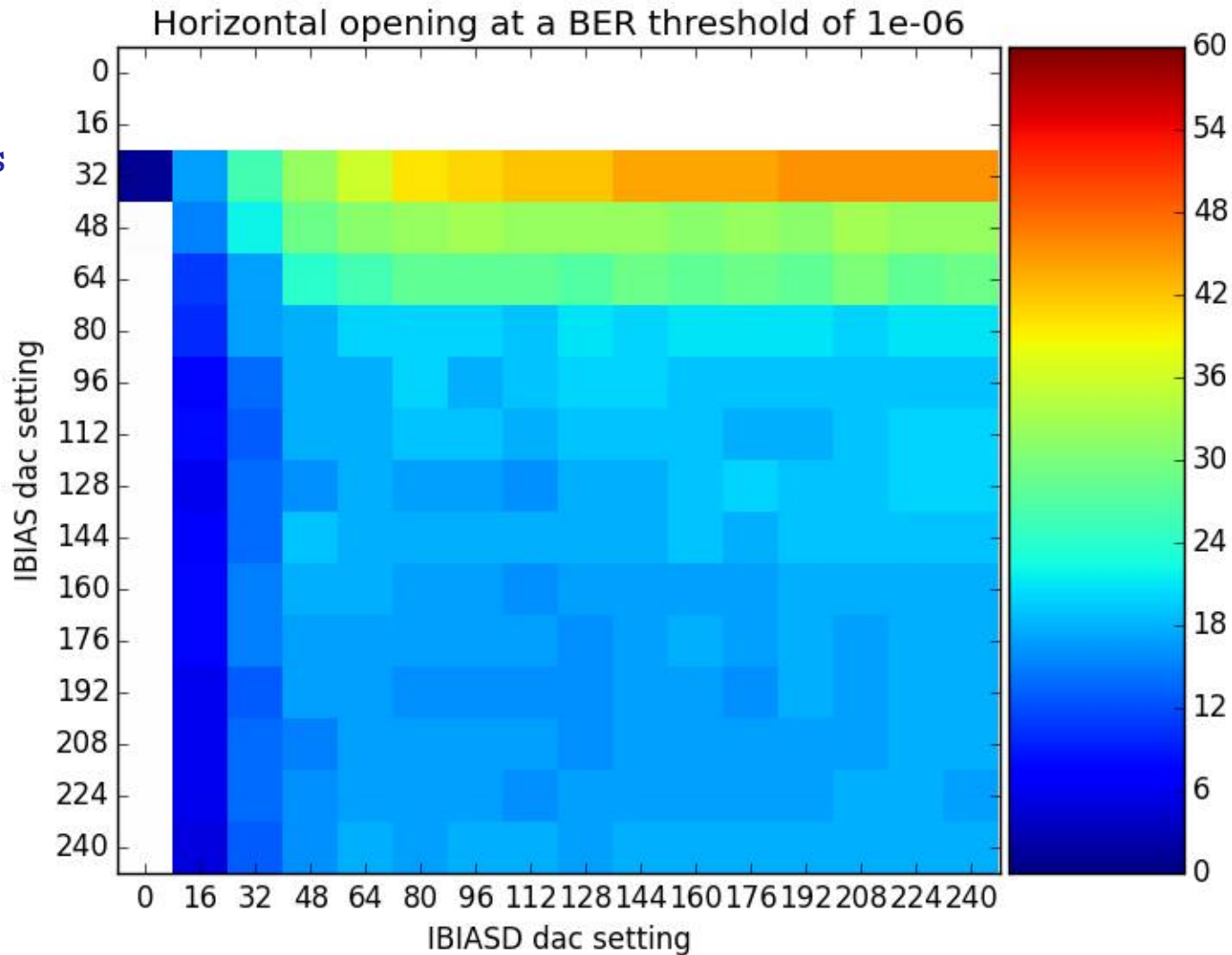
15m TWP  
 DHPT1.1 (fullscale) -19/20-



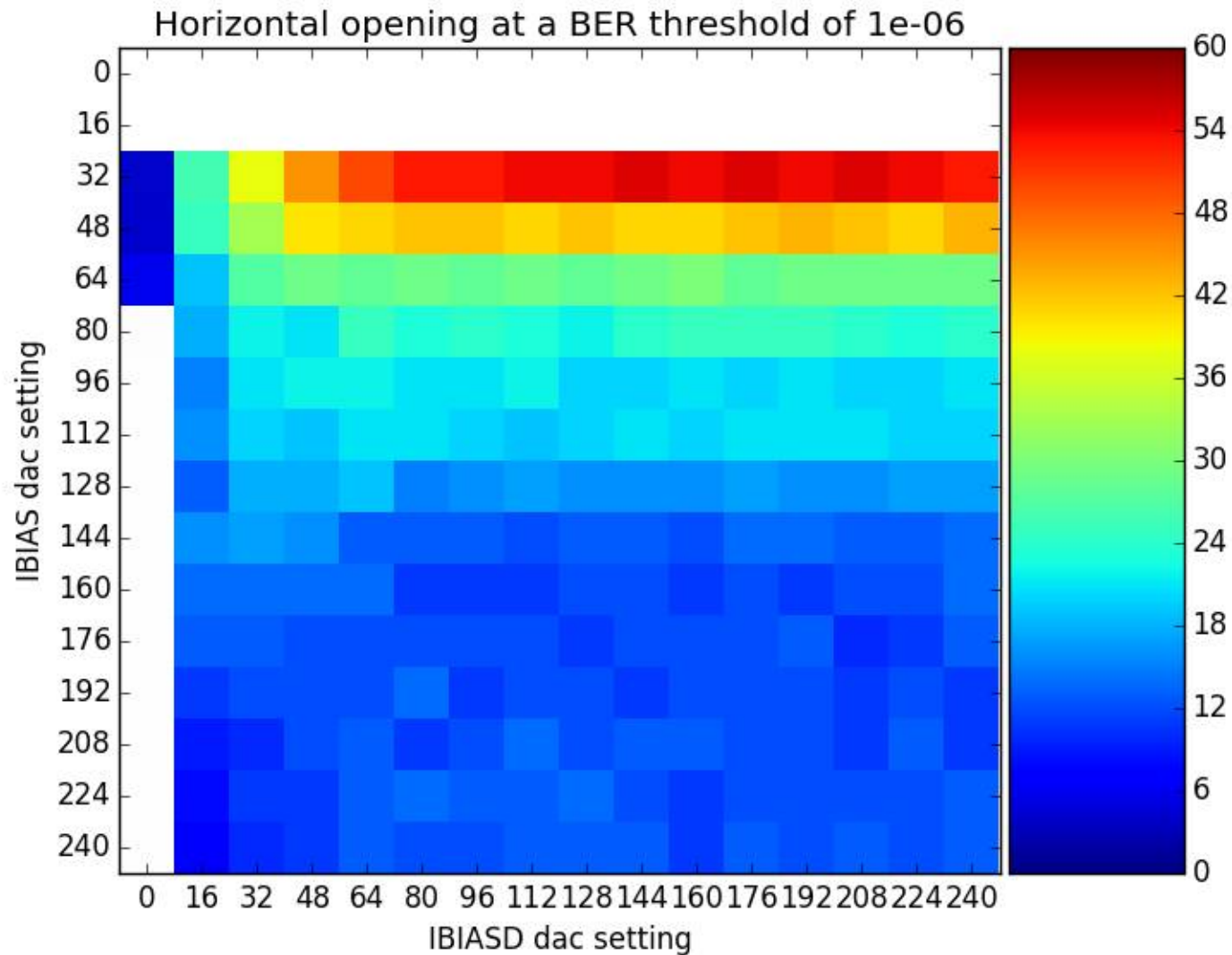




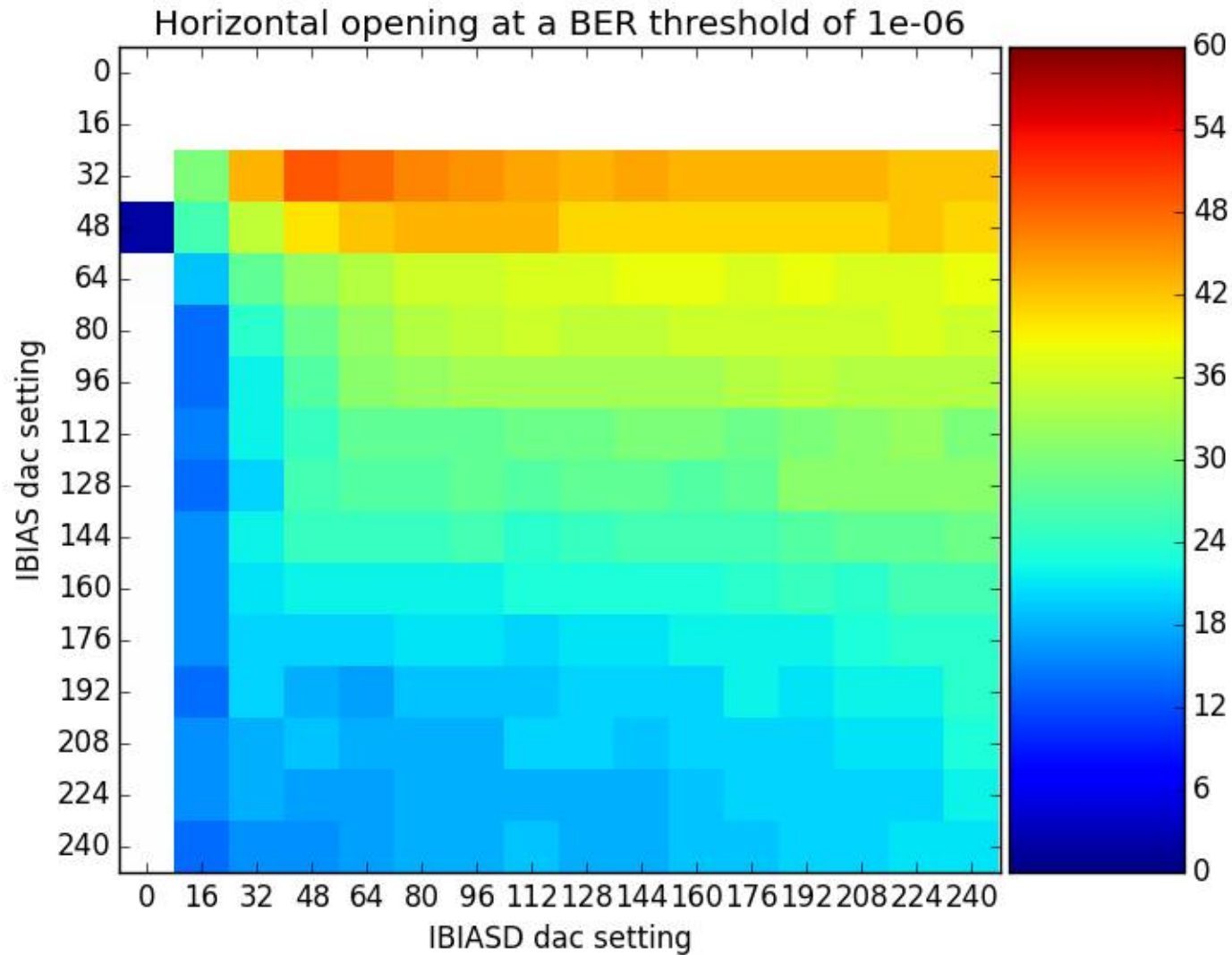
DLY3  
Small  
preemphasis  
width



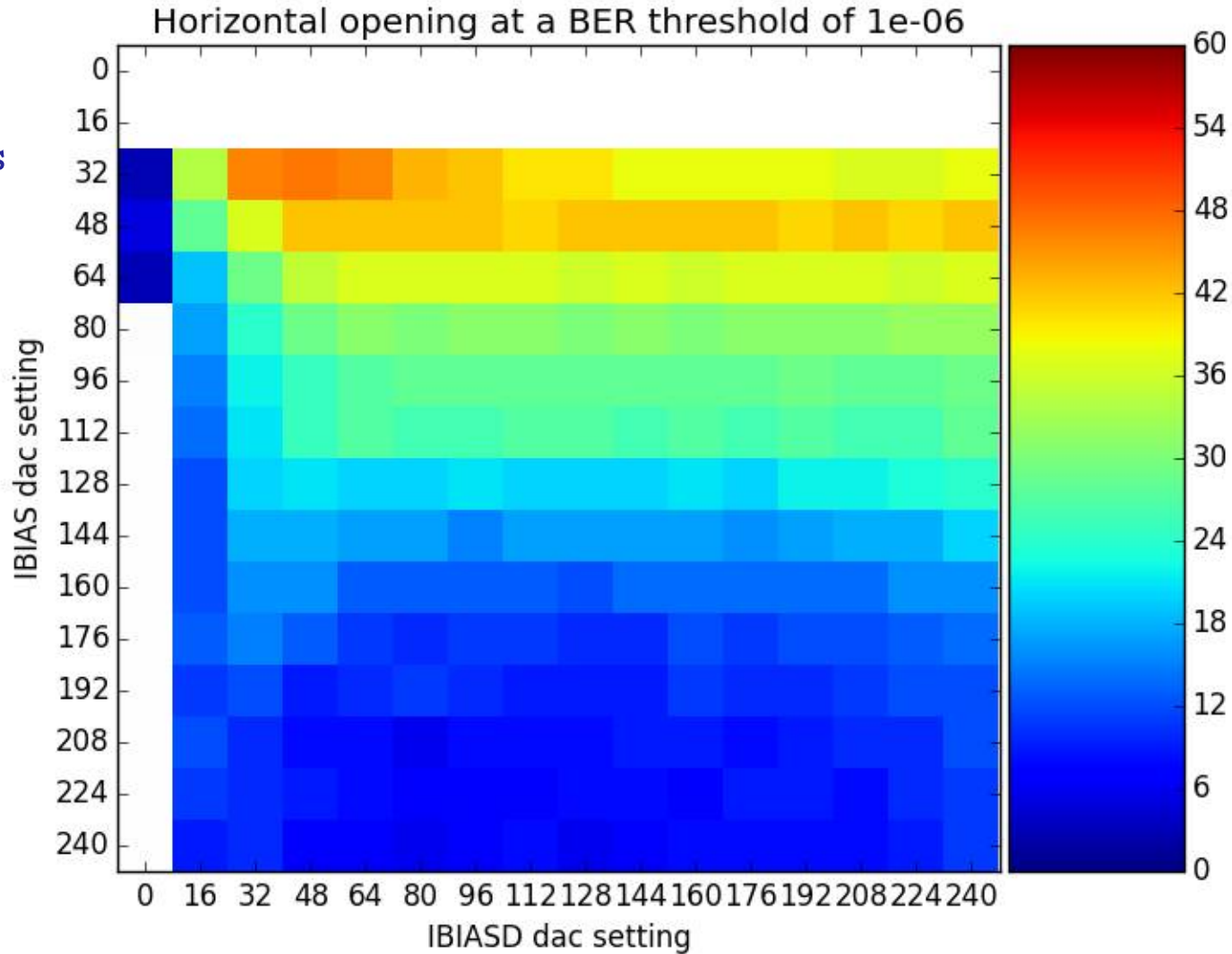
DLY2



DLY1



DLY0  
Large  
preemphasis  
width





# Changes from DHPT 1.0 to DHPT 1.1

VXD Workshop, Valencia

Jan 13-15, 2016

## Production

- Tape-out: September 9, 2015
- Delivery (100 bumped samples): November 14, 2015

## Changes from DHPT 1.0 to DHPT 1.1

- DCD – DHPT Interface
  - Improved data receiver pads (no hysteresis, reduced input capacitance)
  - New delay elements (improved duty cycle balance)
- Serial Data Link
  - New Serializer (fix of the timing bug)
  - Improvement of the CML driver (reduction of parasitic resistances)

➔ Digital part did not change (data processing, configuration etc.)

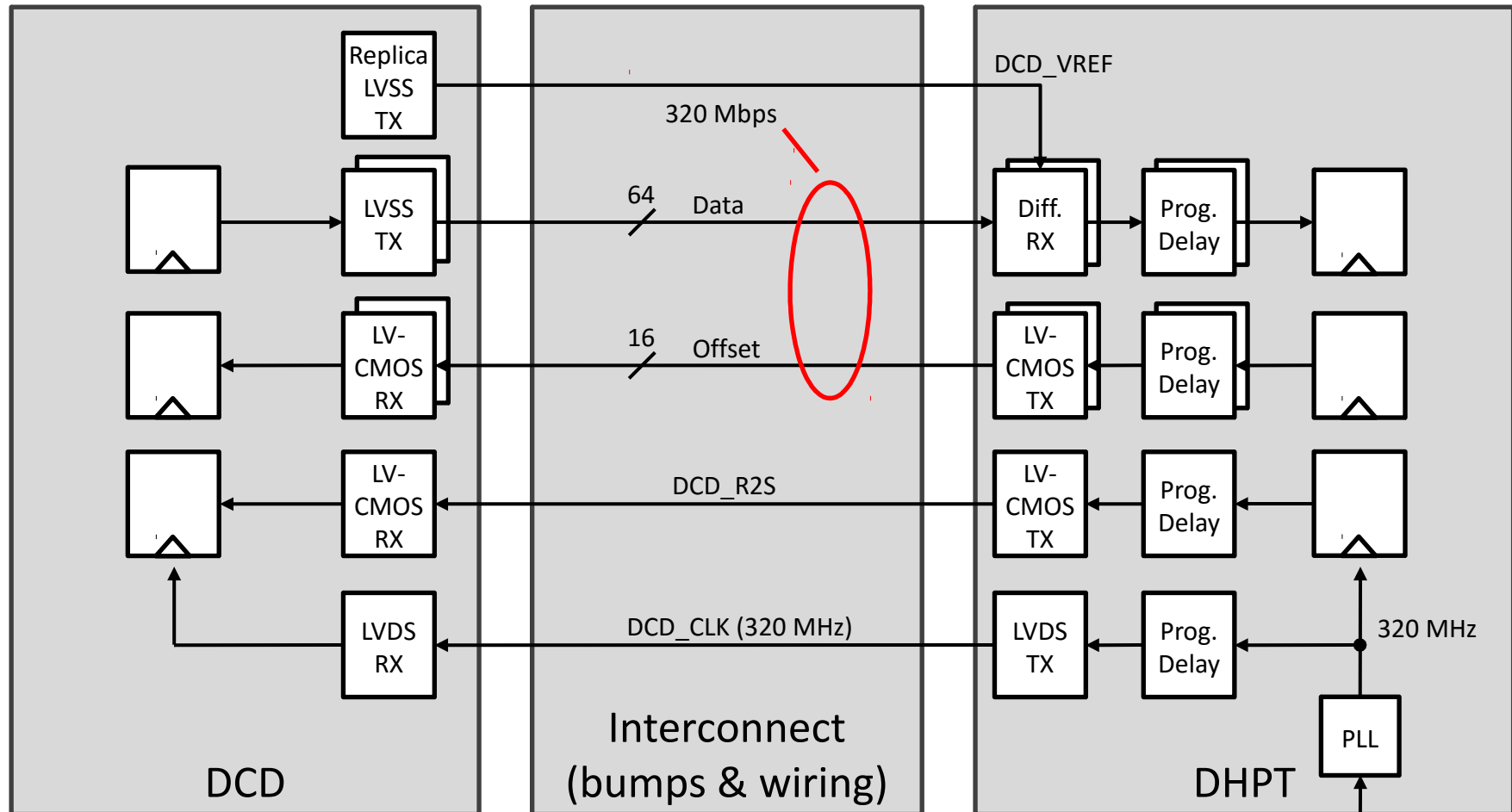
- Decision for DHPT 1.1 as the production candidate by February (?)
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  - Two new needle cards for probe station testing currently being produced (HTT)
- ➔ Estimated testing throughput: ~50 chips per week

If a further DHPT re-design should be unavoidable (for example: Gated-mode operation not yet tested) a DHPT 1.2 with changes in the digital part will be designed and submitted.

- One month re-design (digital synthesis)
  - Two months production
- ➔ ~3 months delay in the delivery of chips for PXD production

# DCD- DHPT INTERFACE

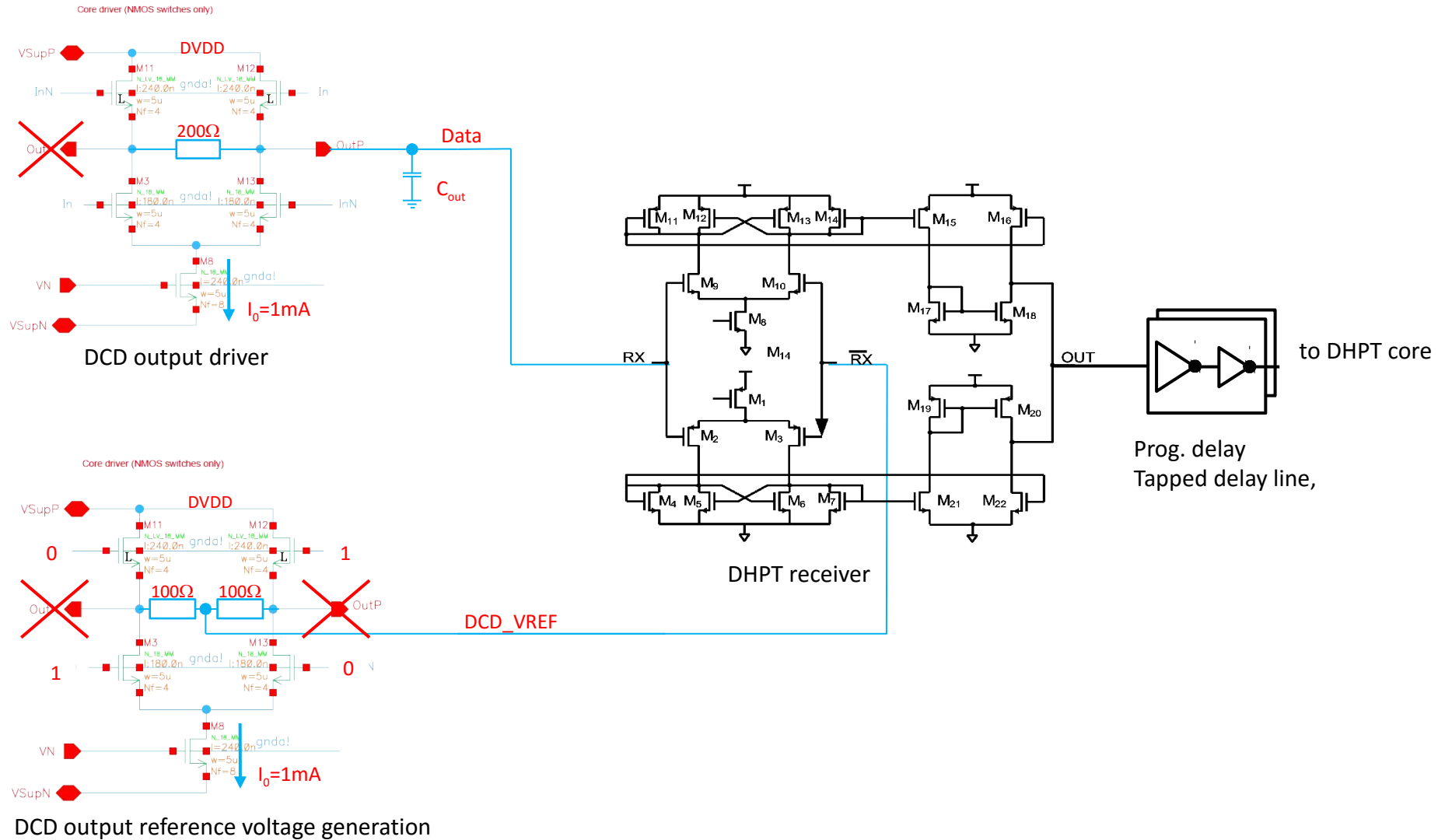
# DCD – DHPT Interface Block Diagram



8 links with 8 data + 2 offsets bits each  
ADC sample rate = 10MHz  
32 ADCs per link → 320 Mbps

GCK  
(80 MHz)

# DCD – DHPT Data Transmission Schematic Details

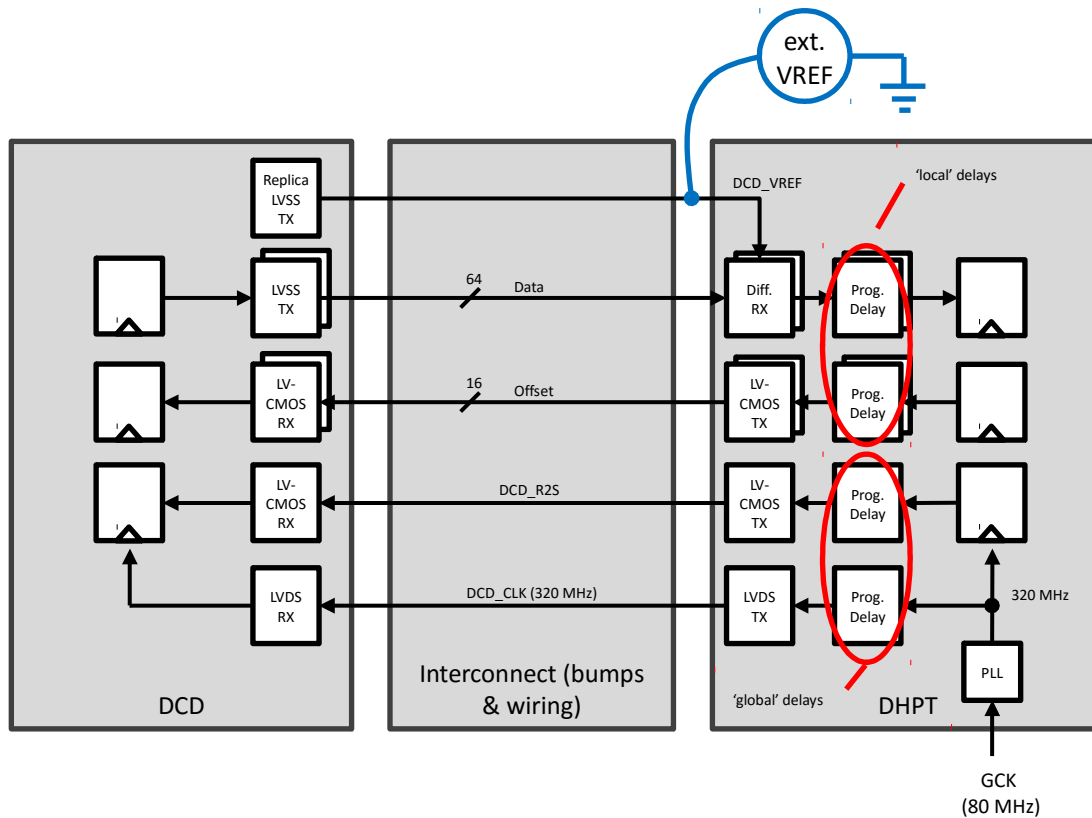




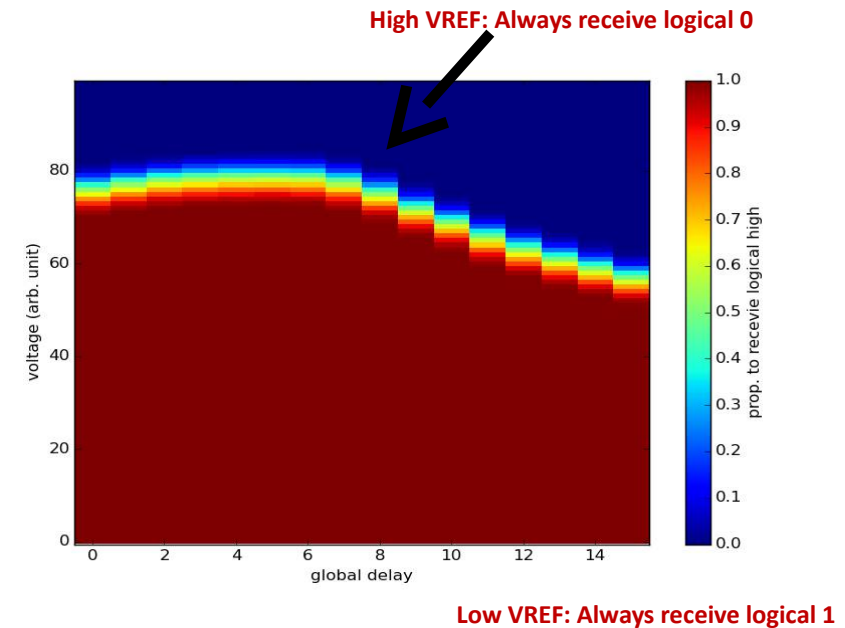


# Data Line Waveform Analysis

- Combined reference voltage- and delay scan (no direct access to data lines)



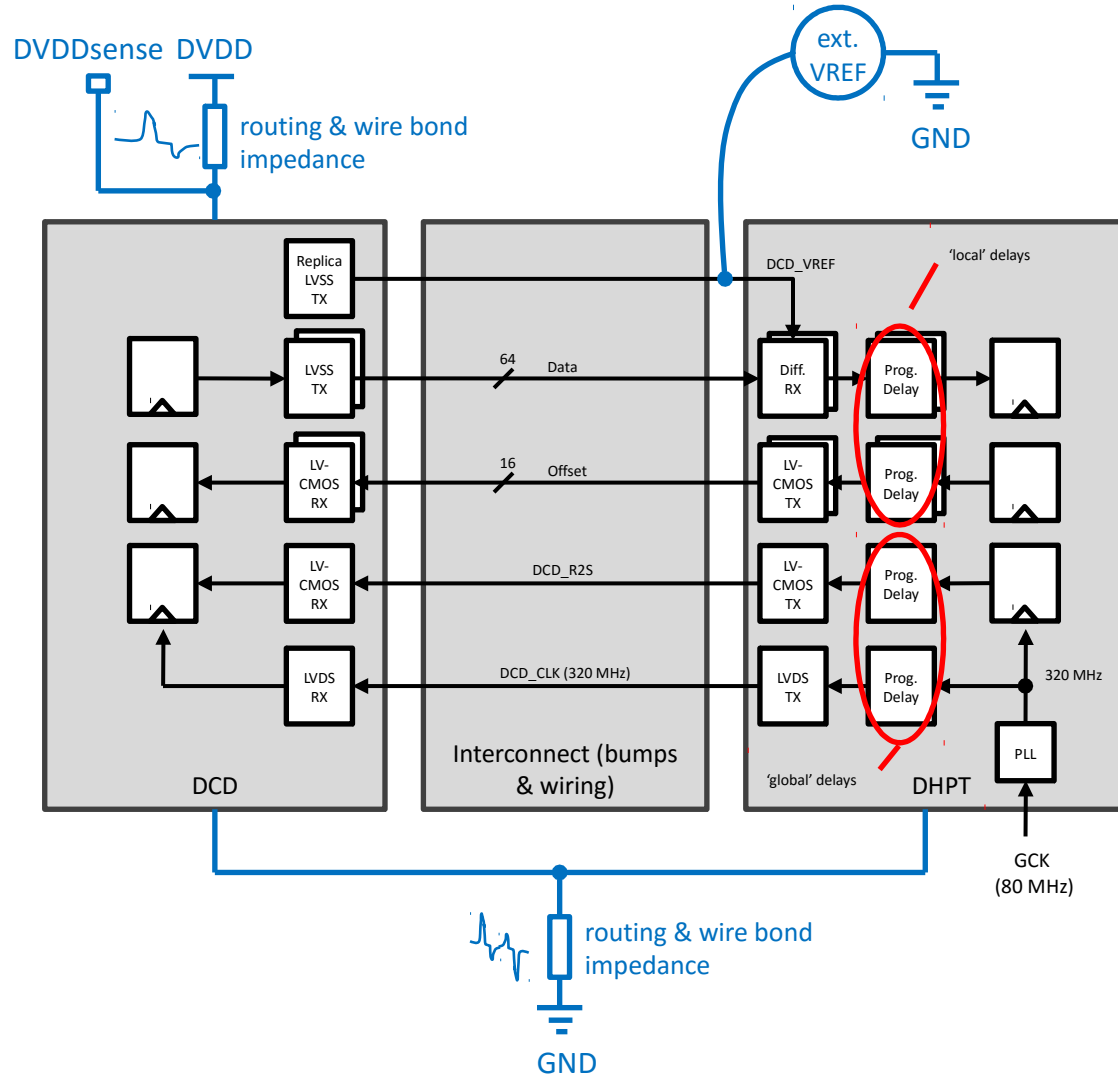
Measurement Setup



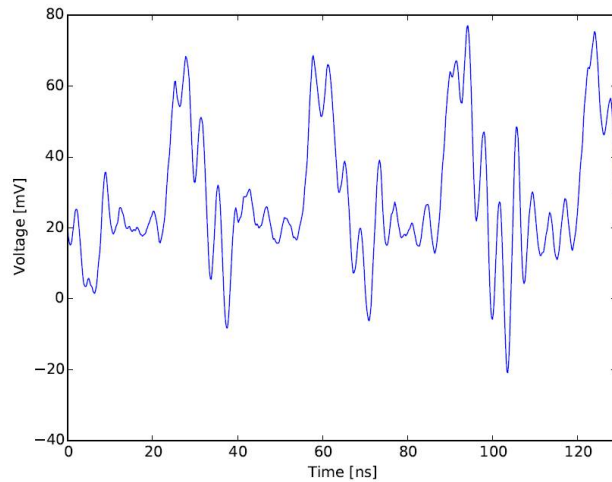
Typical scan result



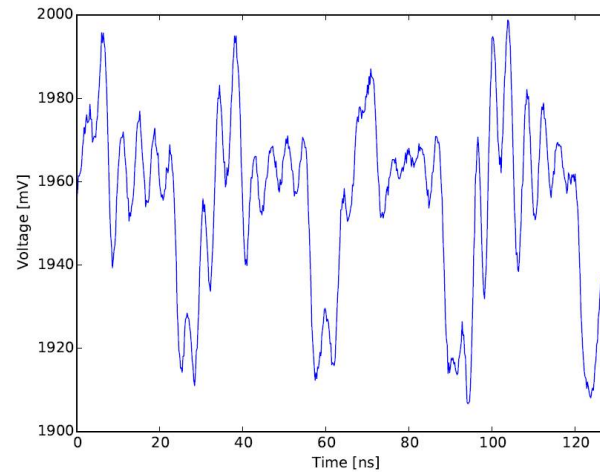
# DCD\_VREF external Control & Measurement



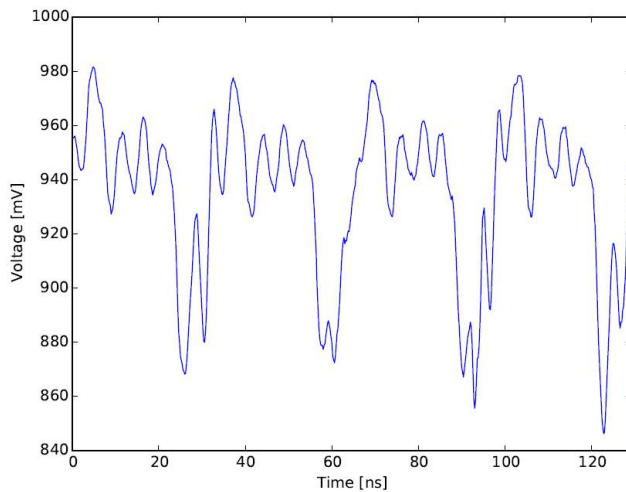
# Measurement Artefacts



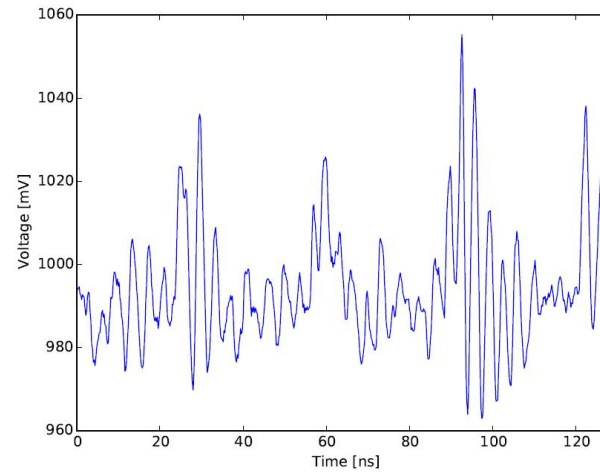
DVDD – DVDDsense



DVDDsense – GND



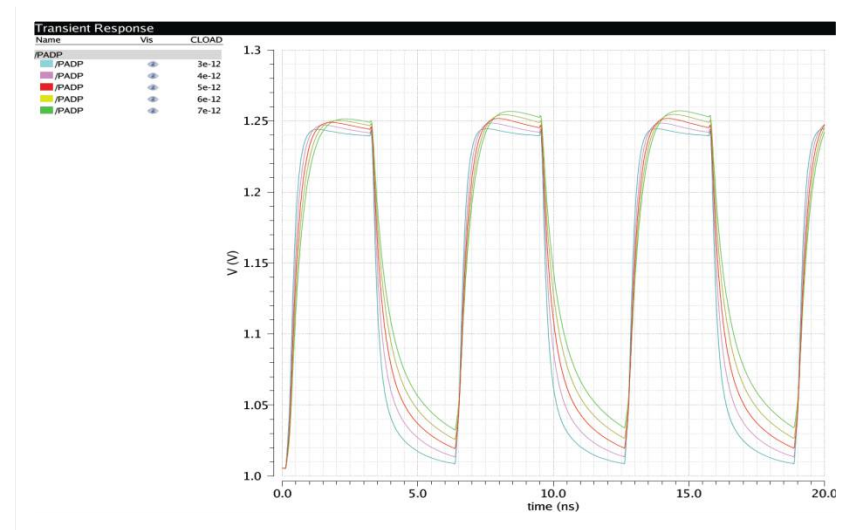
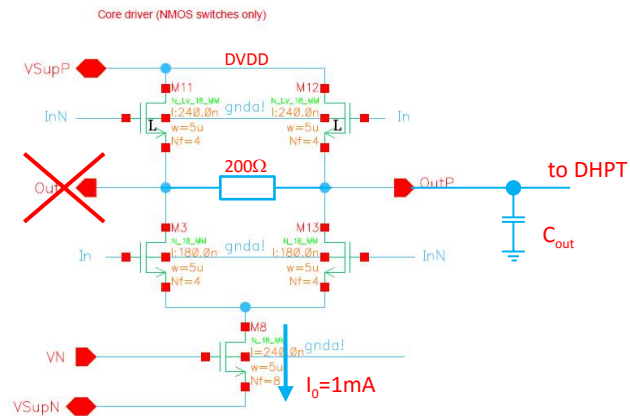
DVDDsense – DCD\_VREF



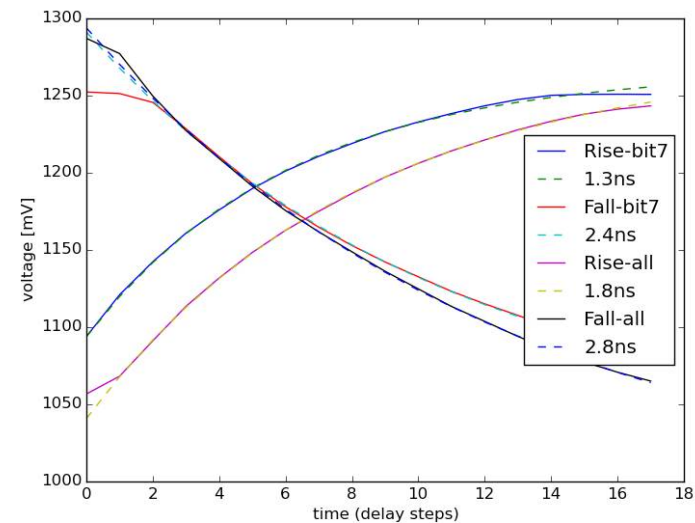
DCD\_VREF – GND

# DCD output driver

- Schematic level simulation
  - capacitive load ( $C_{out}=3..7\text{pF}$ )



- Rise-/fall time extraction from  $V_{ref}/\Delta T$  scans



- Synchronization of data line critical
  - Little contingency for delay settings
  - Sensitive against TID
- Distortion of the duty cycle
  - Delay elements on DHPT
  - Hysteresis of the DHPT differential receiver (plus asymmetric rise and fall times of the DCD driver)
- Slow signals
  - Underestimated parasitic capacitance of wiring and pads
  - DCD driver output levels not adjustable and drive strength asymmetric



- Fix duty cycle distortion
    - Symmetric delay elements on DHPT inputs
    - DHPT differential receiver → remove hysteresis
- } See next chapters
- Make signal faster
    - Reduce parasitic capacitance of the DHPT input pads ( $C_{\text{PAD}} \approx 3 \text{ pF}$  dominated by ESD protection) → analysis/simulation started, pad layout change in progress
    - DCD output driver → Increase drive strength, make programmable (see Ivan's talk)
    - Changes of routing on PXD module ? (estimated  $C_{\text{line}} \approx 1 \text{ pF}$ ) TBD

# Known Issues & Design Changes (DHPT 1.0 -> DHPT 1.1)



Known Issues & Design Changes (DHPT 1.0 -> DHPT 1.1)						
Item #	Block	Description	Critical points, comments	Class/Priority	Implementation Status	Measurements / simulations needed
1	Serializer	Error in load strobe generation logic	check all FF setup & hold timing	bug/high	implemented/done	no
2	CML driver	Increase output amplitude by reducing parasitics, optimize current mirrors and drive strenght	layout parasitic resistance, current source saturation Uds_sat	enhancement/med	implemented/done	no
3	Delay elements	Duty cycle distortion	add dummy loads for intermediate nodes	bug/med	implemented/done	no
4	Data Receiver	Reduce hysteresis in the DCD data differential receivers		enhancement/med	implemented/done	simulate with DCD output stage
4a	Data Receiver	Simulate offset voltage dispersion	Increase input transistor size if offset dispersion would need to be reduced	enhancement/med	implemented/done	MC simulation
4b	Data Receiver	Extract input pad capacitance		no issue yet	implemented/done	QRC extraction
5	Core	Include chip ID in raw data header		low	not considered yet	
6	Core	Gated mode operation	more system tests pending	no issue yet	not considered yet	Hybrid 5 & EMCM system tests
7	Core	High occupancy data processing, common mode processing	more system tests pending	no issue yet	not considered yet	Hybrid 5 & EMCM system tests
8	JTAG	New IDCODE	LSB must be "1"	enhancement/med	pending	
9	Bias	Implement self-bias parallel to DAC bias	check default bias setting	enhancement/med	pending	
10	General	extrapolate SEU x-section for thermal neutrons			done	literature search

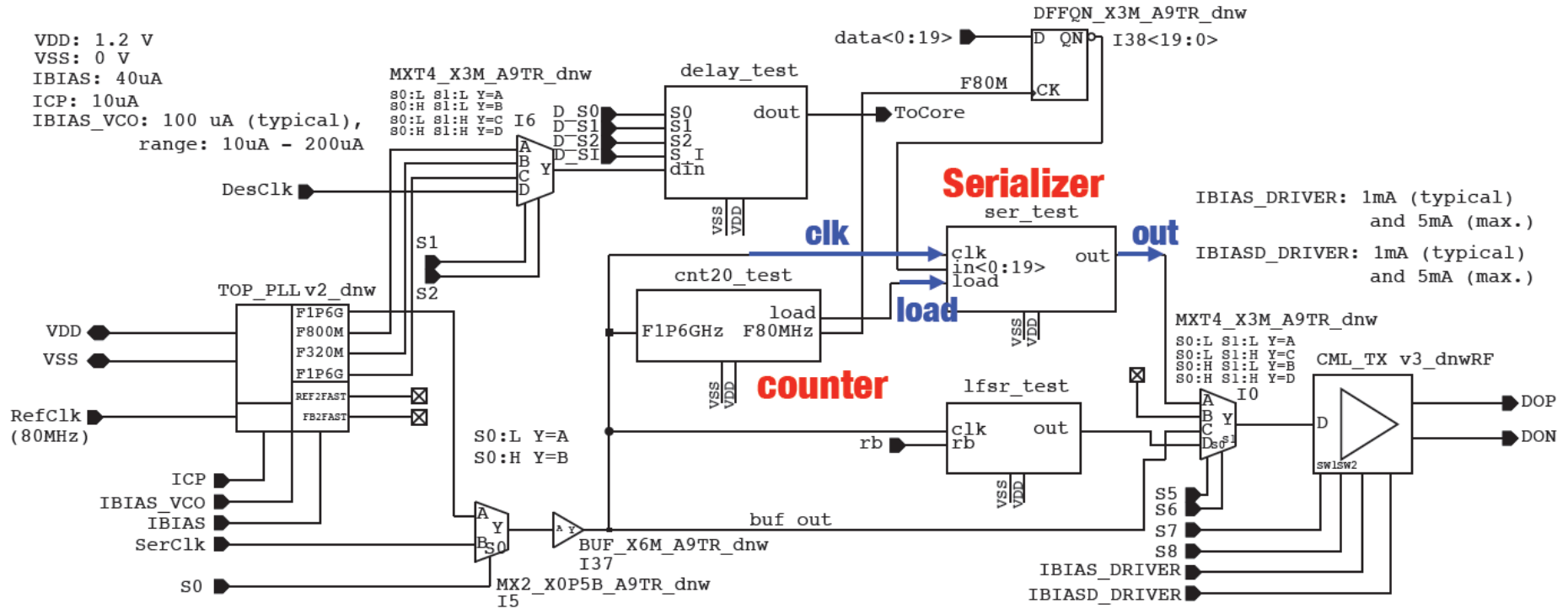
Status: 7.7.2015



DHPT 1.0

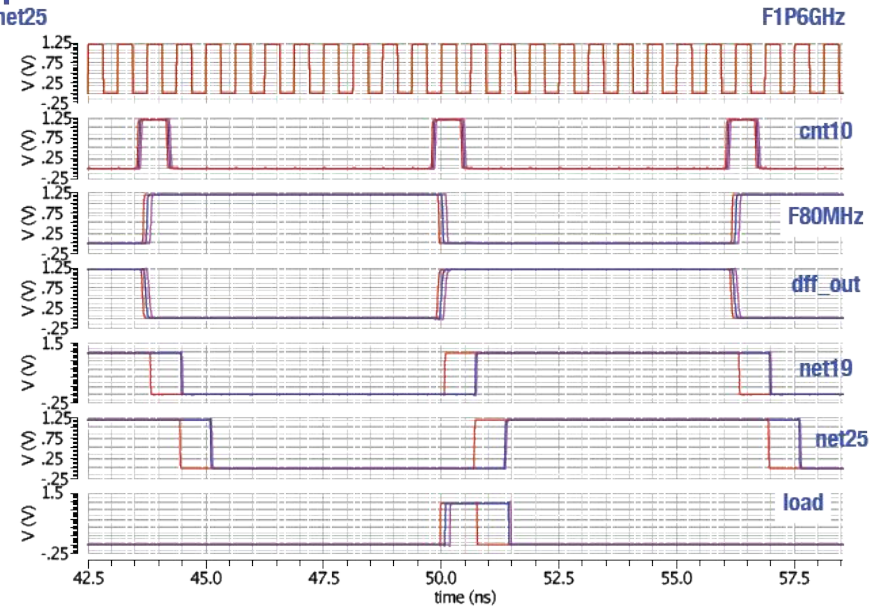
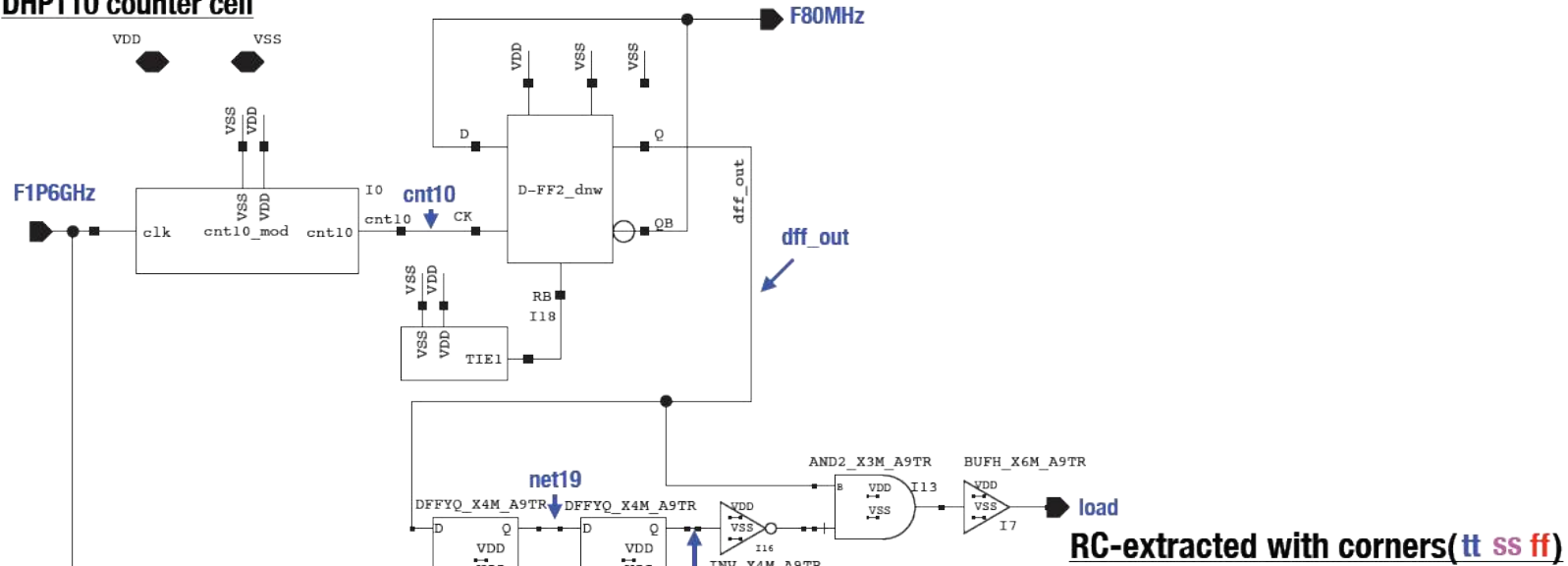
# **SERIALIZER**

# PLL + SER Block Diagram



# Load Strobe Generation (Counter)

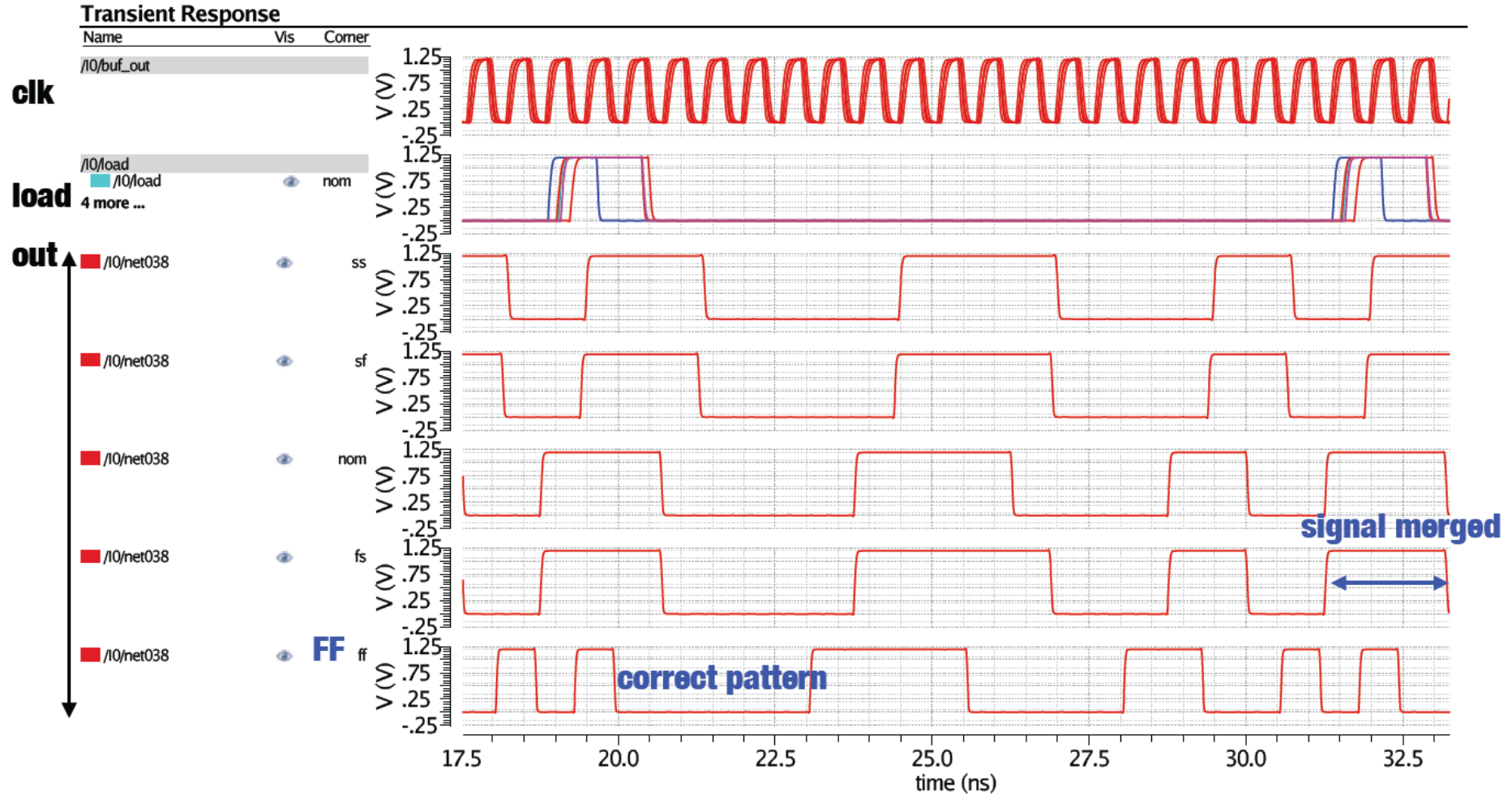
## DHPT10 counter cell



- Mistake made during extracting and simulating the layout with all process corners
- Serializer works, but VCC and/or GCK have to be adjusted:
  - GCK= 80 MHz → VCC = 1.6V (works but should not be applied for a long time)
  - GCK= 60 MHz → VCC = 1.4V (ok)
- Manufacturer test data → wafer batch has „slow NMOS“ (too high threshold)

PARAMETER	BY LOT:	SPEC LO	SPEC HI	MIN	MAX	MEAN	STD DEV
VT1_N4	(N/.3/.06/1)	0.300	0.490	0.368	0.490	0.423	0.029
Isof_N4	(N/.3/.06/1)	-1.400E-07	0.000	-8.958E-10	-3.833E-11	-2.339E-10	2.063E-10
Isat_N4	(N/.3/.06/1)	0.491	0.735	0.547	0.673	0.593	0.031

# DHPT 1.0 Serializer Simulation

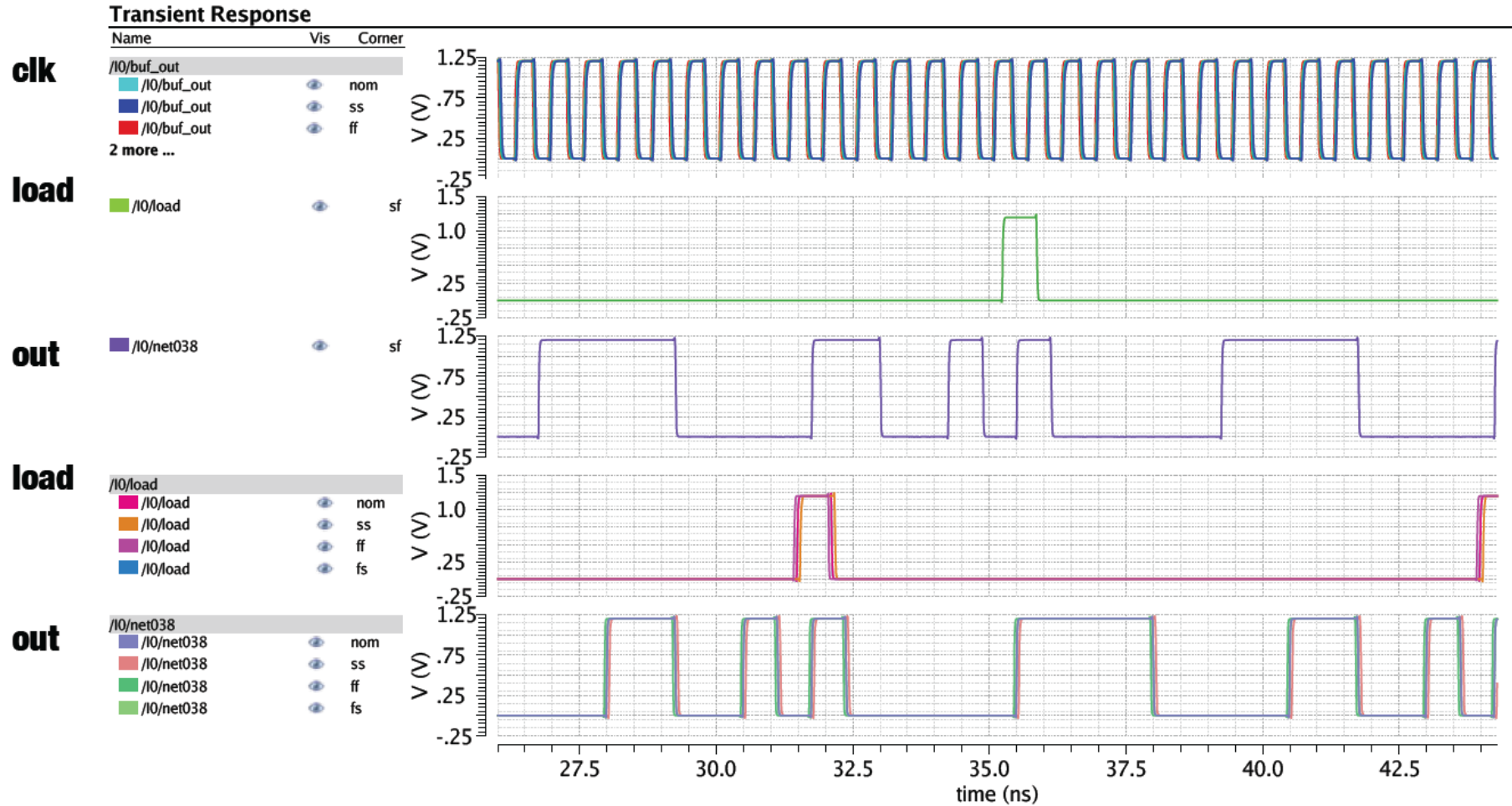


**Timing of "load" is not provided correctly, except fast-fast corner.**





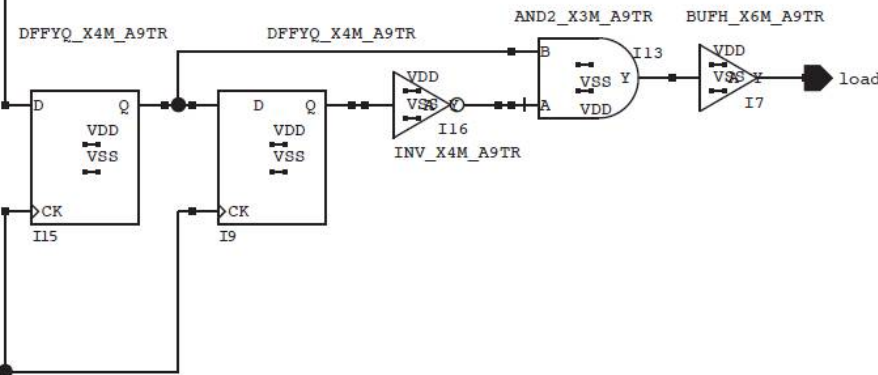
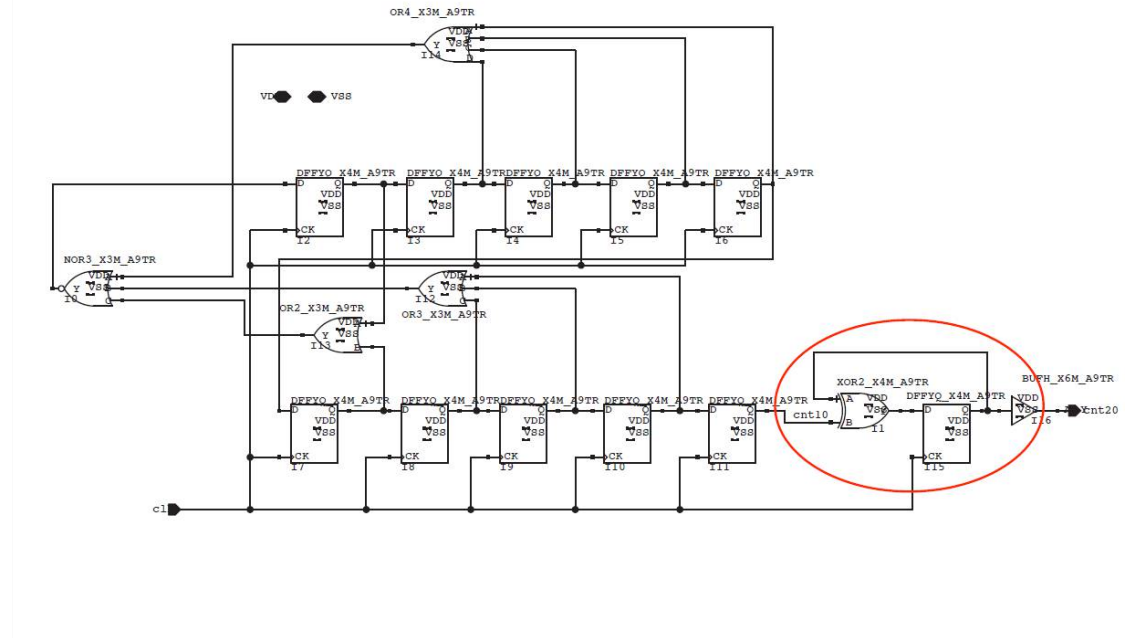
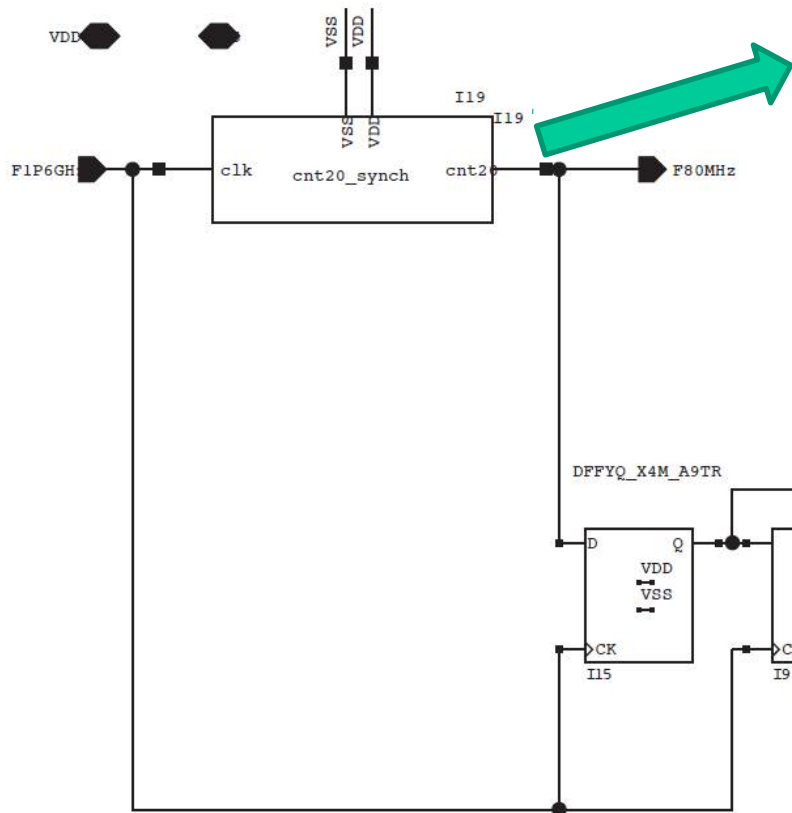
# Serializer Simulation with Modification (DHPT 1.1)



**Correct pattern can be obtained with all corners.**

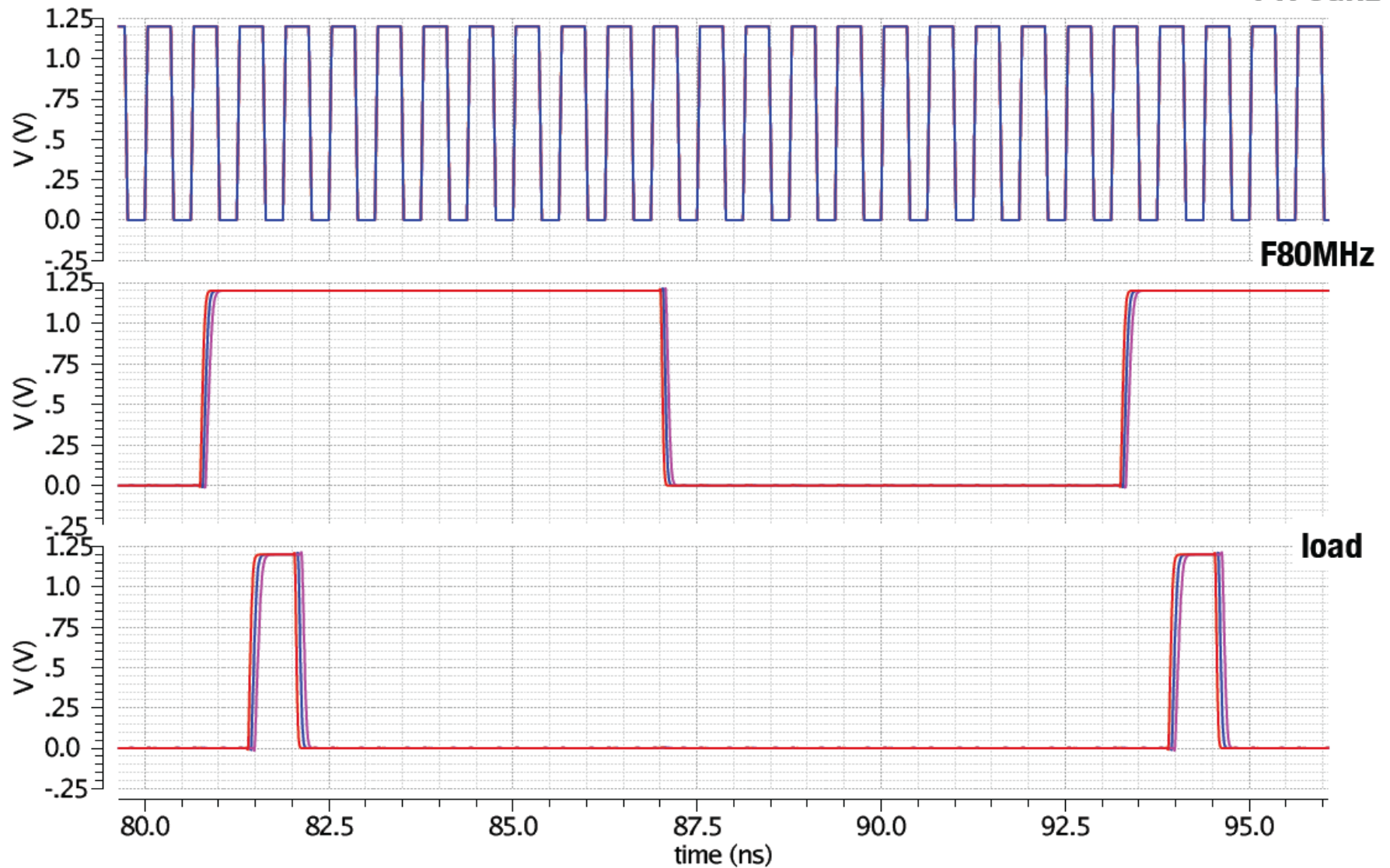
# New Serializer Load Strobe Generator

- Synchronous design



# RC-extracted simulation with corners( **tt** **ss** **ff** )

F1P6GHz



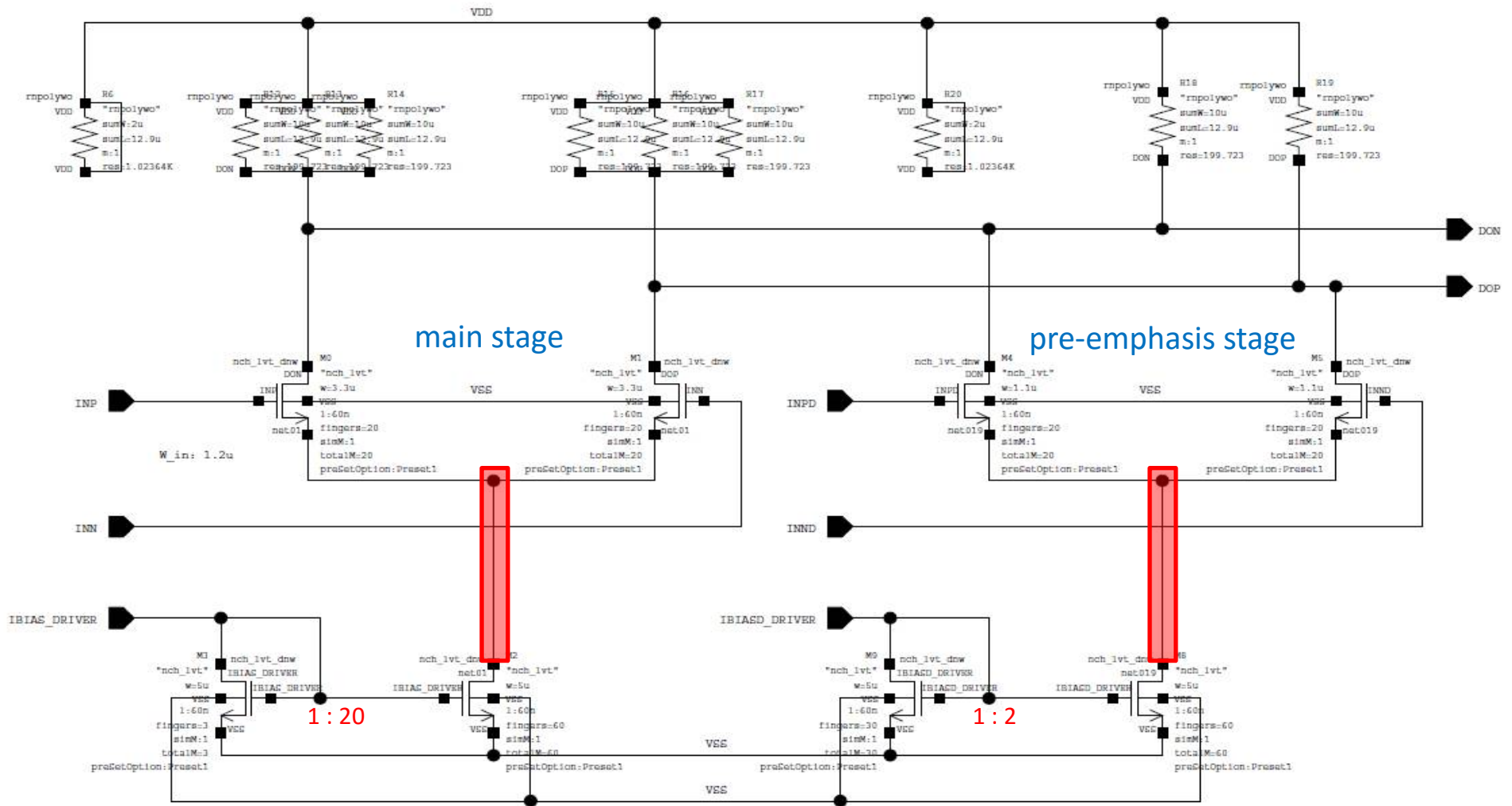
DHPT 1.0

# **CML DRIVER**

DHPT 1.0

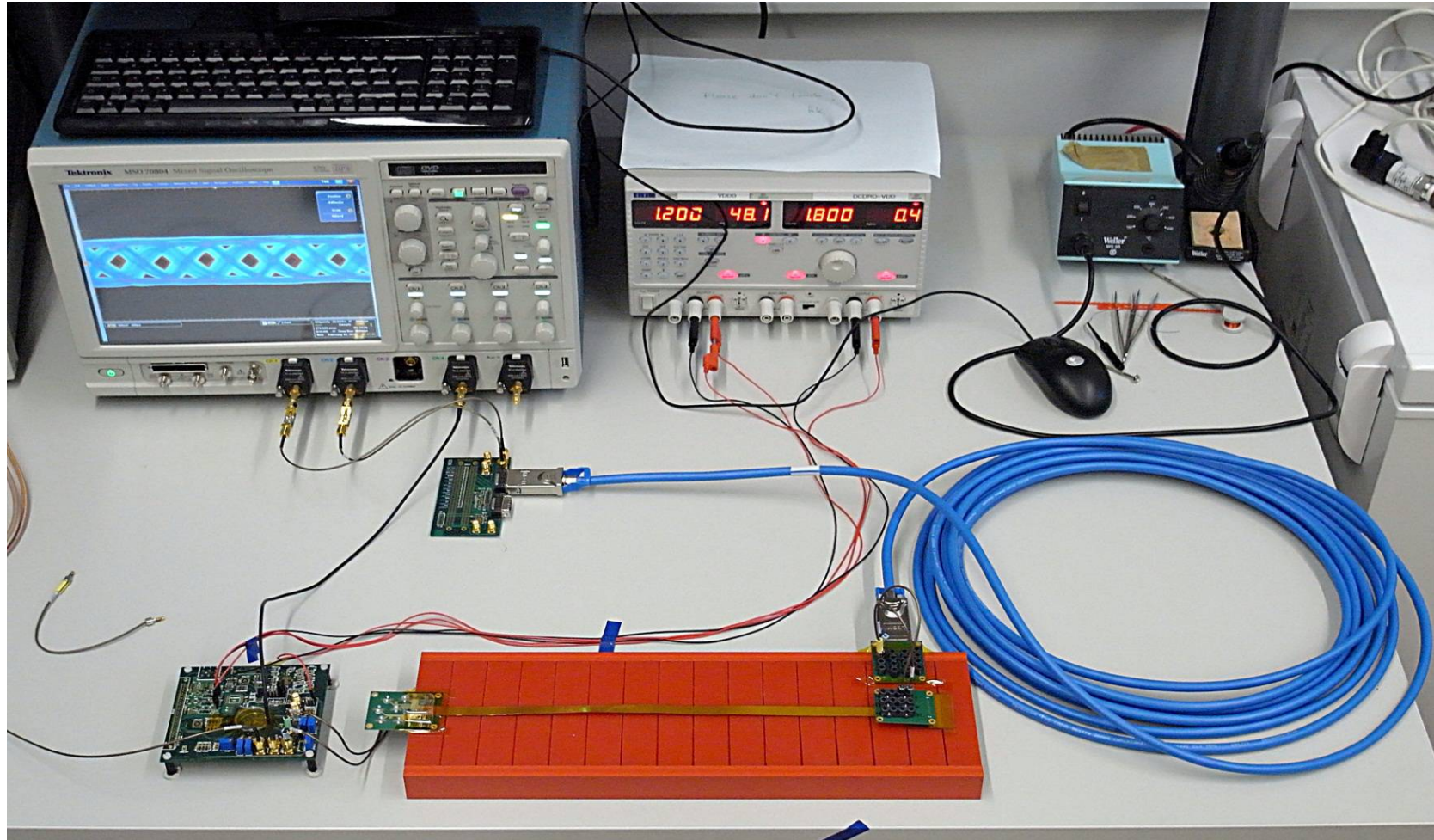
# **CML DRIVER**

# Driver Schematic



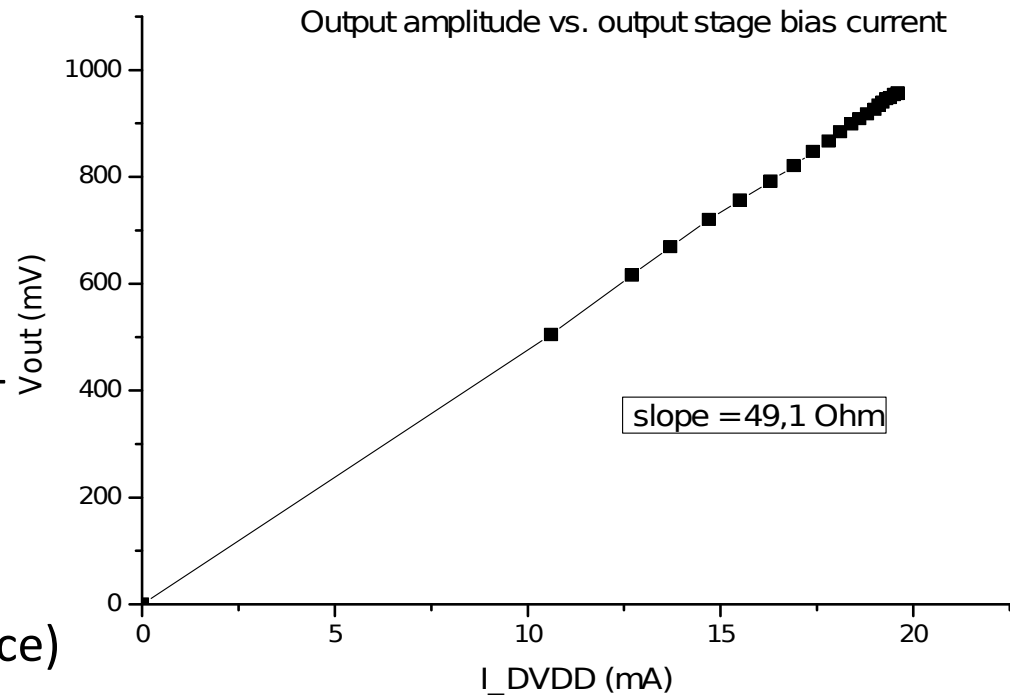


# DHPT 0.1 – Test setup



# Differential Output Amplitude

- Linear function of bias current (IBIAS\_DRIVER)
- IBIAS\_DRIVER  $\approx$  I\_DVDD
- Preemphasis off (IBIASD\_Driver = 0)
- Effective output resistance: 49.1 Ohm
- DC output resistance: 55 Ohm
- ➔ ~3.5 Ohm Series resistance (chip wiring, bond wire, PCB trace)

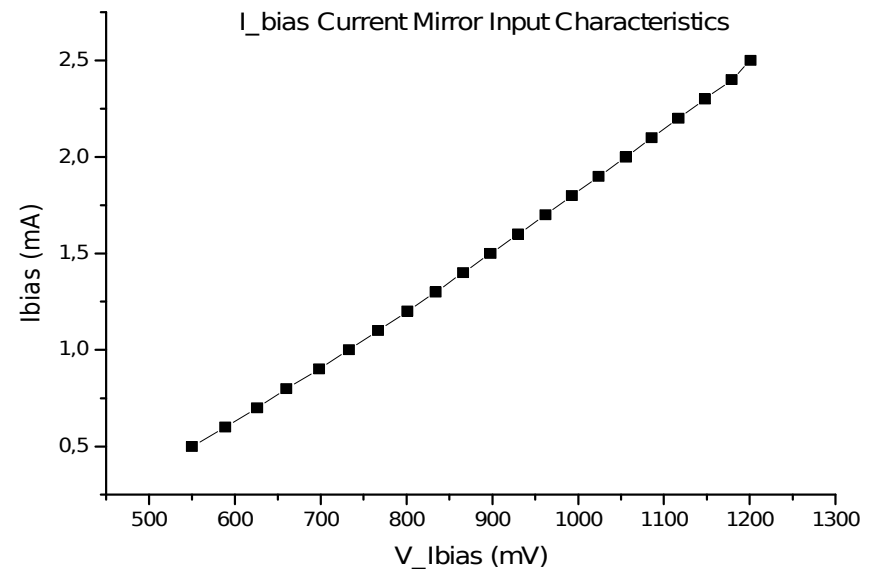
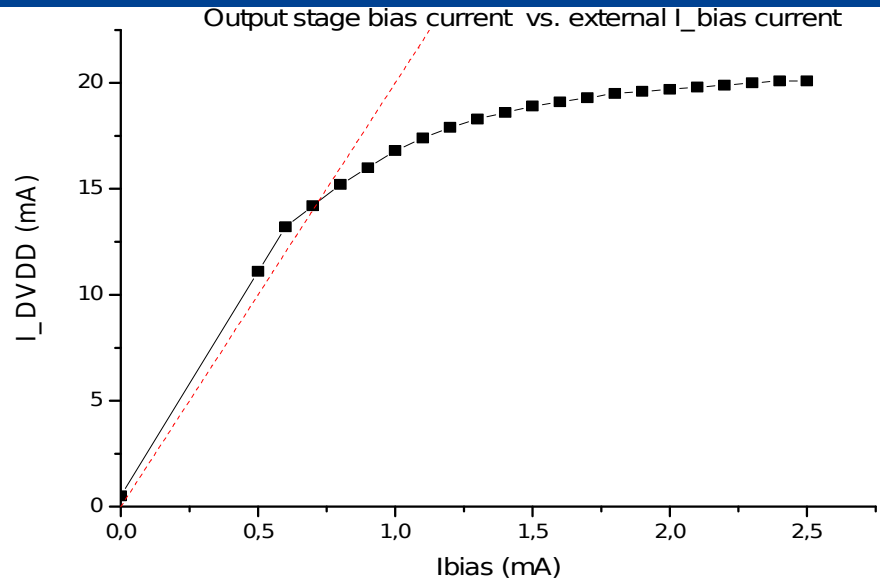


➔ Output resistance Ok

# Main Output Current Mirror

- IBIAS\_DRIVER current mirror
- Design value  
 $IBIAS\_DRIVER/I_{bias} = 20$
- Non-linear for  $I_{bias} > 0.7\text{mA}$   
→ M2 not saturated?
- Drive current limited to 20 mA  
→  $V_{out\_max} = 957\text{ mV}$

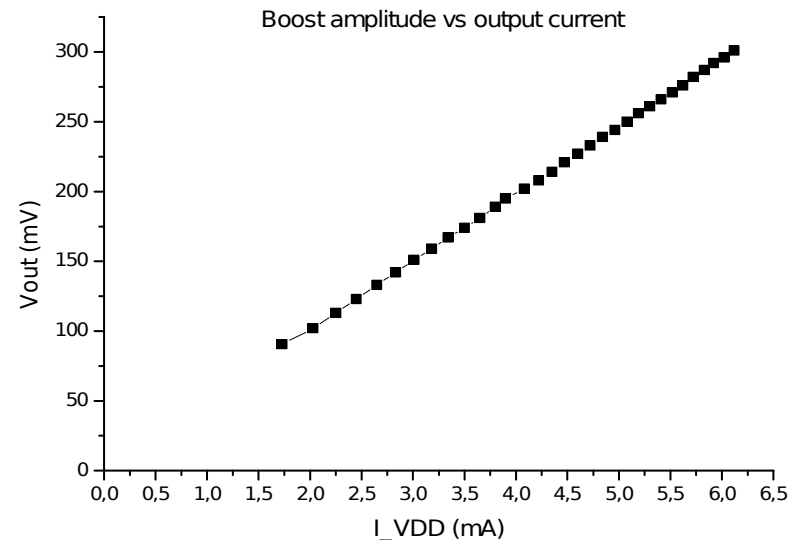
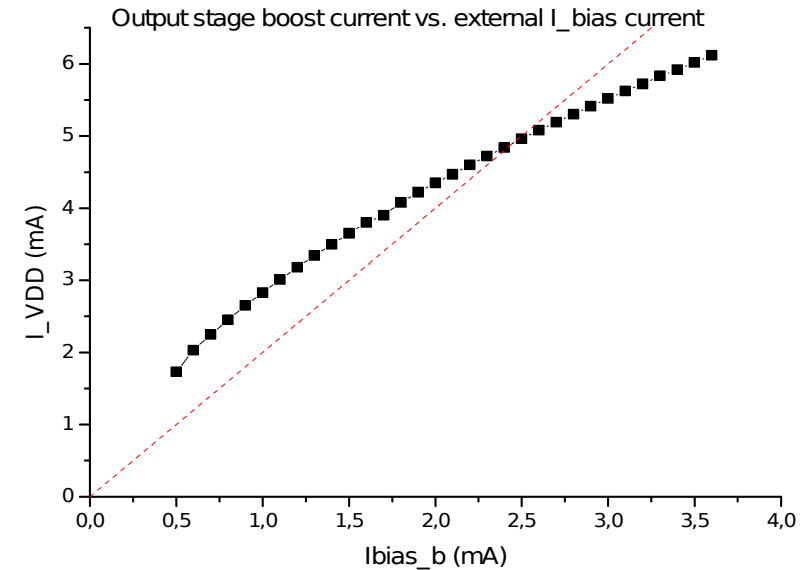
→ Limited by current sink (M2) or switches M0/M1 (too high on resistance or parasitic wiring resistance)



# Boost Output Current Mirror

- IBIASD\_DRIVER current mirror
- Design value  
 $I_{BIASD\_DRIVER}/I_{biasd} = 2$
- Fair linearity
- Drive current limited to 6.12 mA  
→  $V_{boost\_max} \sim 300mV$

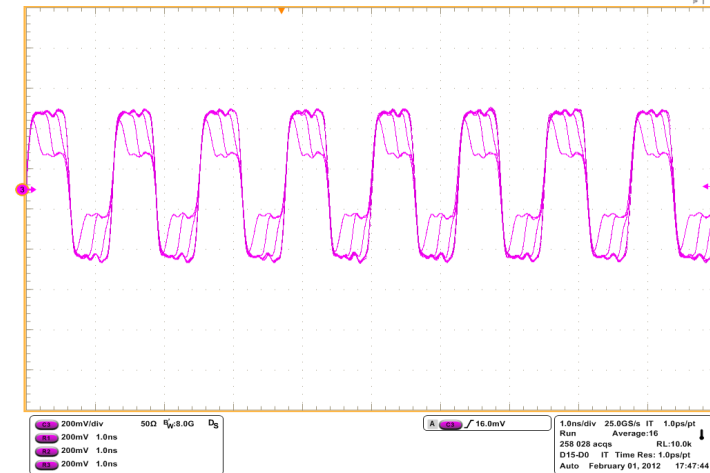
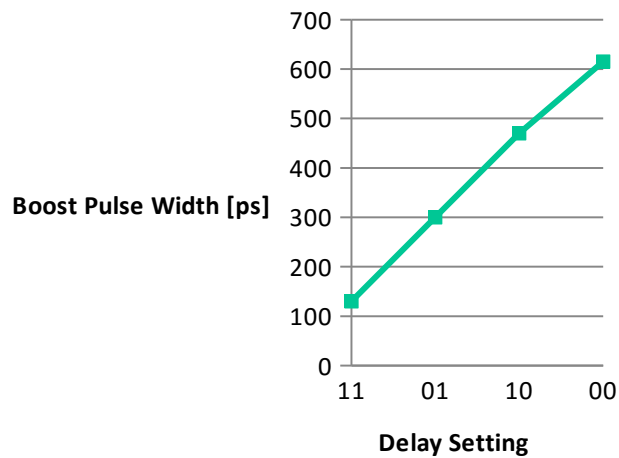
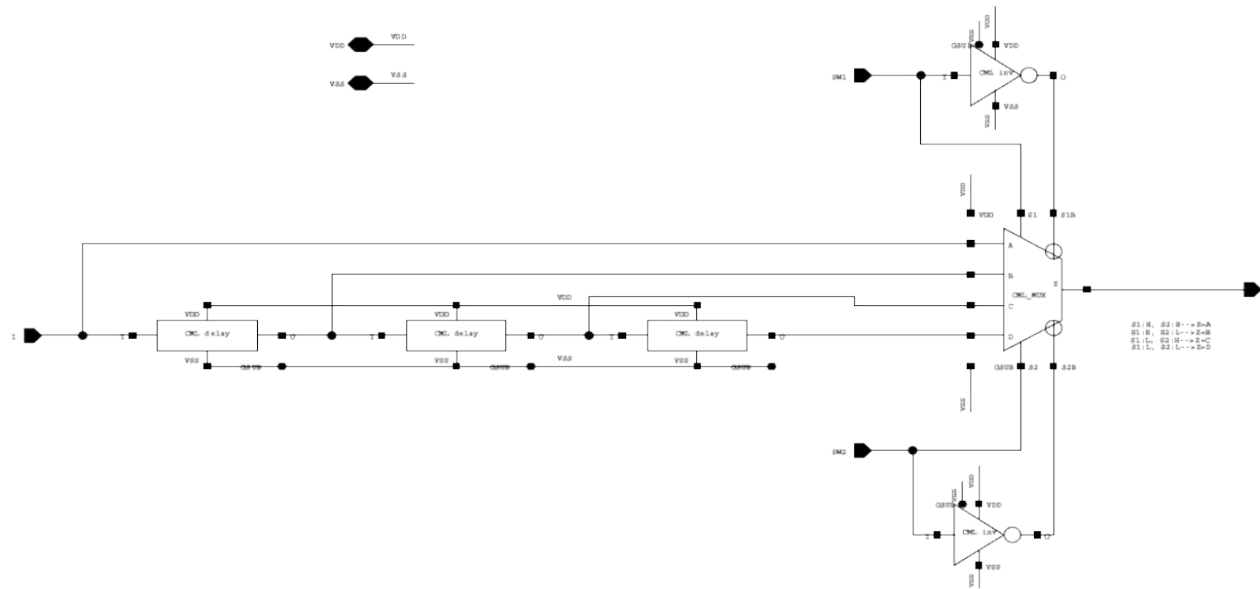
→ Enhancement:  
Make boost current sink M8 stronger



# Delay Settings

Setting SW[1:0]	Pulse Width [ps]
11	130
01	300
10	470
00	615

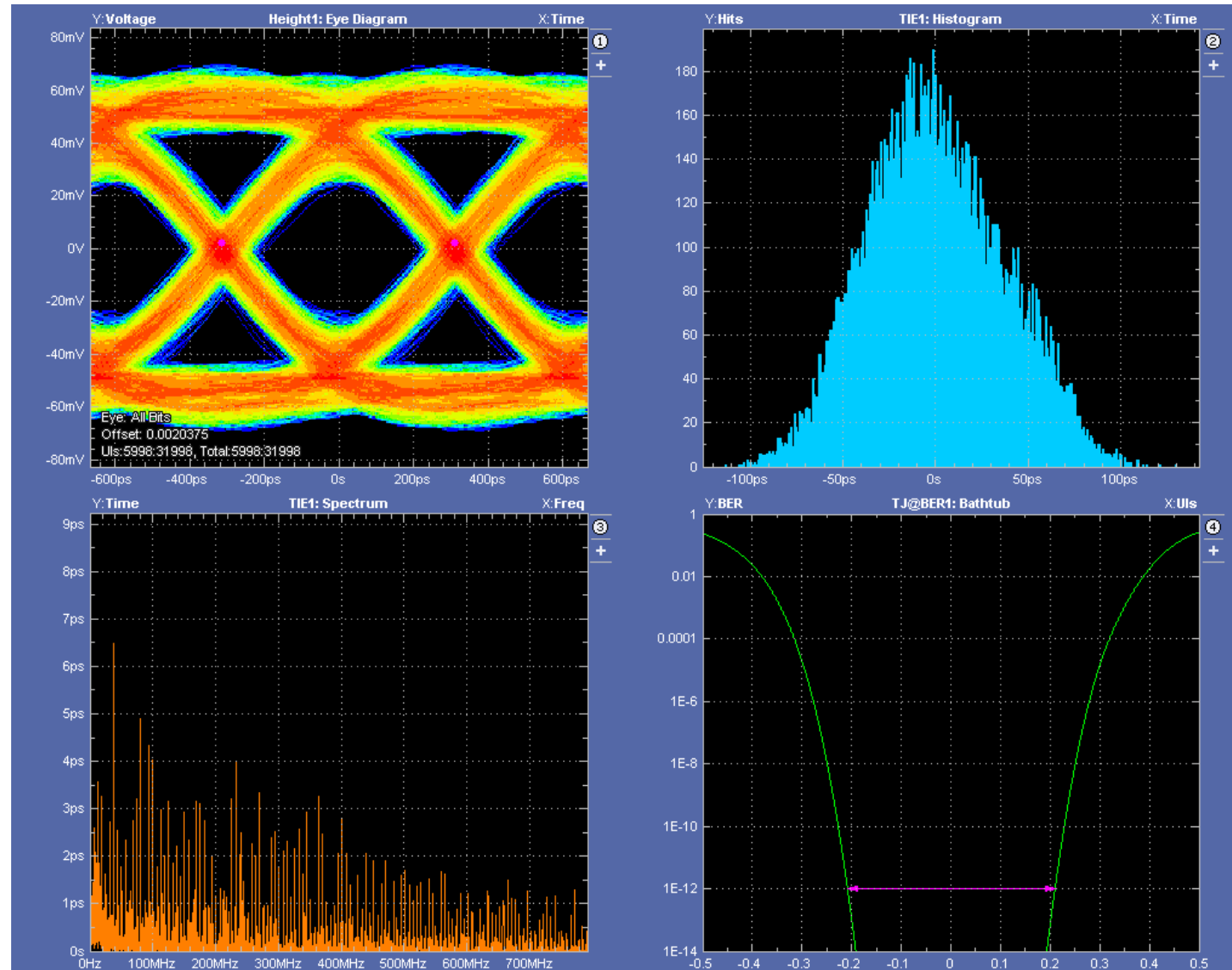
→ ~170 ps per delay buffer



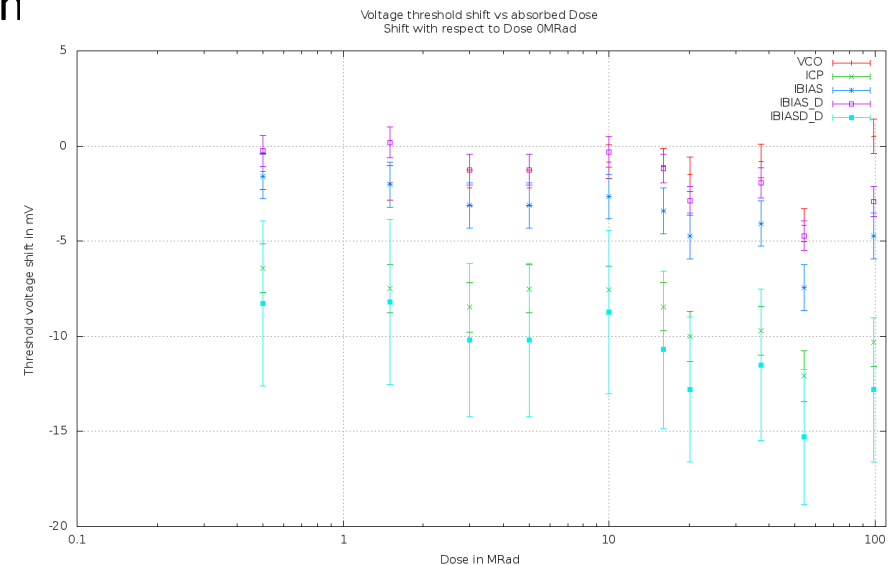
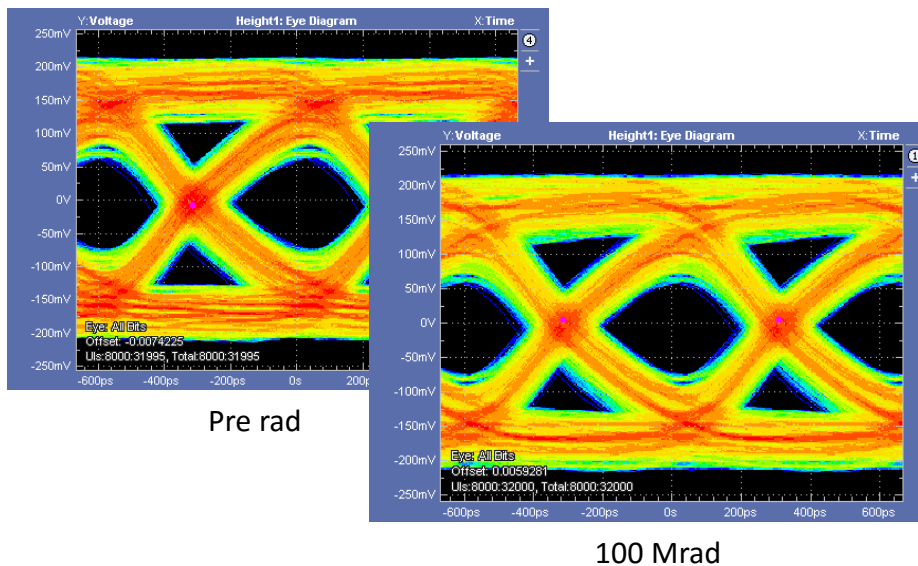
800 MHz clock, different delay settings

# Signal Integrity Characterization

- 1.6 Gbps LFSR-8
- 30 cm kapton cable + 20m AWG26 twisted pair cable



- TSMC 65nm TID tolerance:
  - $V_{THR}$  shift (wide pMOS and nMOS only)
  - PLL + Gbit link performance
- Up to 100 Mrad (60keV X-ray tube, Karlsruhe)
- Dose rates:  $\sim 300$  kRad/h (initial)  $\rightarrow \sim 2$ Mrad/h (end)
- Annealing after each step:  $80^{\circ}\text{C}$  for 100 min

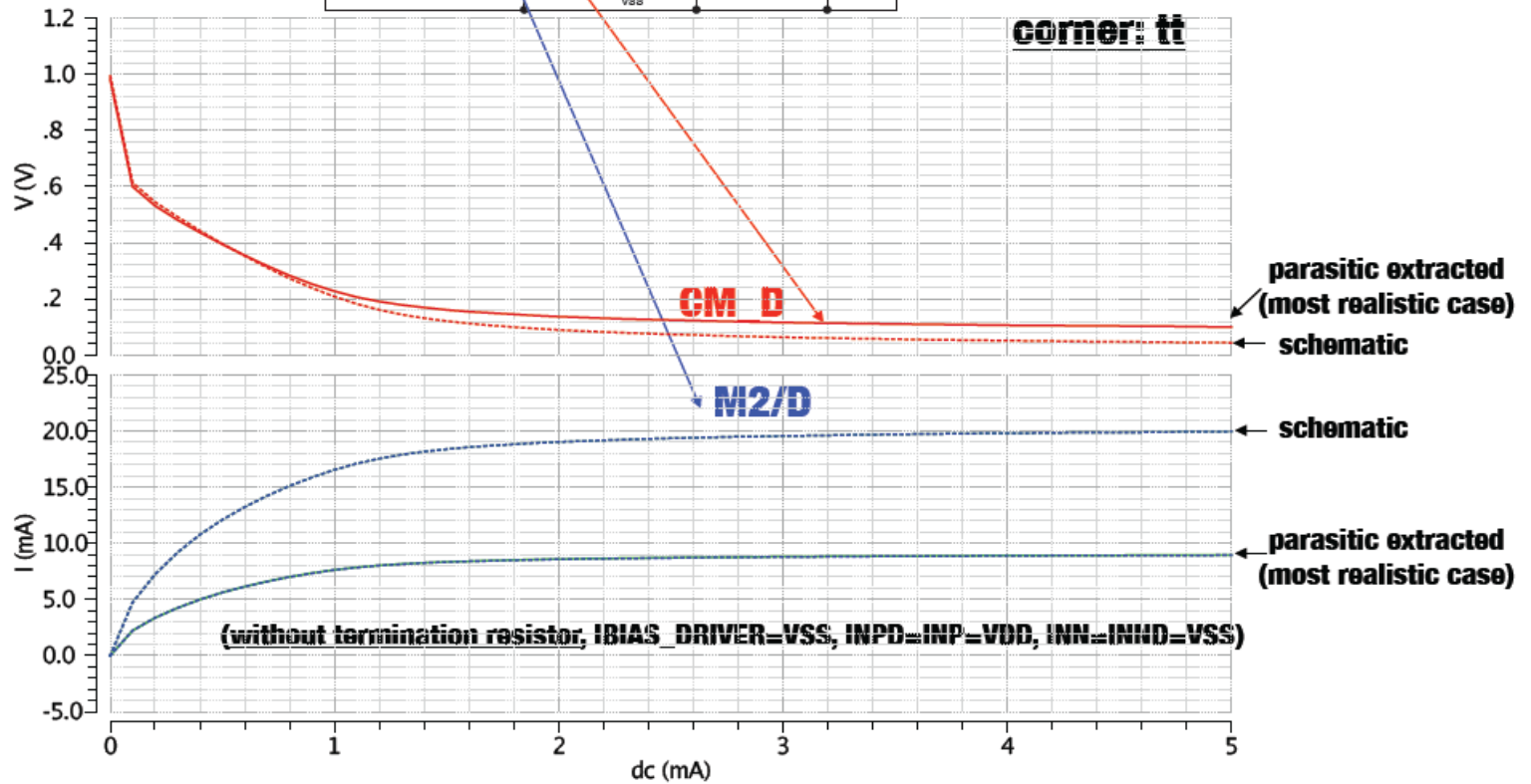
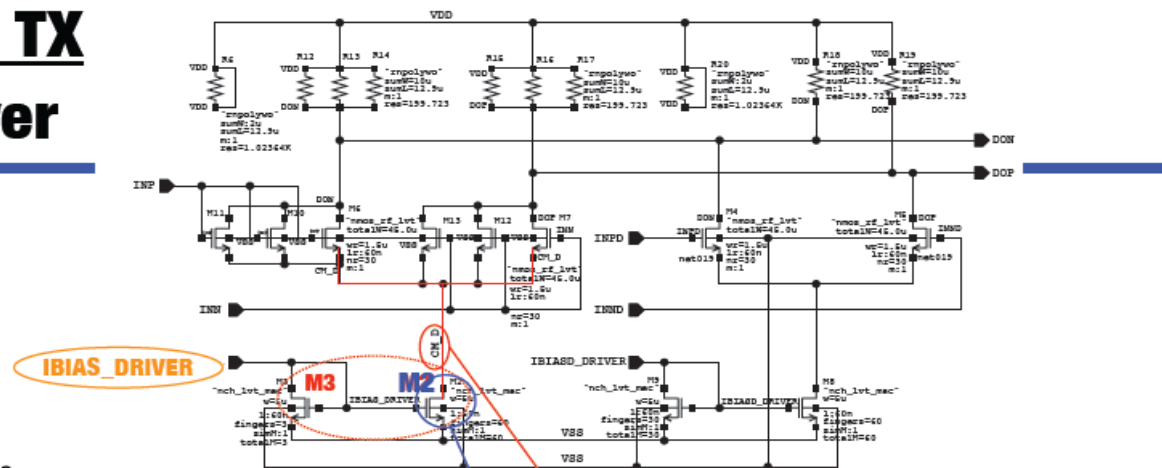


No TID induced degradation observed up to 100 Mrad



# DHPT10 CML TX

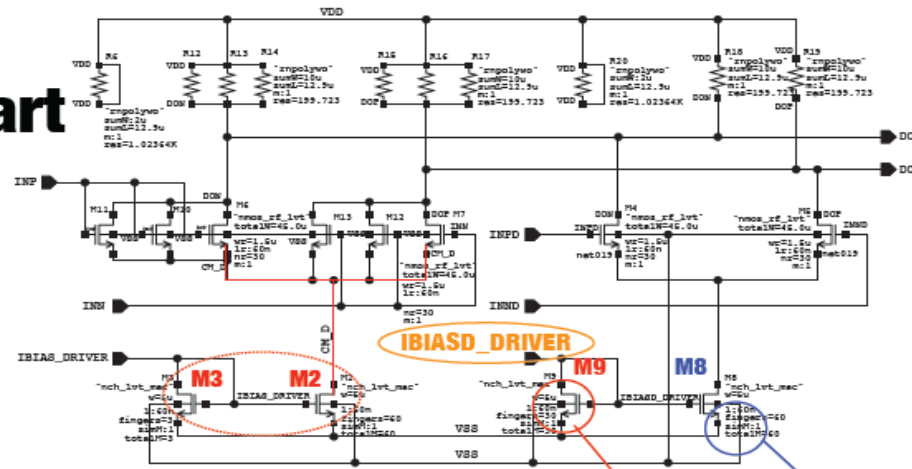
## Main driver



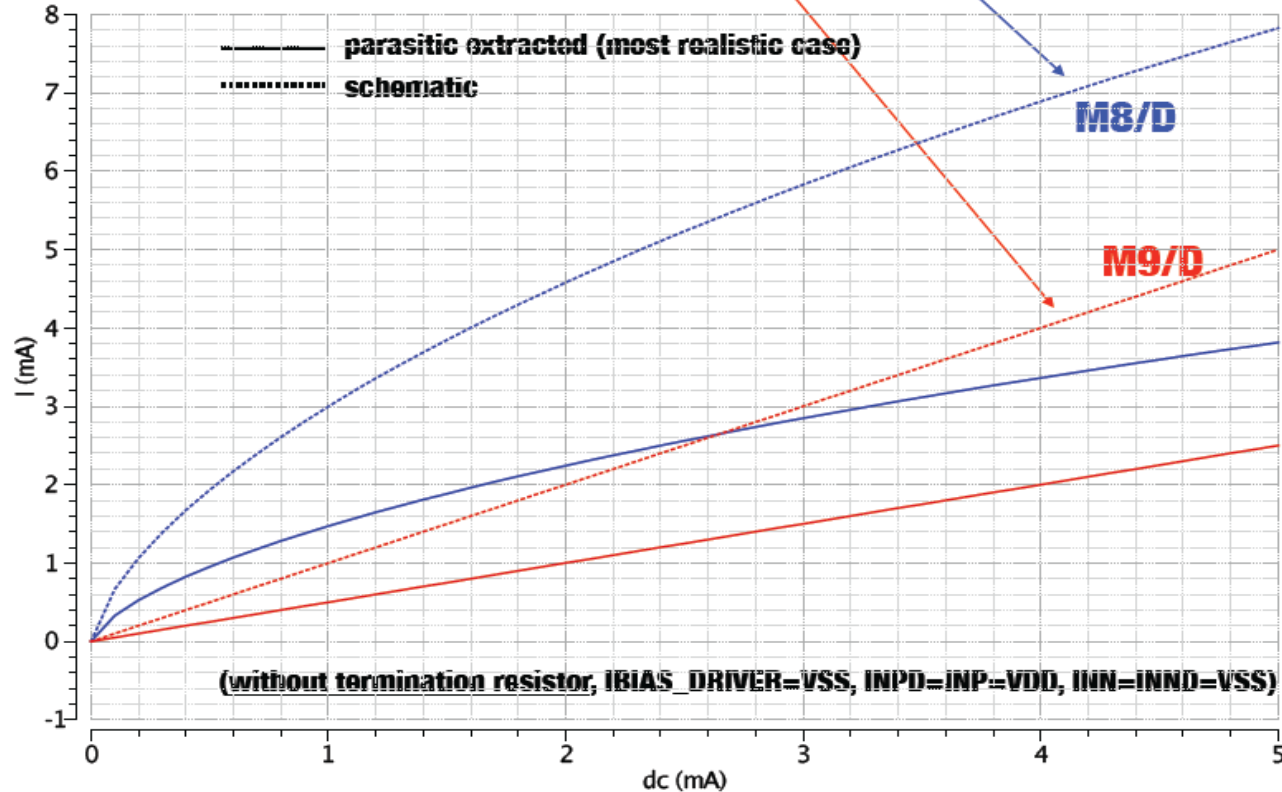
IBIAS\_DRIVER (mA) (←supplied externally, not from DAC)

# DHPT10 CML TX

## Pre-emphasis part



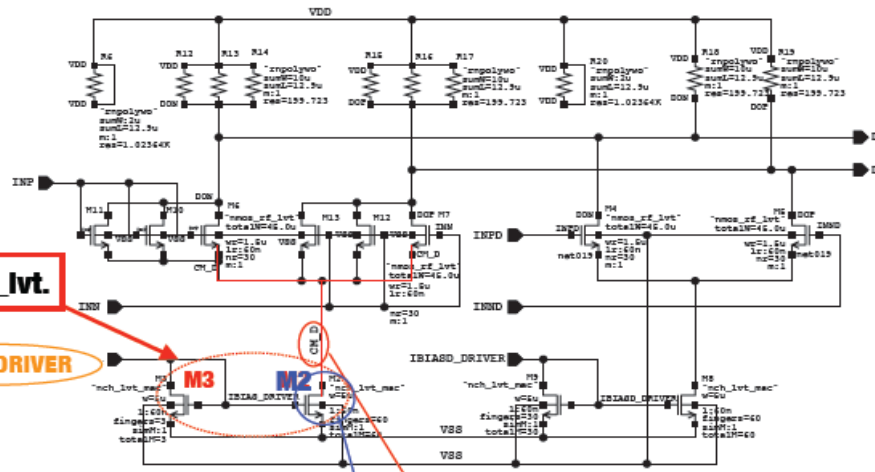
**corner: tt**



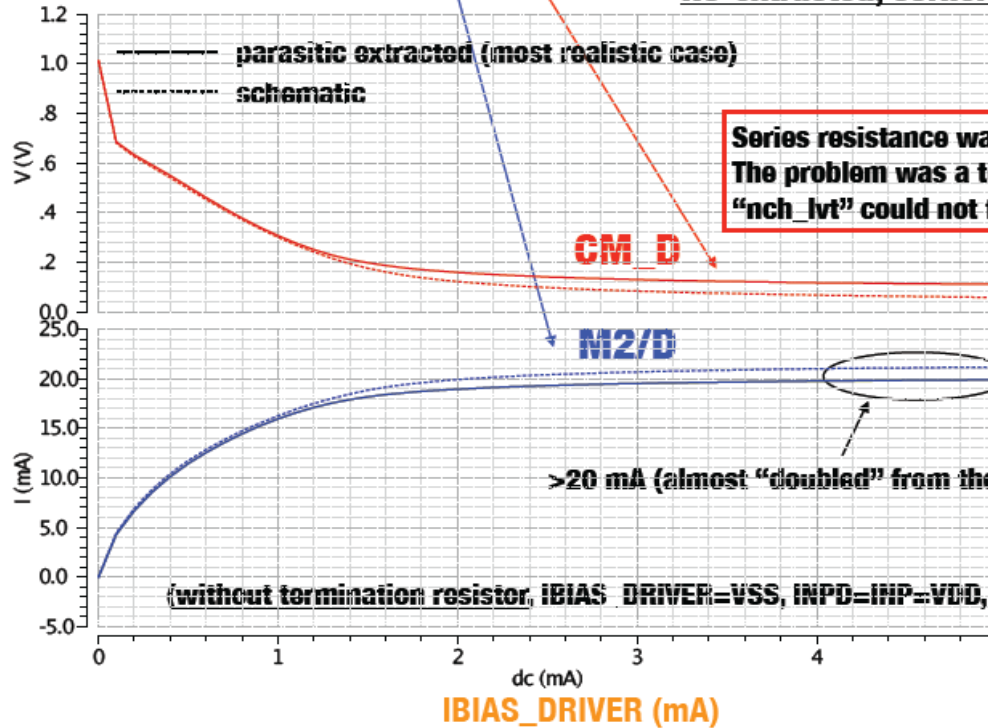
# Improved Design Main driver

replaced from "noh\_lvt" to nmos\_rf\_lvt.

IBIAS\_DRIVER



RC-extracted, corner: tt

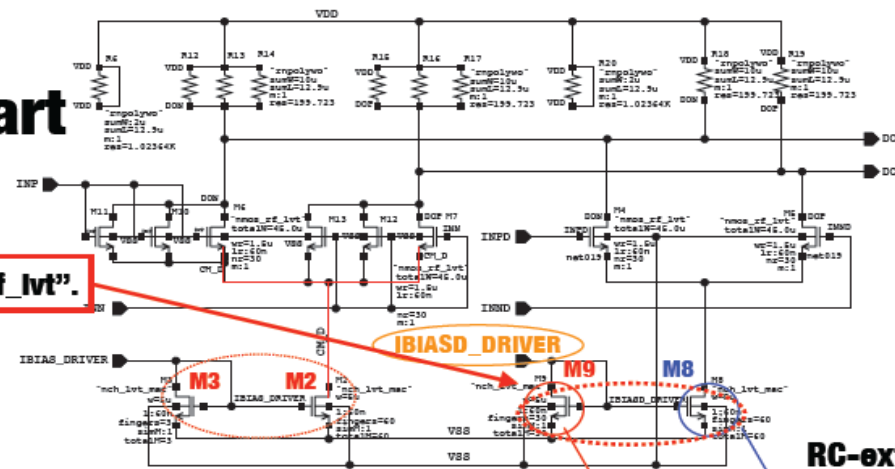


Series resistance was not a major problem.  
The problem was a transistor type of the current mirror.  
"noh\_lvt" could not flow much current.

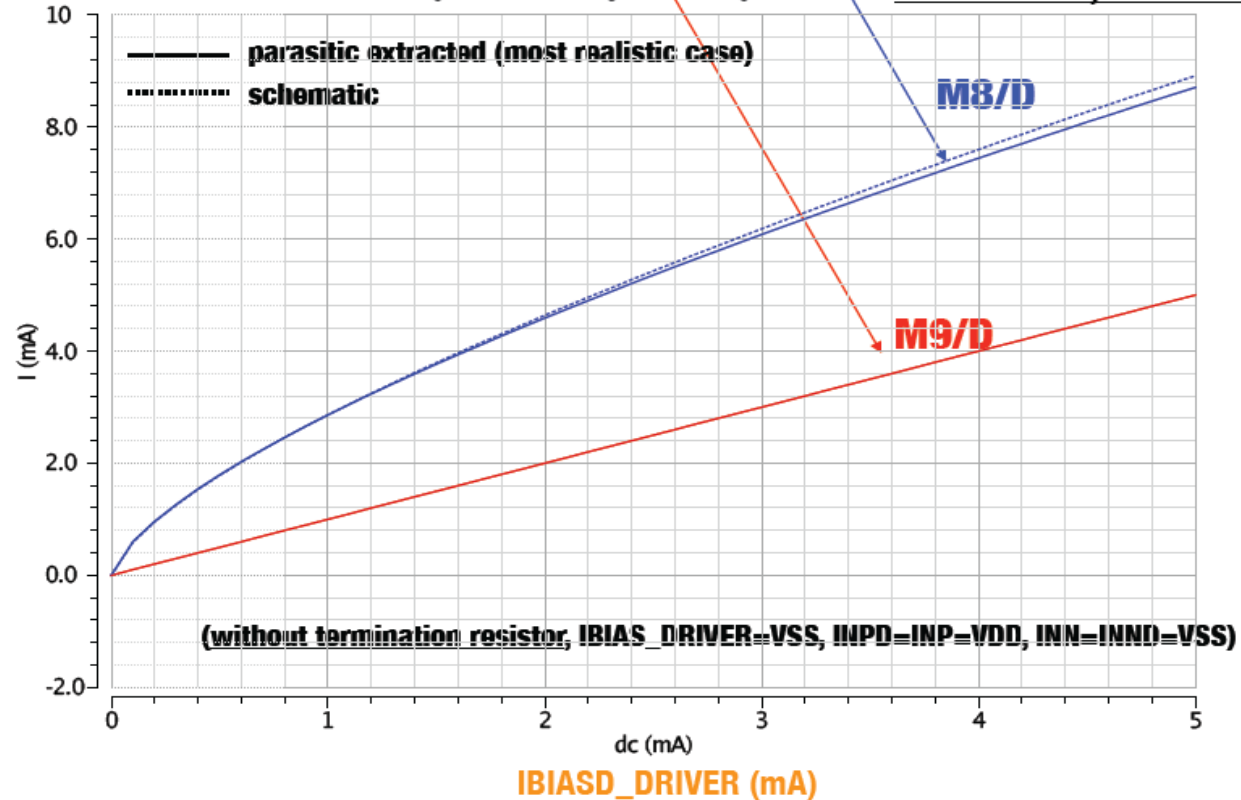
# Improved Design

## Pre-emphasis part

replaced from "nch\_lvt" to "nmos\_rf\_lvt".



RC-extracted, corner: tt

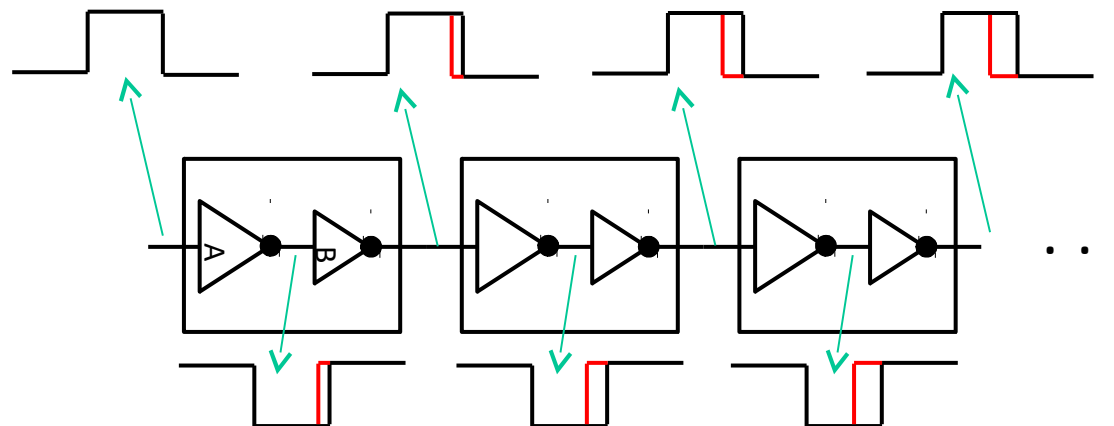


DHPT 1.0

# **DELAY ELEMENTS**

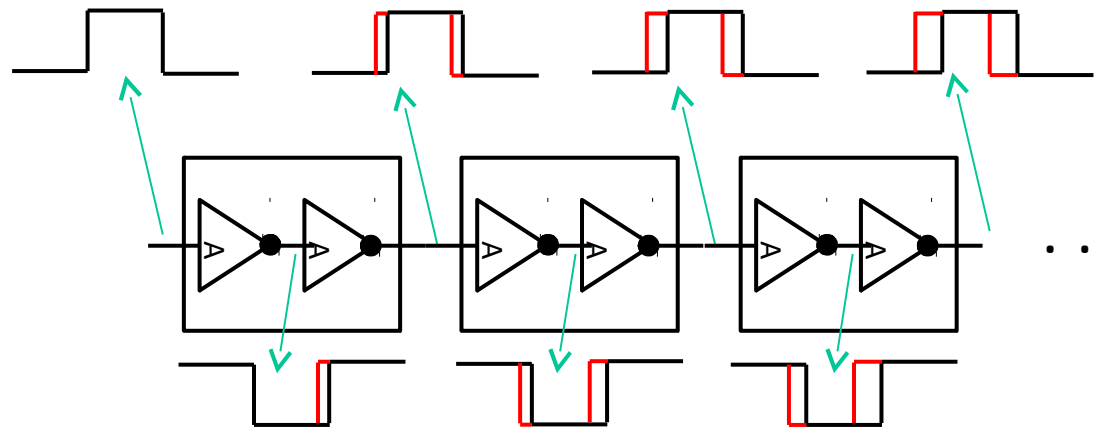
- Programmable delay lines made from std. cell delay elements (dual inverters)
- Inverter have usually unequal propagation delays for rising and falling edges (Asymmetry of PMOS-NMOS drive strength, process corners, W/L...)
- The **std. cell delay** elements consist of **alternating no-equal sized inverters**

→ The difference in  $t_{pd}$  for rising and falling edges for inverter A and B is different!



→ Duty cycle distortion increases (accumulates) with the number of delay elements used, i.e. the programmed delay time

- If all **inverters in the delay chain are equal** (and the number of inverters is even), **no duty cycle distortion** occurs (differences in rising and falling edge propagation delay cancel out)

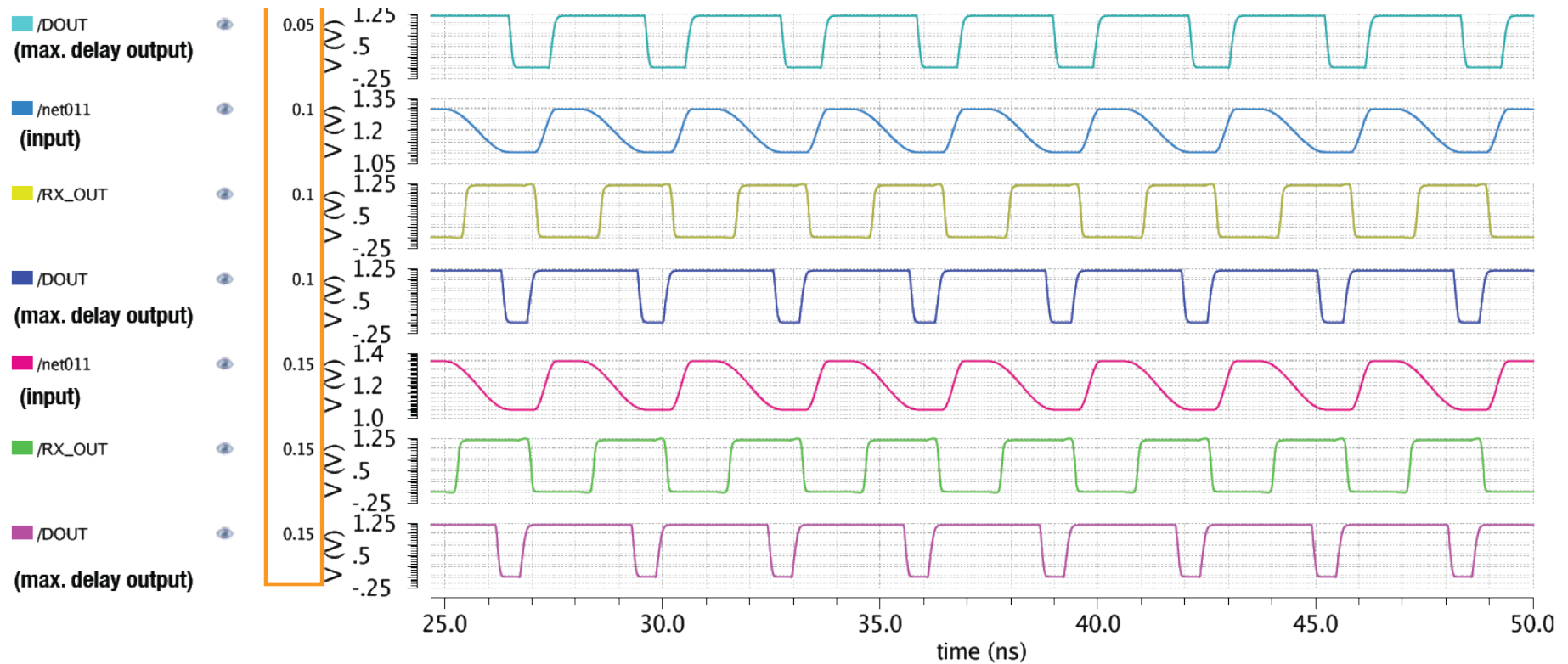


➔ Implemented new, custom made delays based on identical inverters



# Duty cycle distortion

- Duty cycle distortion was overlooked during DHPT 1.0 sign-off



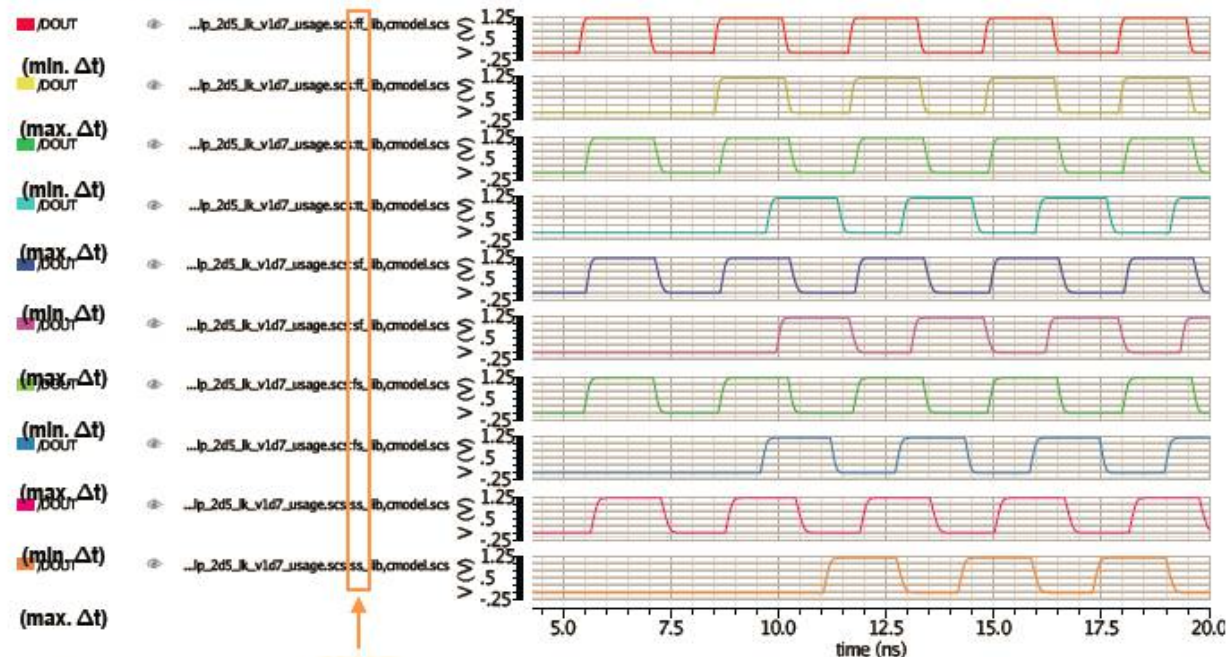
# Delay Element Modification

- Custom delay elements made out of identical inverters

All corners covers 3.125 ns ( $\leftarrow$  320 MHz).

Max. delay time with extracted model

	$\Delta t$	duty cycle (min. $\Delta t$ )	duty cycle (max. $\Delta t$ )
tt	4.20 ns	52.0%	53.3%
ff	3.15 ns	51.4%	52.2%
fs	4.10 ns	51.6%	51.8%
sf	4.43 ns	52.2%	54.9%
ss	5.42 ns	52.8%	54.9%



07.04.2015, T.Kishishita

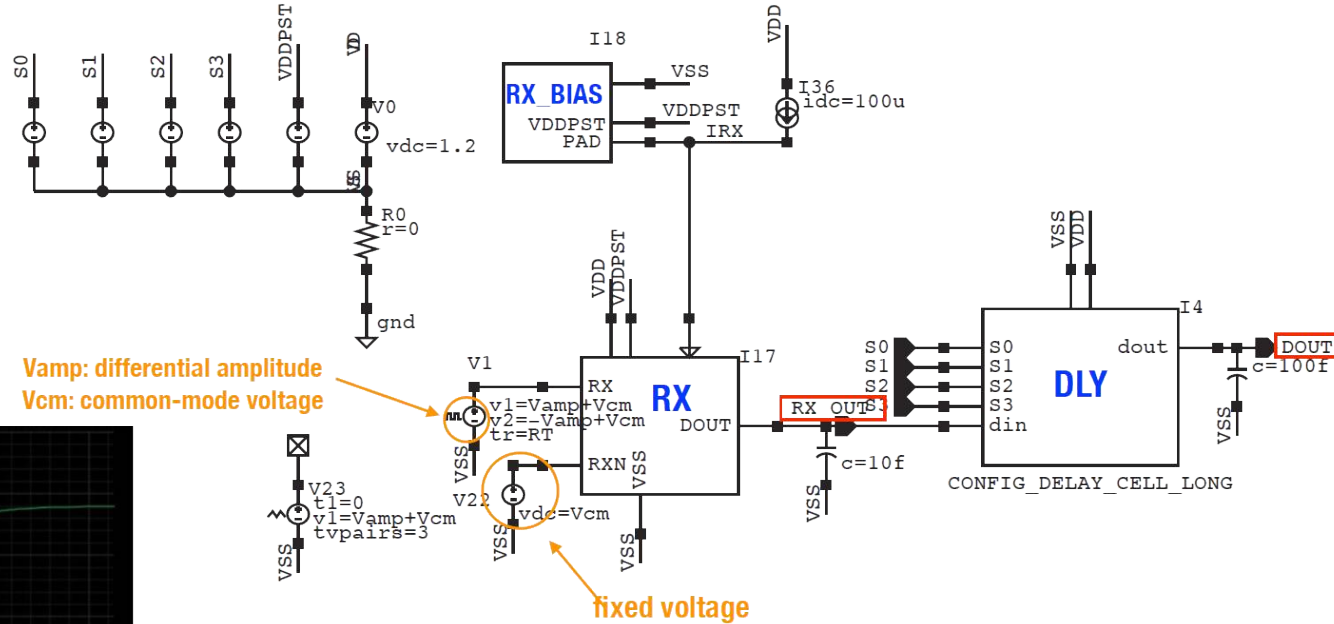
Duty cycle degrades at most a few percent after max. delay.

DHPT 1.0

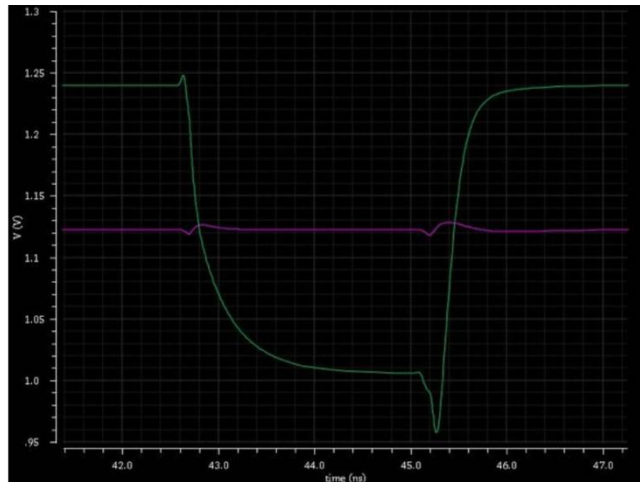
# **DCD DATA RECEIVER**

# DCD Data Receiver

- Single ended DCD data receivers based on LVDS receivers → low voltage single ended signaling (LVSE)



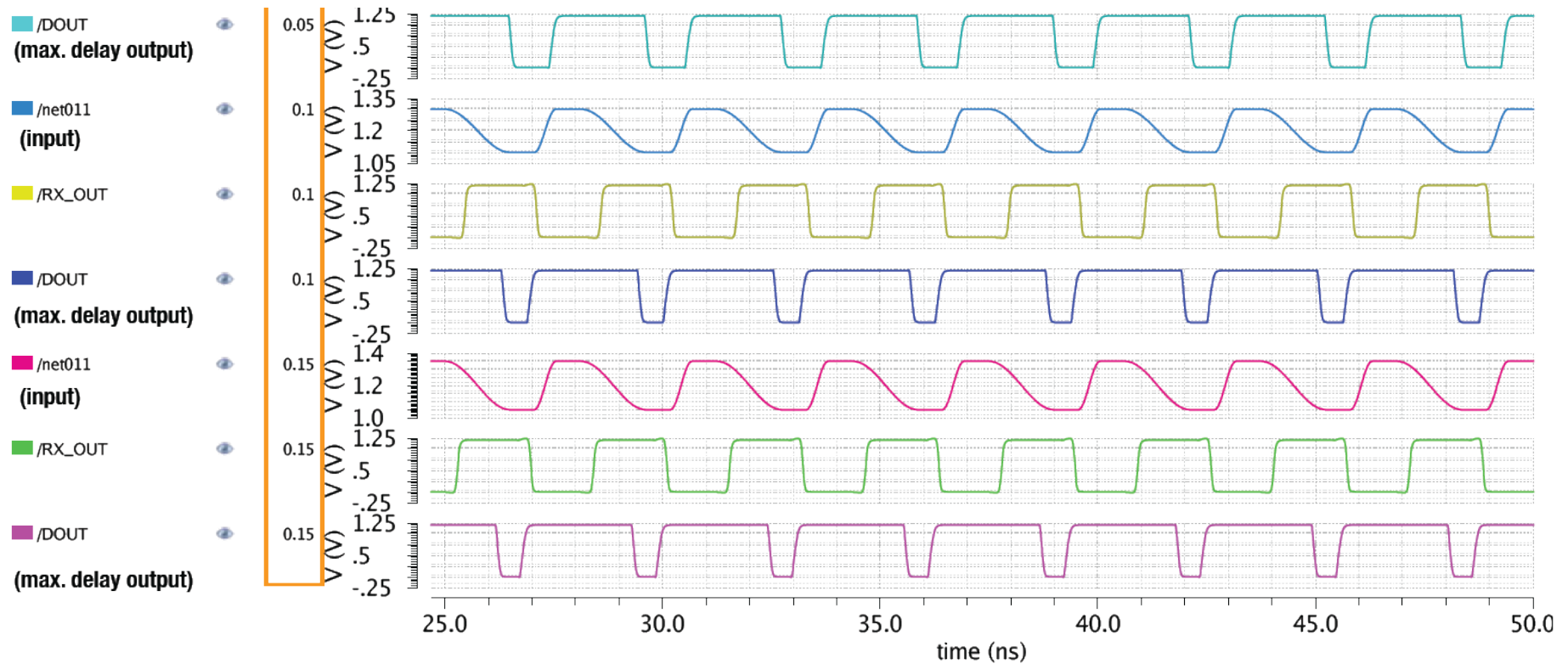
DCD LVDS output (from Ivan)



- the falling and rising edges with non-symmetrical shape
- differential amplitude of 120 mV

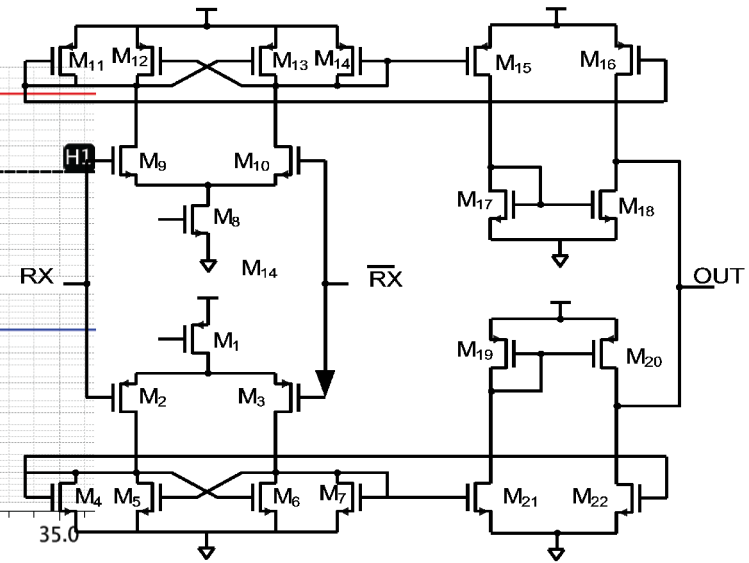
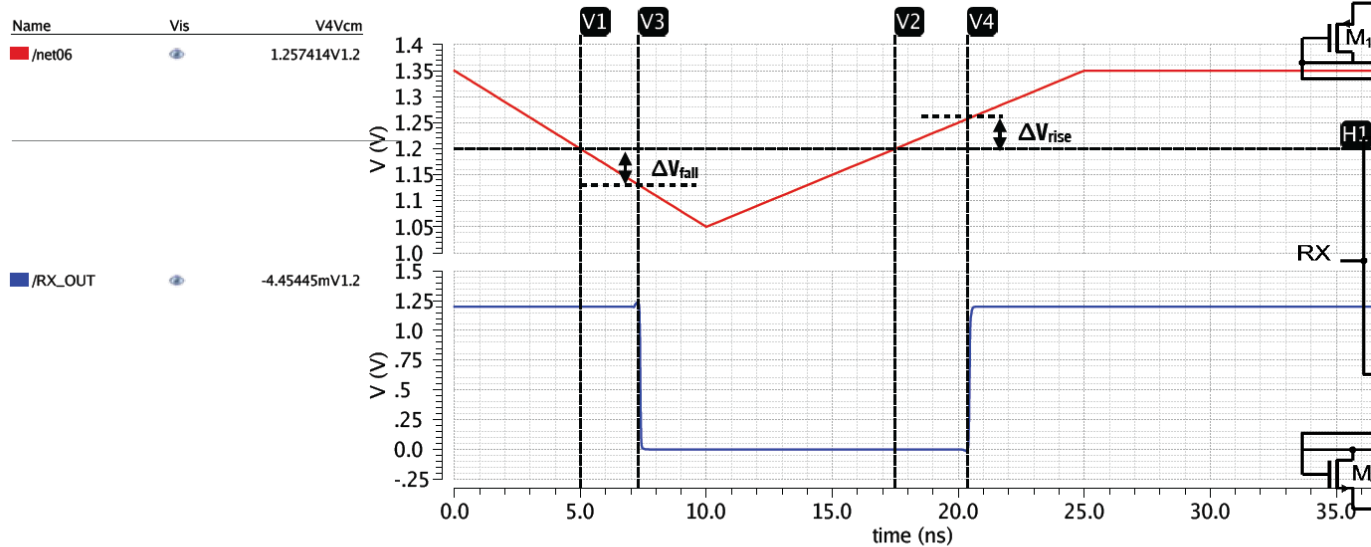
# Duty cycle distortion

- Duty cycle distortion was overlooked during DHPT 1.0 sign-off



# LVDS Receiver (DHPT 1.0)


- LVDS RX with build-in hysteresis



### Markers

	Vcm	V1	V2	V3	V4
x		5.0ns	17.4689ns	7.31256ns	20.3707ns
/net06					
/net06	1.2	1.2V	1.199378V	1.130623V	1.257414V
/RX_OUT					
/RX_OUT	1.2	1.2V	37.1315nV	1.22718V	-4.45445mV

	$\Delta V_{fall}$	$\Delta V_{rise}$
ff	55 mV	46 mV
fs	71 mV	57 mV
sf	68 mV	57 mV
ss	85 mV	68 mV


 **$\Delta V_{rise} = 57 \text{ mV}$**   
 **$\Delta V_{fall} = 70 \text{ mV}$**  (for nominal corner)



# LVDS Receiver Design Modification

FET sizes and layout modified to reduce hysteresis (~50% of the current DHPT1.0 design).

## Hysteresis values with extracted model

	$\Delta V_{fall}$	$\Delta V_{rise}$
tt	27.5 mV	34.4 mV
ff	19.8 mV	30.0 mV
fs	29.1 mV	33.4 mV
sf	26.3 mV	34.1 mV
ss	33.7 mV	35.8 mV

## DCD-like input behaviors ( $V_{amp}=0.1$ V)

